

AMC 2024

2024 ADVANCED MATERIALS CHARACTERIZATION *workshop*

Optical Characterization Methods

Part I

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University of Illinois at Urbana-Champaign

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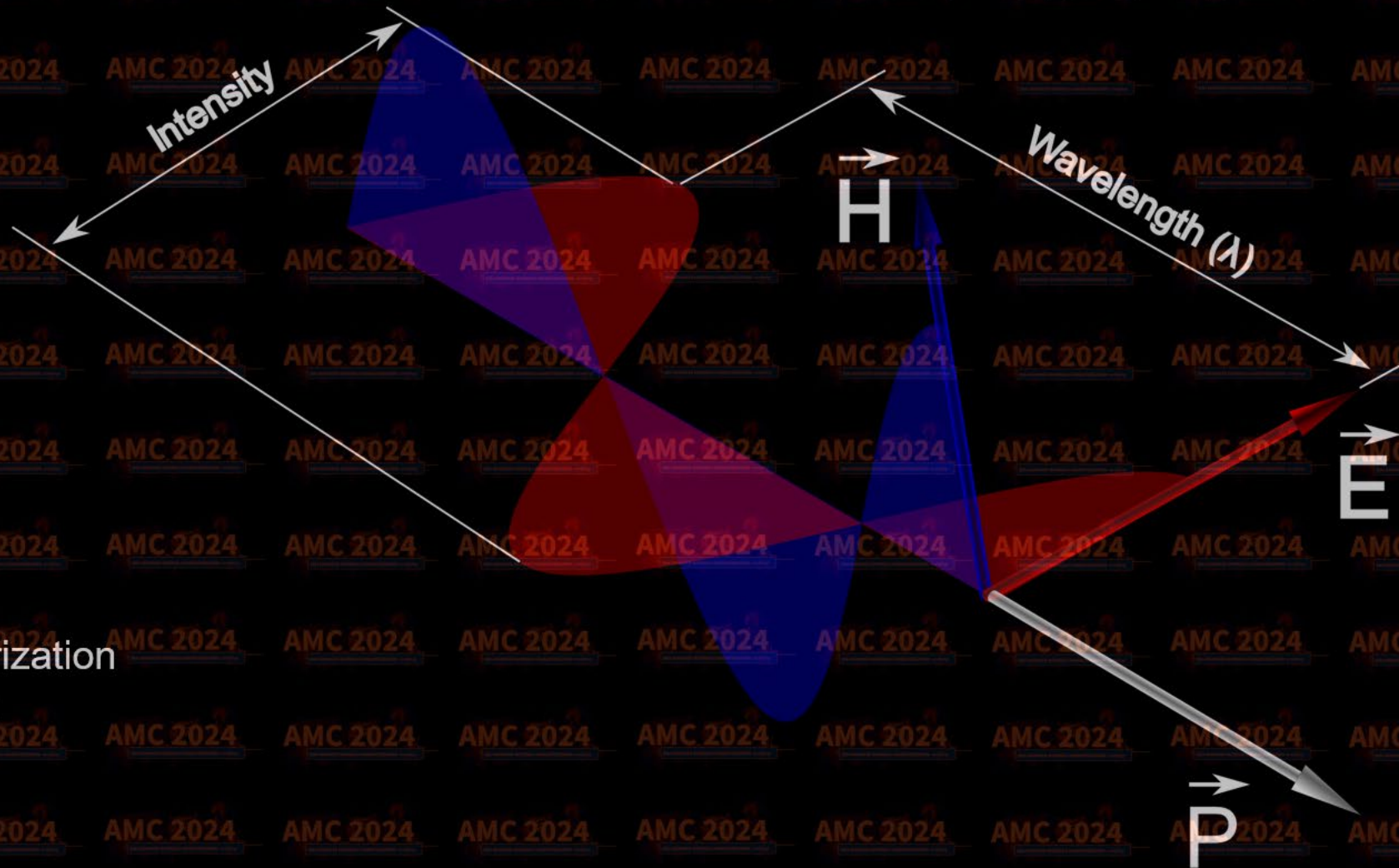
Optical Characterization



Light Properties
Light-matter interaction
Instrumentation and methods
Application examples
Strengths and limitations
Complementary techniques



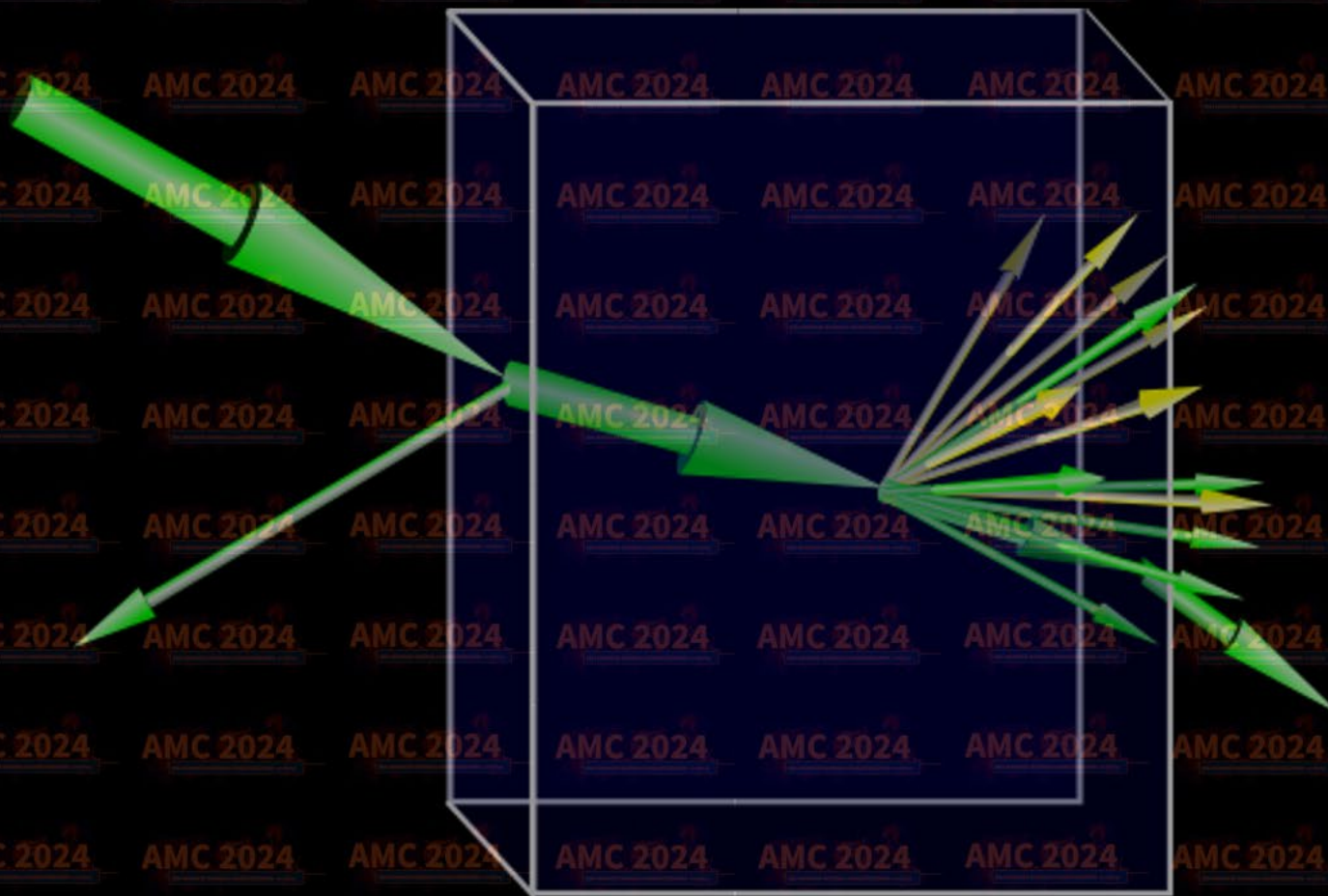
Light properties



- Direction of propagation
- Electric field direction or polarization
- Photon energy or wavelength
- Intensity

Light interactions

- Transmission
- Reflection
- Absorption
- Emission
- Scattering
- Refraction



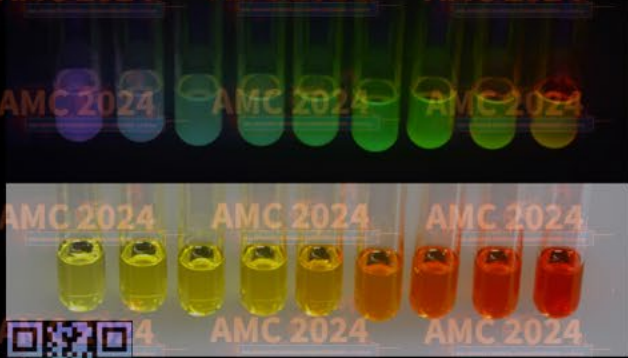
Non-linear effects

- SFG
- SHG
- DFG
- Multi-photon absorption



Light interactions with matter

Size



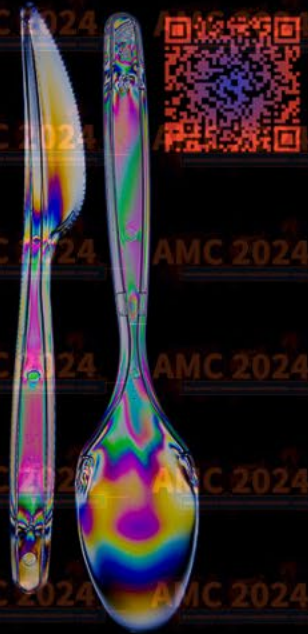
Lattice structure, dopants



Temperature



Stress



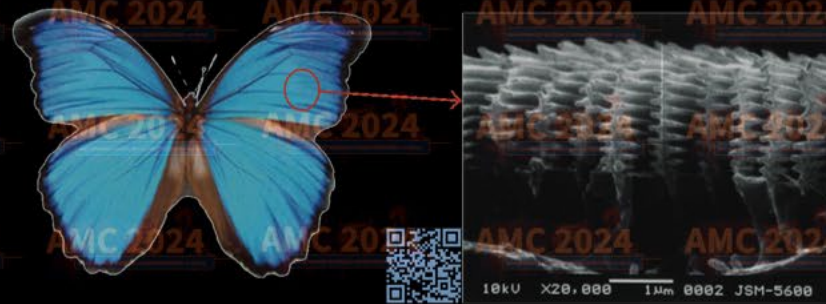
Thickness



Concentration



Microstructure

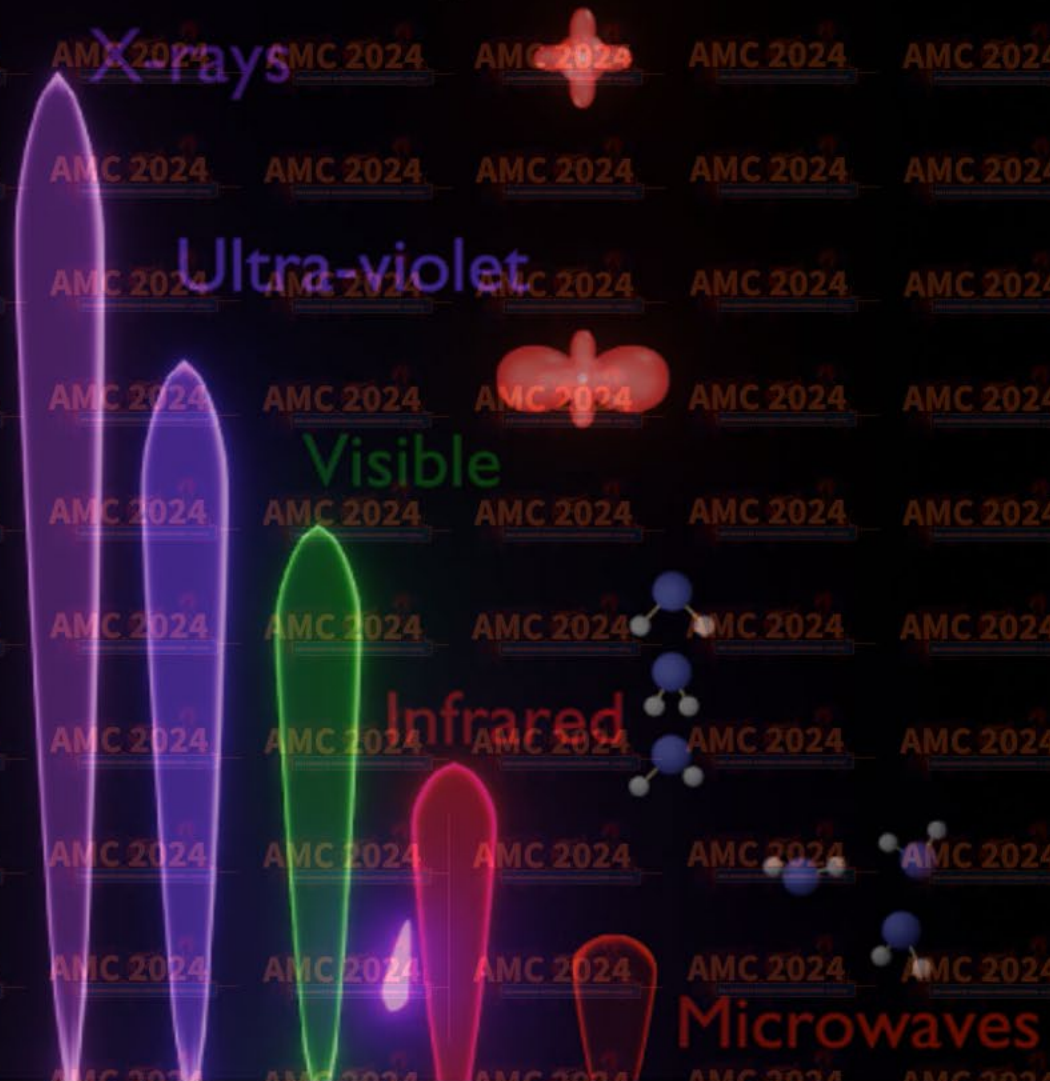


Composition



Light interactions with matter

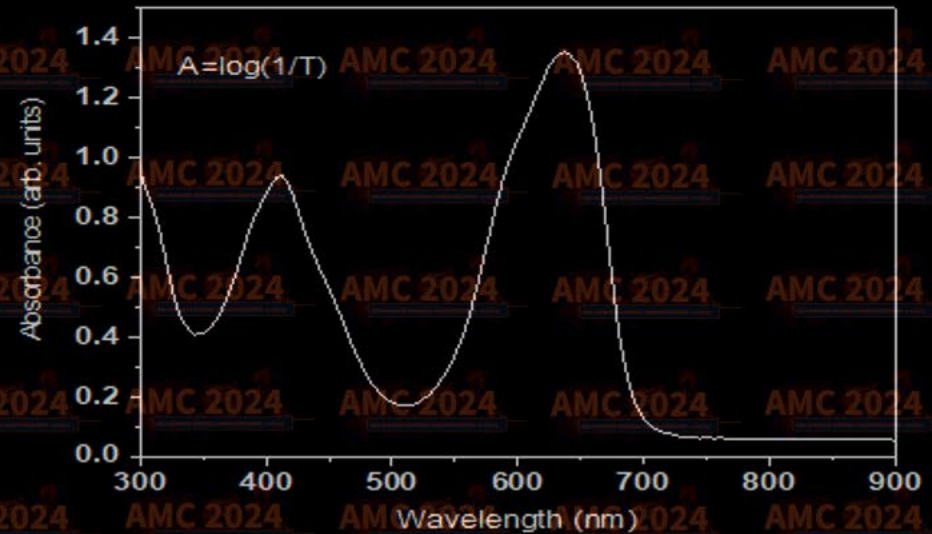
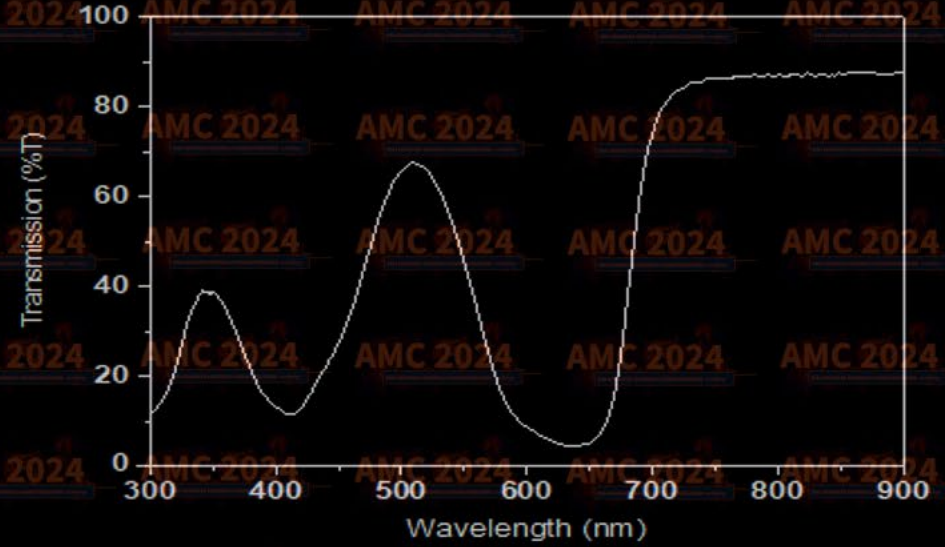
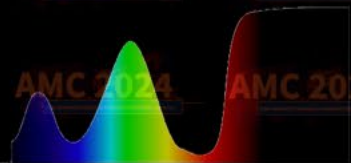
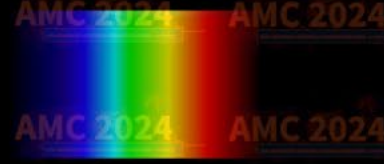
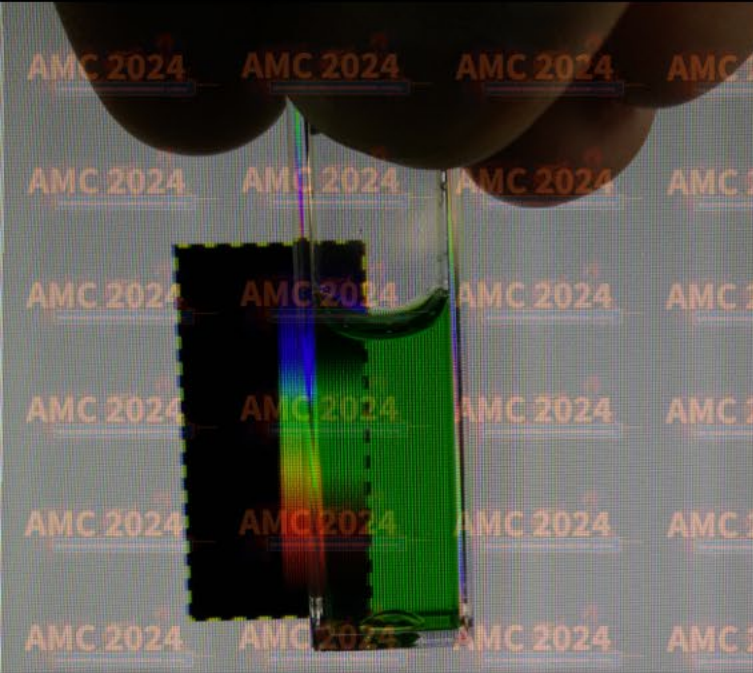
photon energy



00:06.06



Spectroscopy



Transmission, Reflection, Absorption

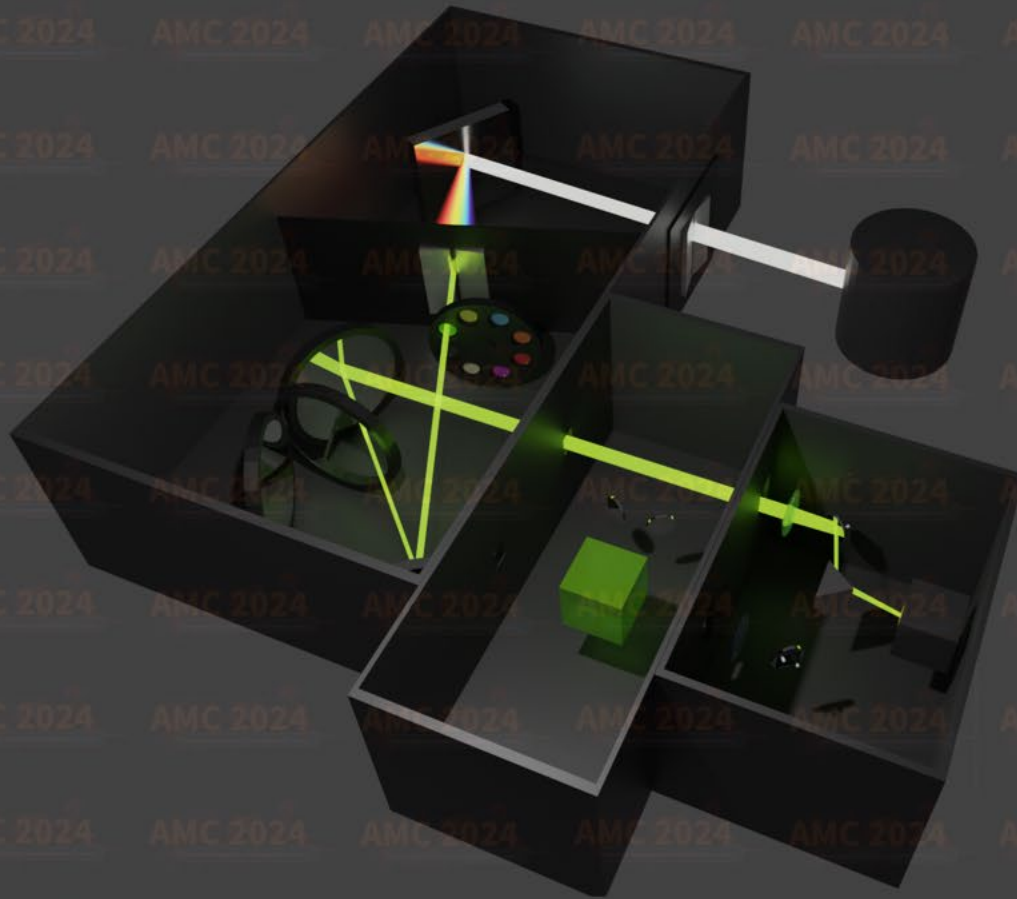
What is measured:

The transmitted and reflected light intensity as a function of the incident photon energy, which depends on the material's electronic, atomic, chemical and morphological structure.



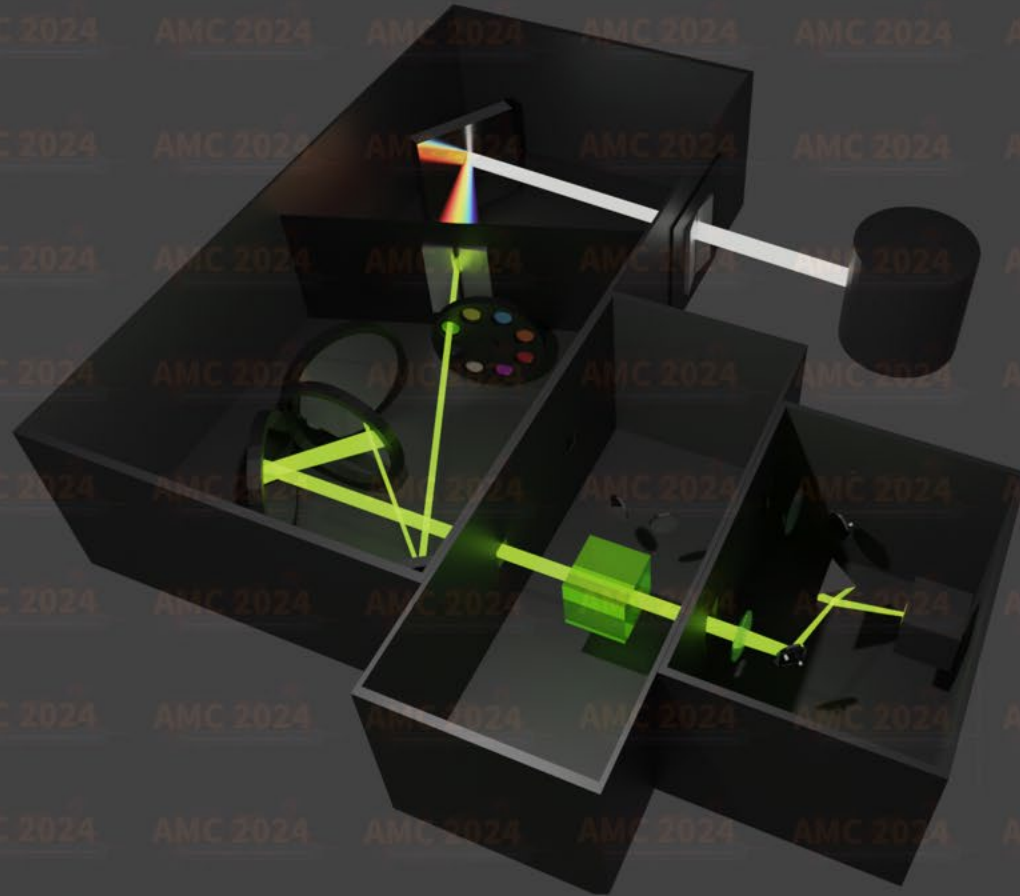
Spectrophotometry (UV-VIS-NIR)

Instrumentation:



Spectrophotometry (UV-VIS-NIR)

Instrumentation:



Spectrophotometry (UV-VIS-NIR)

Instrumentation:



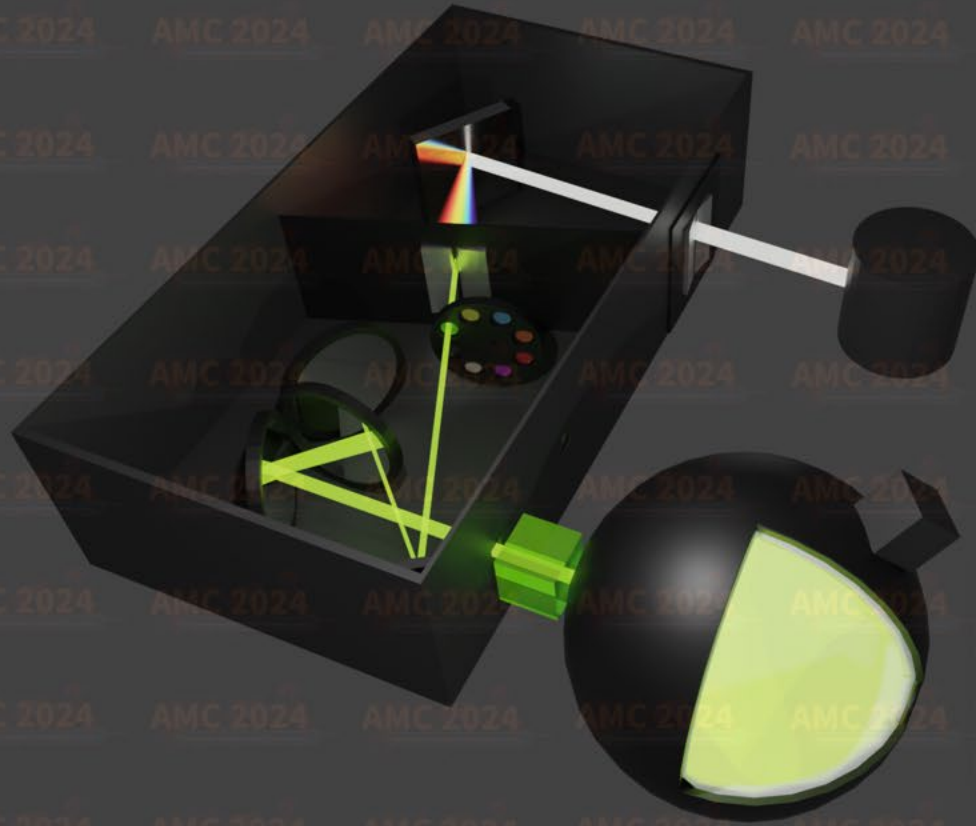
Spectrophotometry (UV-VIS-NIR)

Instrumentation:



Spectrophotometry (UV-VIS-NIR)

Instrumentation:



Spectrophotometry (UV-VIS-NIR)

Monoatomic gas (H_2)

Solid material (CdS)

Electronic levels

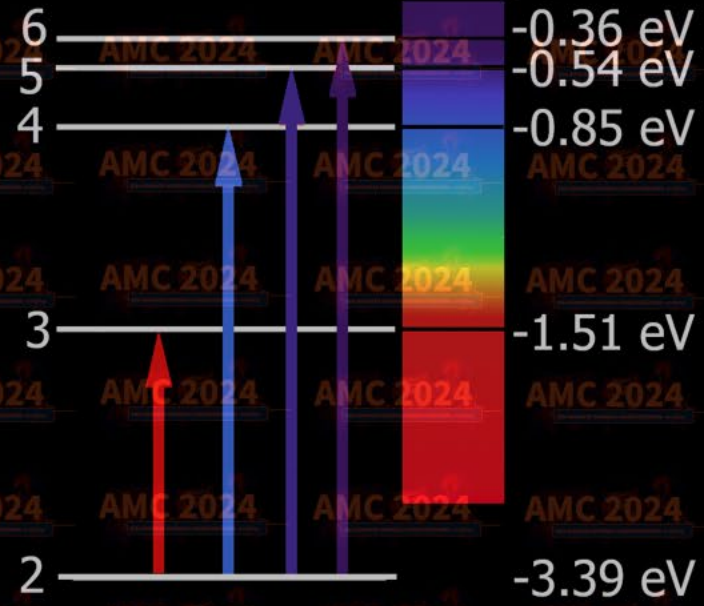
Electronic bands



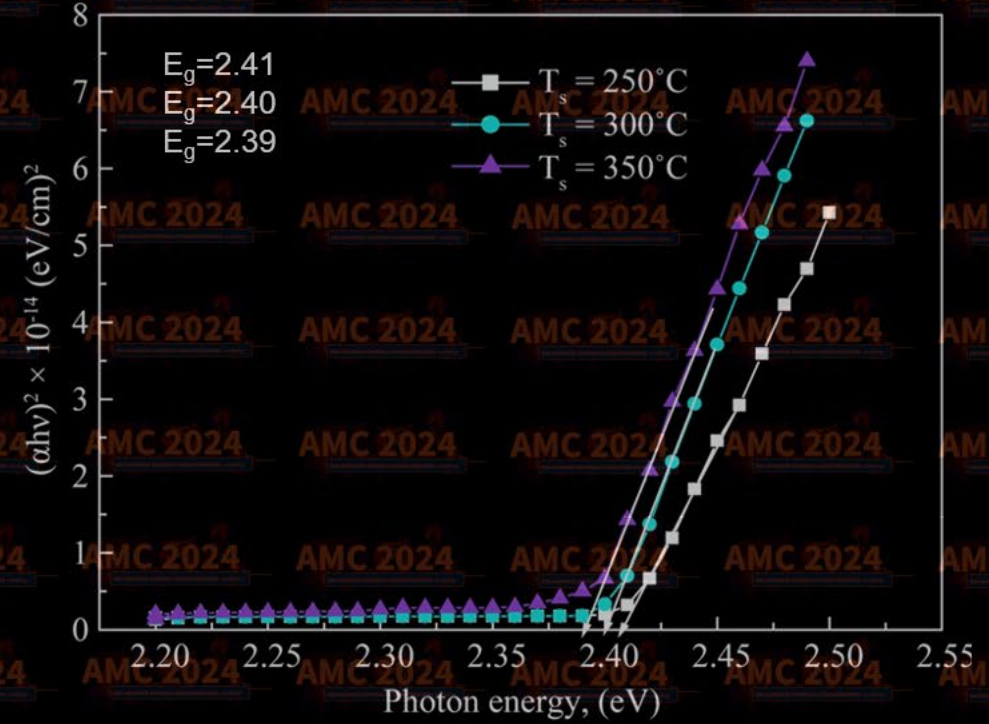
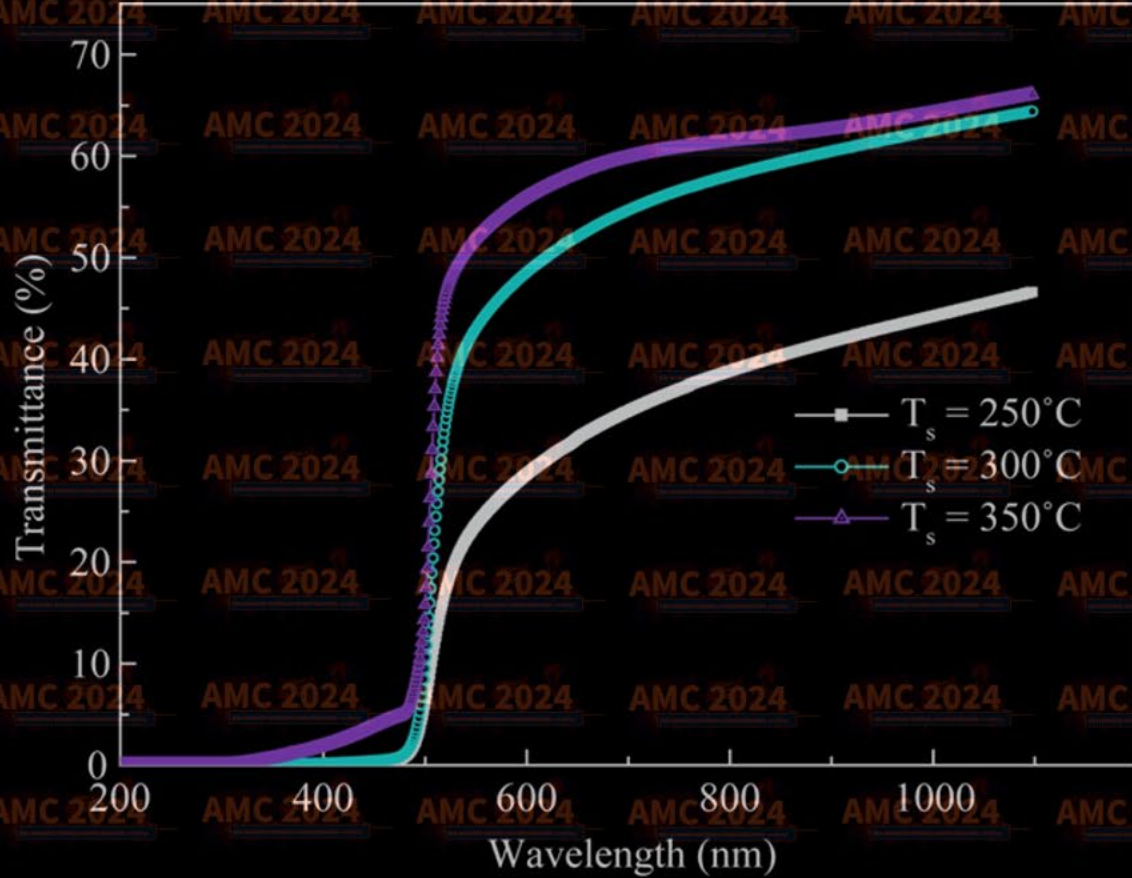
Electronic states of H

Absorption spectrum (white light)

Absorption spectrum (white light)



Spectrophotometry (UV-VIS-NIR)



Optical band gap determination of CdS thin films as a function of growth substrate temperatures

Tauc's relation: $\alpha h\nu = A(h\nu - E_g)^m$

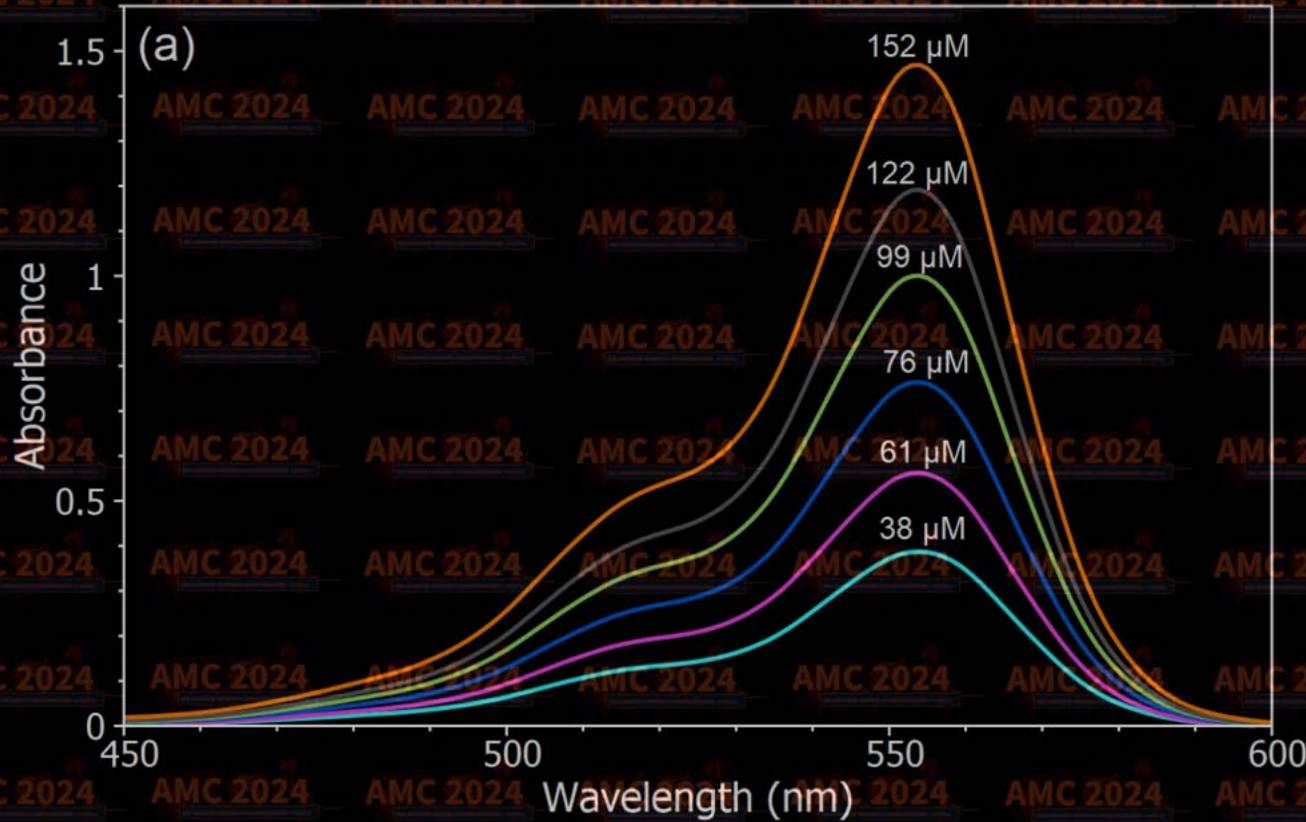
$m = 0.5$ for direct and 2 for indirect allowed transitions.



J. Surf. Eng. Mat. and Adv. Tech. **3**, 43 (2013)



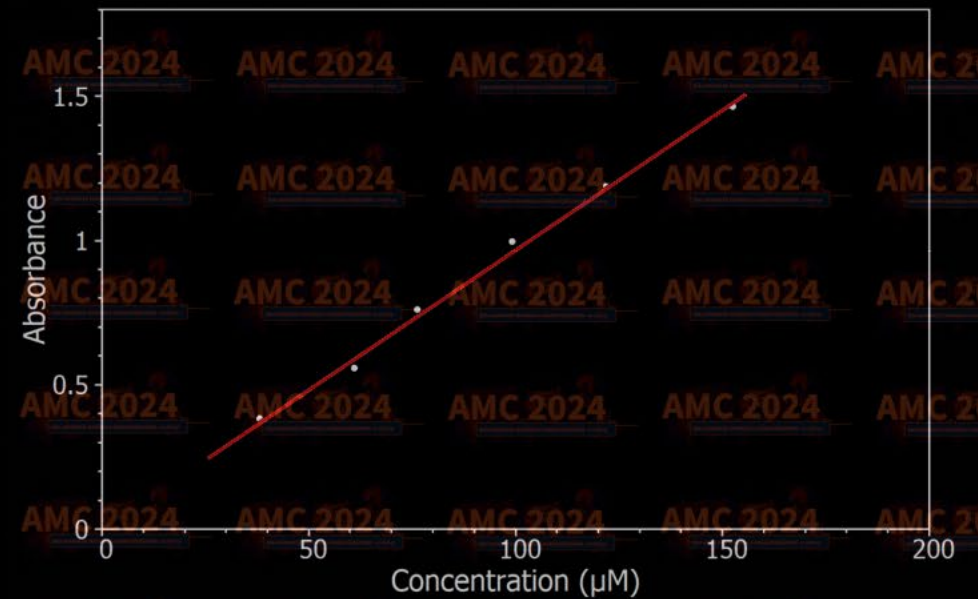
Spectrophotometry (UV-VIS-NIR)



Beer-Lambert Law

$$Abs = K \ell c = a \ell$$

$$Abs = \log (1/T)$$



Using absorbance to determine Rhodamine B concentration in water solutions



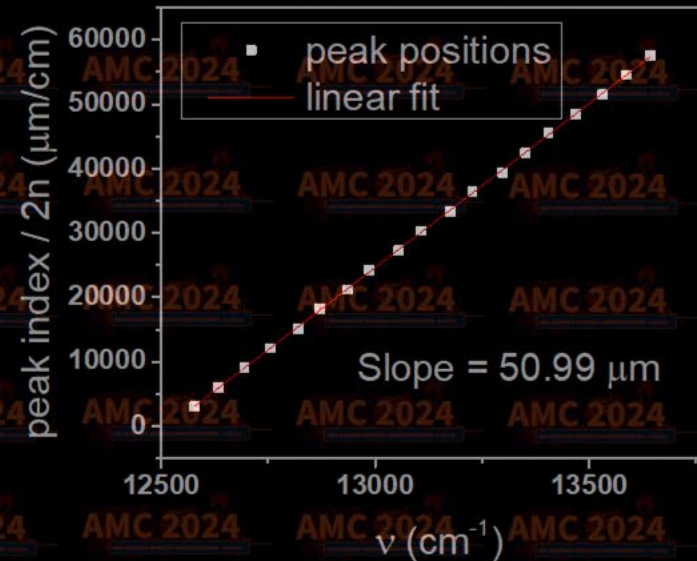
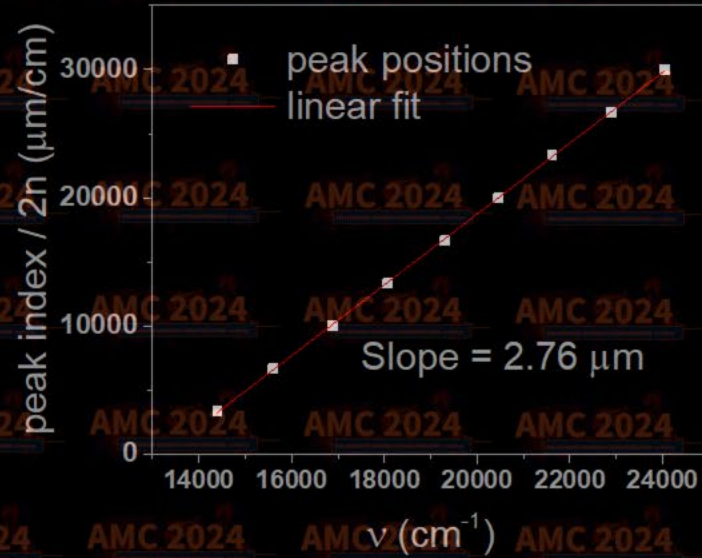
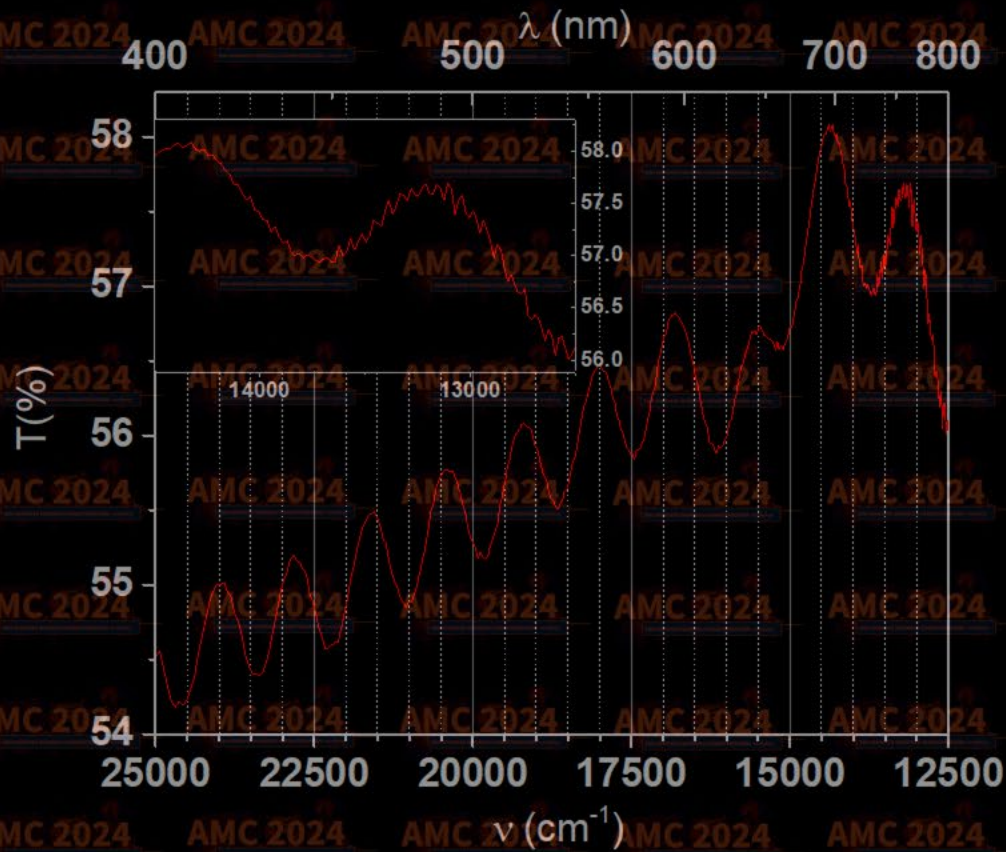
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INSTRUMENTS



Spectrophotometry (UV-VIS-NIR)



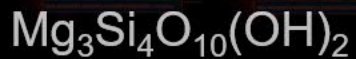
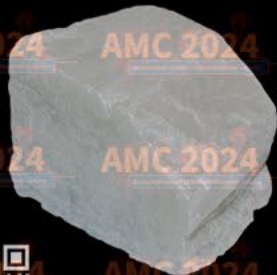
Spectrophotometry (UV-VIS-NIR)



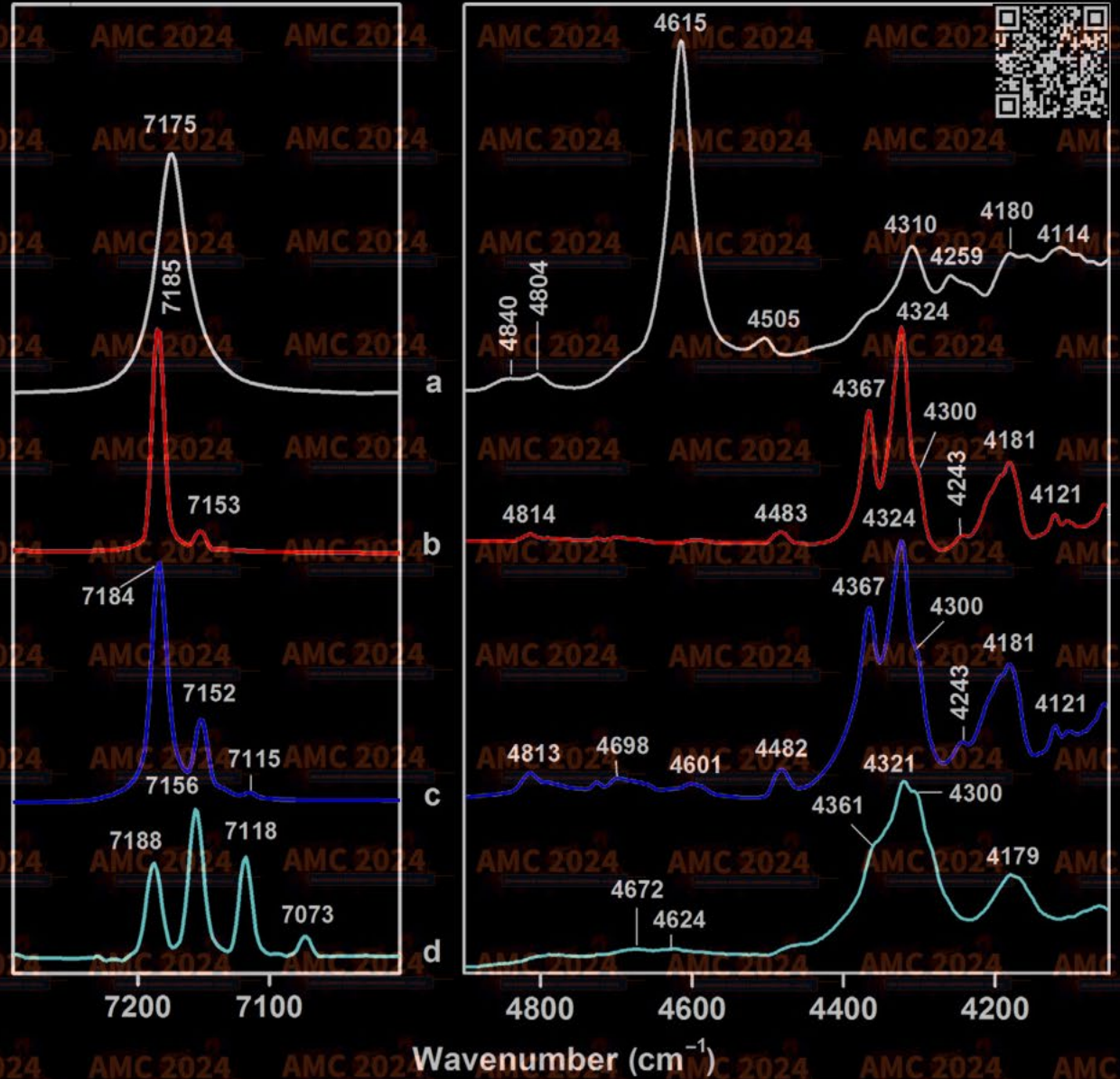
Using transmission interference fringes to determine thickness



Spectrophotometry (UV-VIS-NIR)



Absorbance

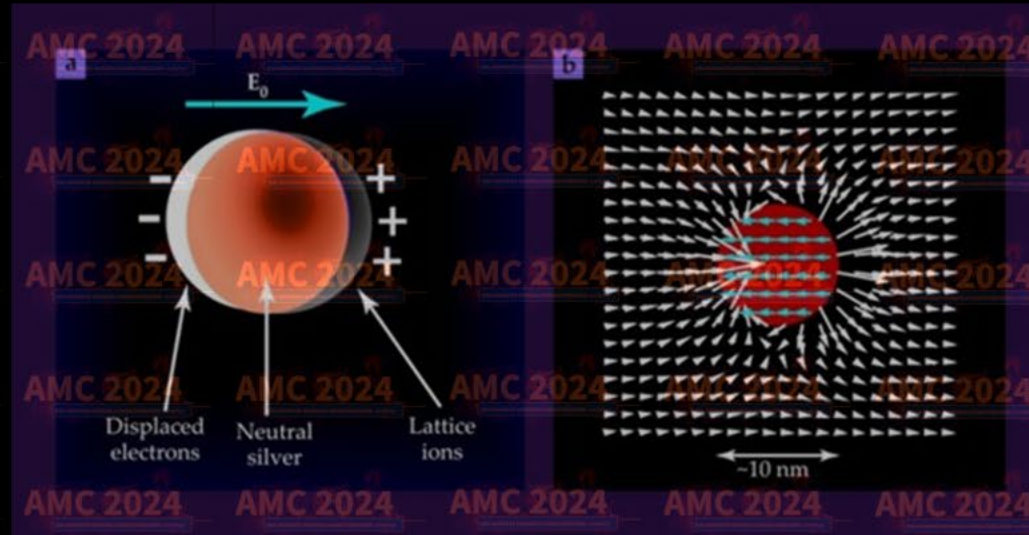
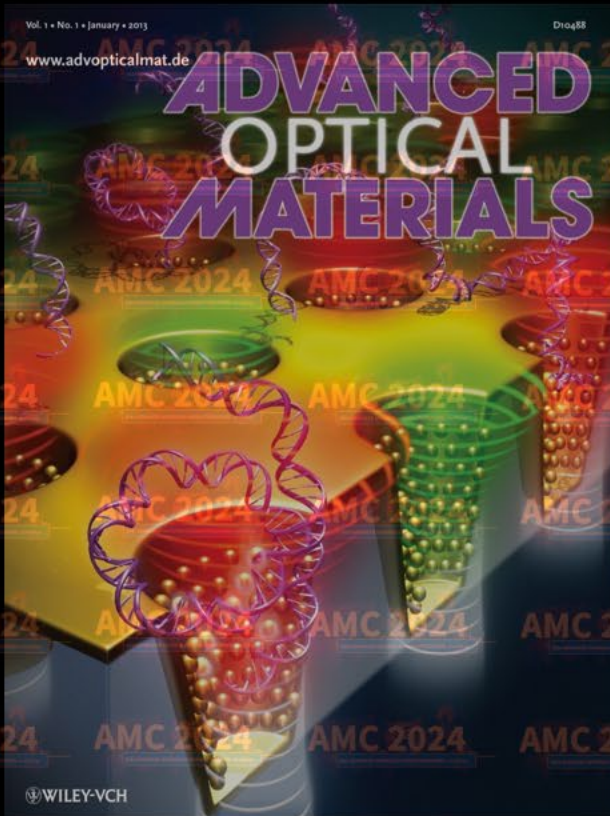


Spectra from *Developments in Clay Science*, Vol. 8, Ch. 5

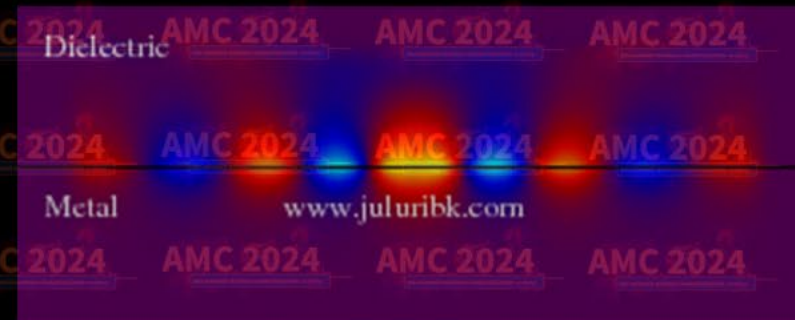


Excitations in materials

- Plasmons

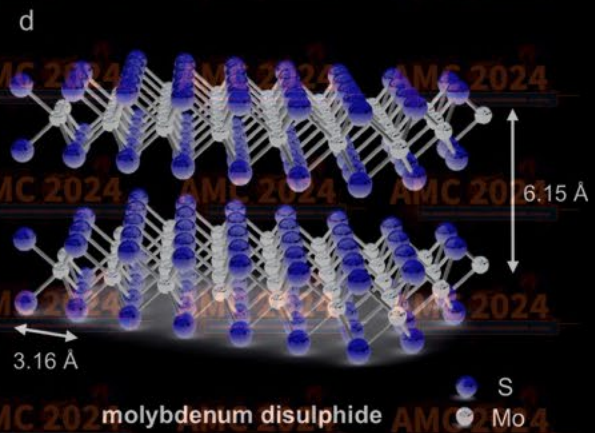
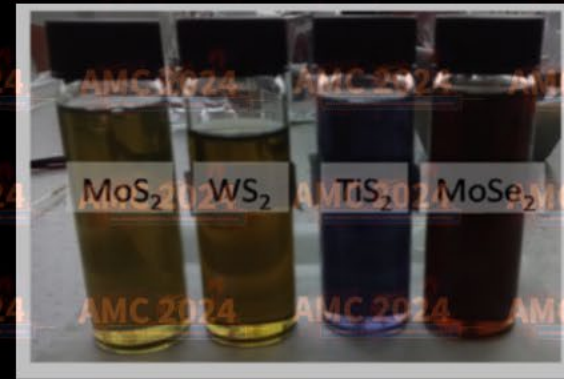
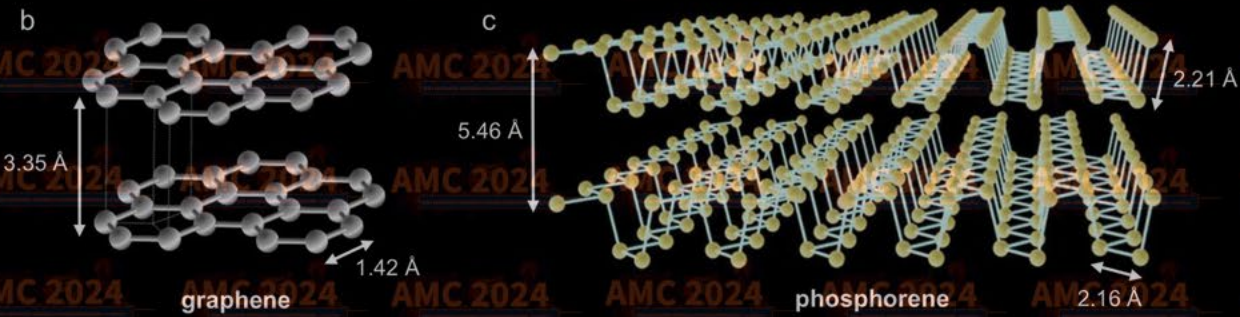


Phys. Today, 64, 39 (2011)

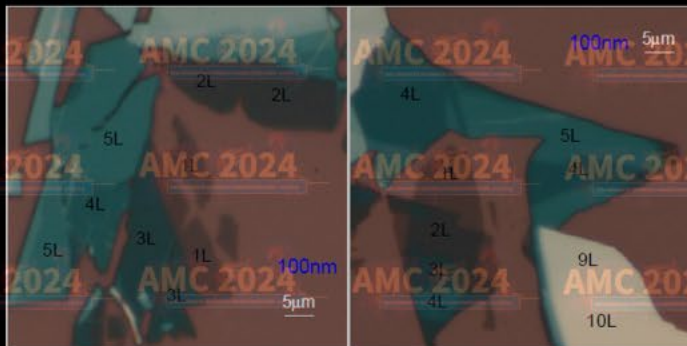
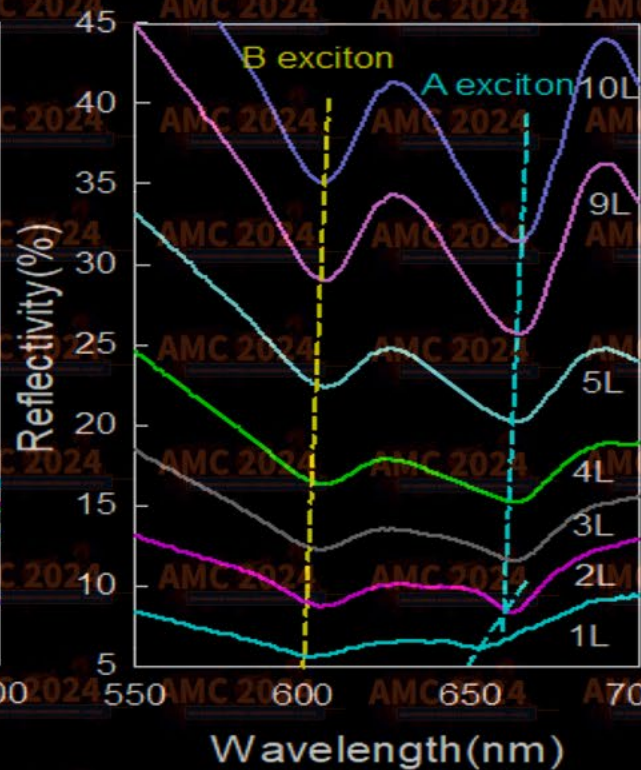
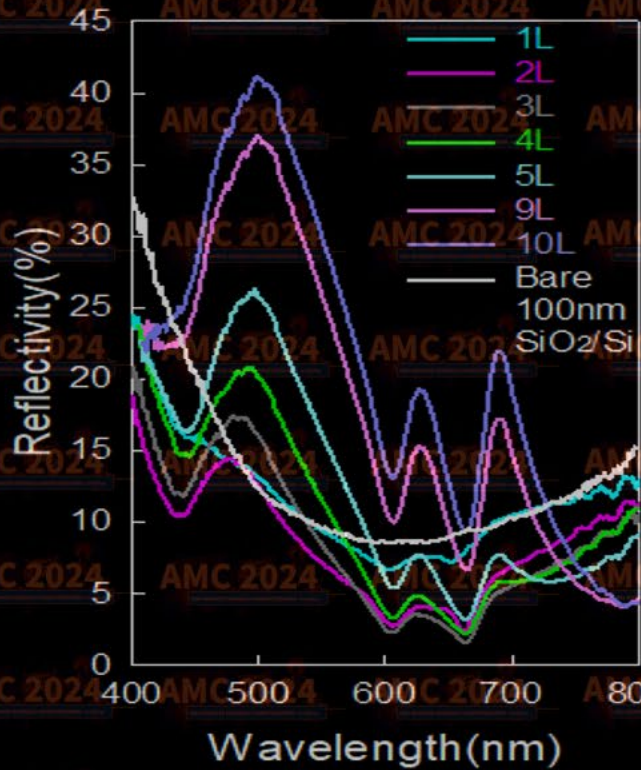


Plasmons are quanta of collective motion of charge-carriers in a gas with respect of an oppositely charged background. They play a significant role on transmission and reflection of light.

Spectrophotometry (UV-VIS-NIR)



Applied Materials Today 8, 68 (2017)



Optical Materials Express, 332858 (2018)



Vibrational spectroscopy

Normal vibrational modes in molecules:

CO₂ (4 modes)



$$\nu_1 = 1388 \text{ cm}^{-1}$$



$$\nu_2 = 667 \text{ cm}^{-1}$$



$$\nu_3 = 2349 \text{ cm}^{-1}$$

H₂O (3 modes)



$$\nu_1 (3657 \text{ cm}^{-1})$$



$$\nu_3 (3756 \text{ cm}^{-1})$$



$$\nu_2 (1595 \text{ cm}^{-1})$$

CH₄ (9 modes)



ν_1 : symmetric stretch



ν_2 : symmetric bend



ν_3 : antisymmetric stretch



ν_4 : antisymmetric bend

Number of modes:
3N-6 for non-linear molecules
3N-5 for linear molecules



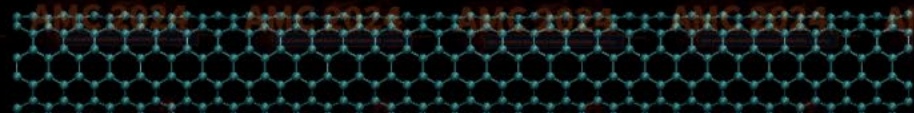
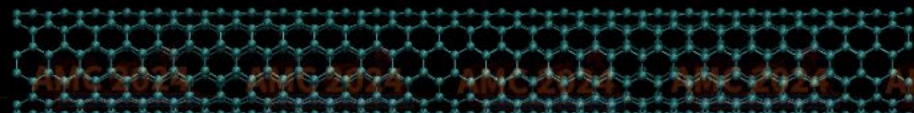
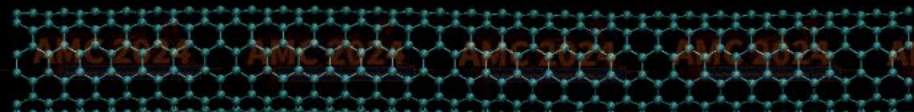
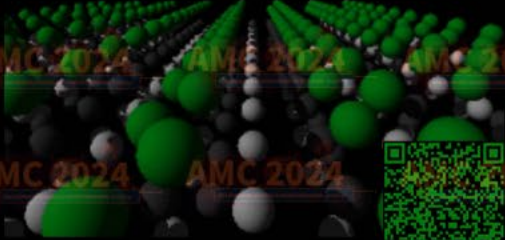
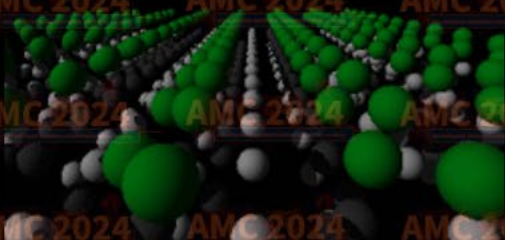
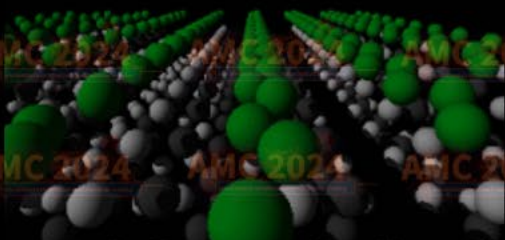
Vibrational spectroscopy

Normal vibrational modes in solids:

SWCNT

Sb/GaAs(110)

GaN



Fourier Transform IR spectroscopy (FTIR)

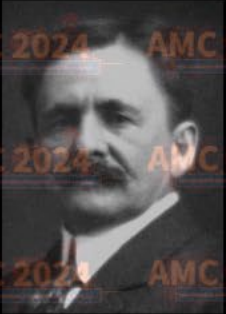
IR active vibrations

The intensity of a vibrational absorption depends on the change of the transition dipole momentum caused by that vibration, so a vibration mode j will be “IR active” only when the vibration causes a change in the dipole momentum of the molecule, i.e. $\Delta\mu \neq 0$

IR active



Fourier Transform IR spectroscopy (FTIR)



The Nobel Prize in Physics 1907
Albert A. Michelson

"for his optical precision instruments and the spectroscopic and metrological investigations carried out with their aid"

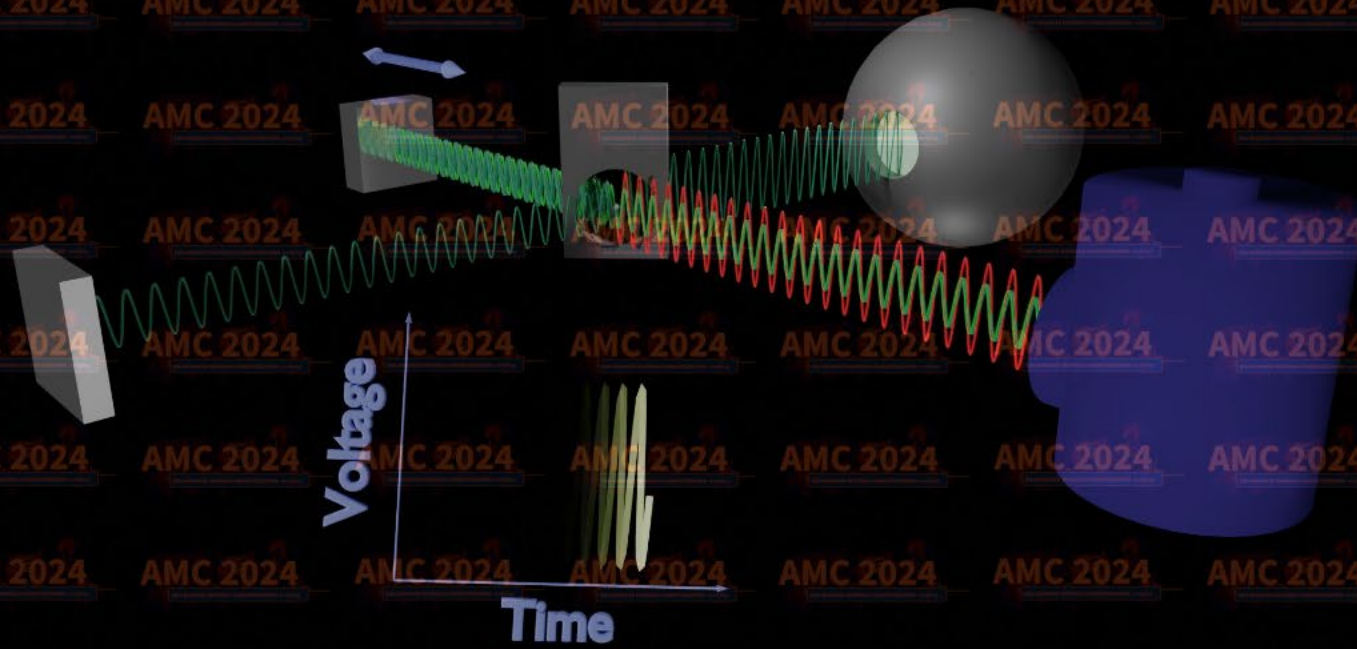
The Nobel Foundation

Instrumentation:

The FTIR uses a Michelson interferometer with a moving mirror, in place of a diffraction grating or prism.

$\Delta L = n\lambda \Rightarrow$ constructive interference

$\Delta L = (n+1/2)\lambda \Rightarrow$ destructive interference



Fourier Transform IR spectroscopy (FTIR)



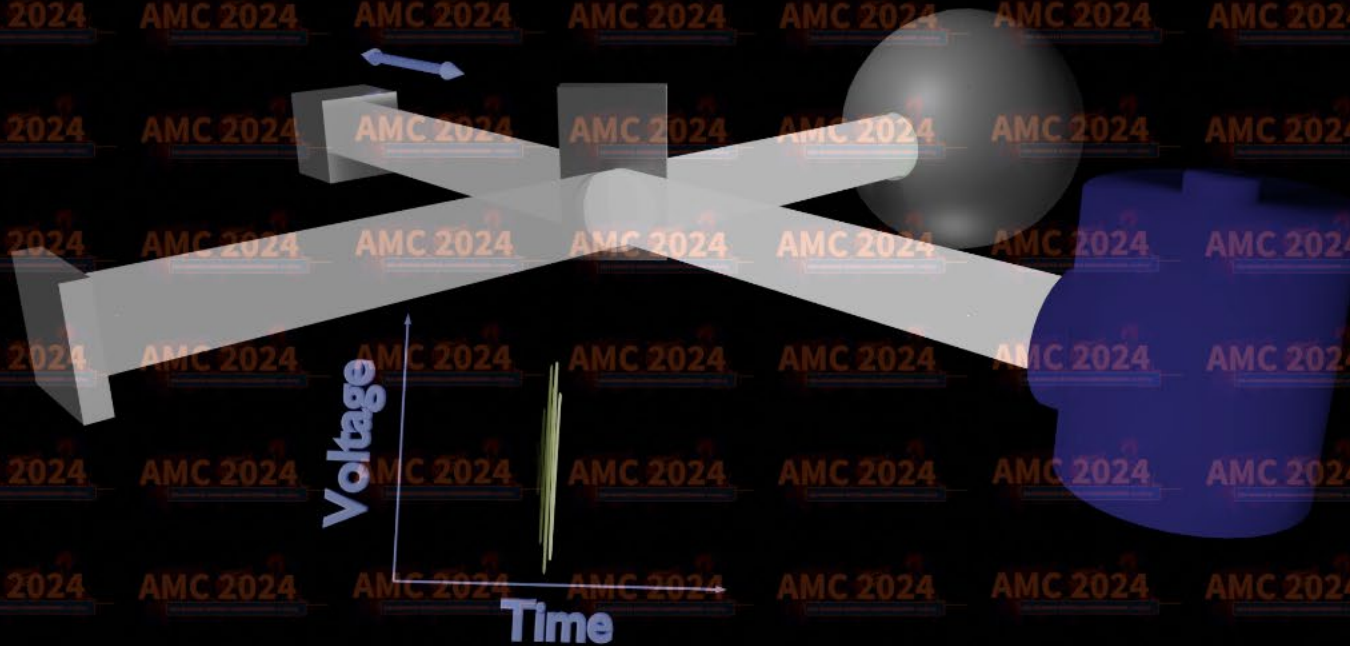
The Nobel Prize in Physics 1907
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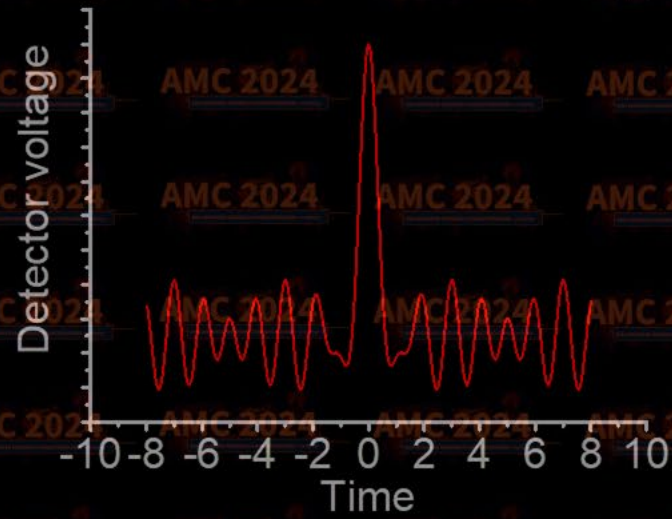
The Nobel Foundation

Instrumentation:

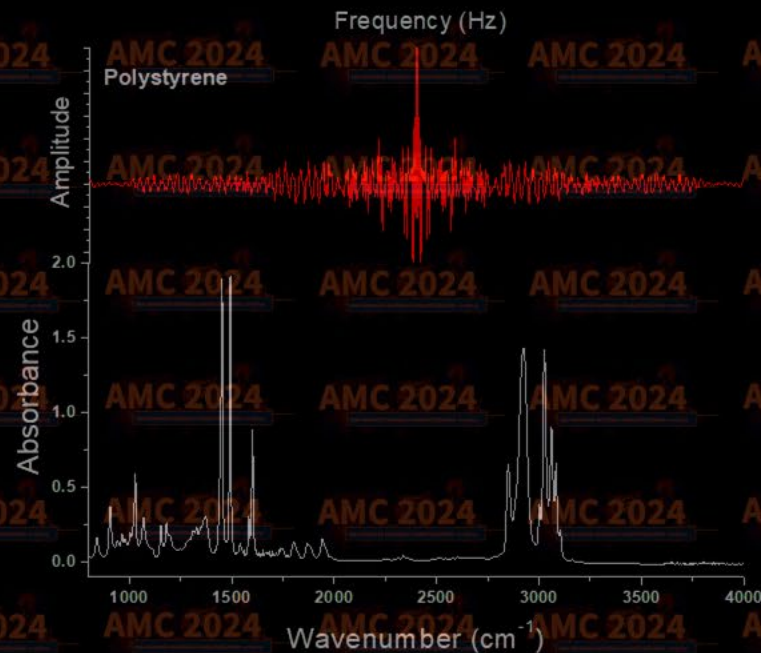
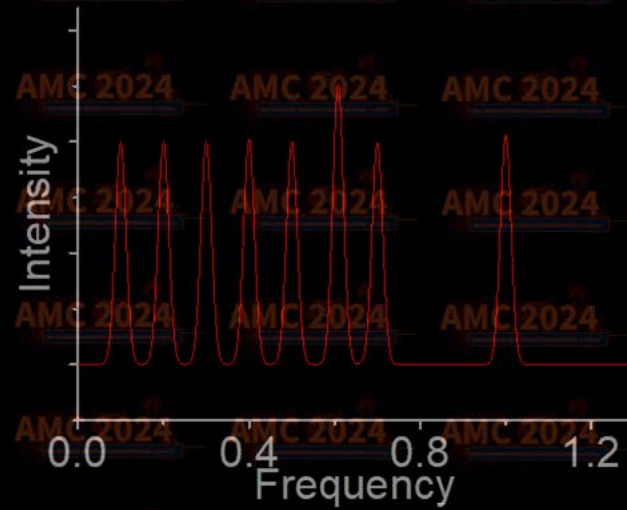
The FTIR uses a Michelson interferometer with a moving mirror, in place of a diffraction grating or prism.



Fourier Transform IR spectroscopy (FTIR)



$$I(\nu) = \int_{-\infty}^{\infty} S(t) e^{2i\nu\pi t} dt$$



Fourier Transform IR spectroscopy (FTIR)

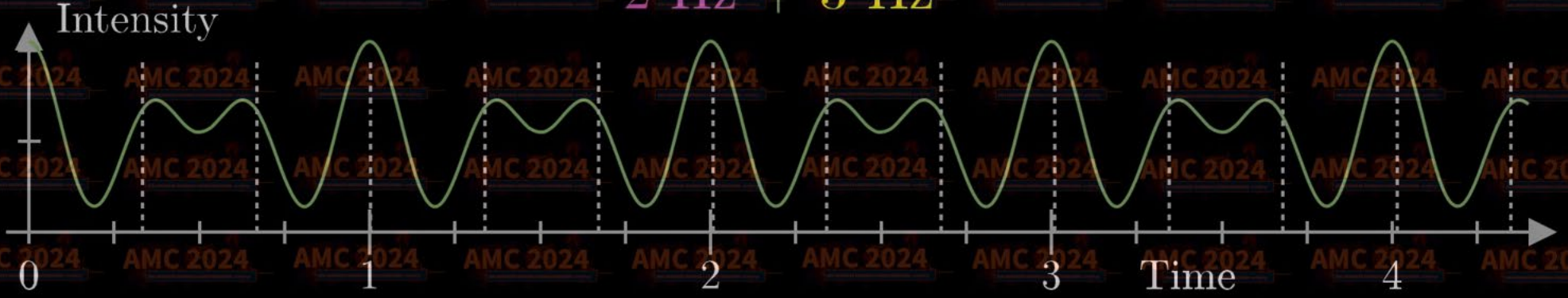
But what is the Fourier Transform? A visual introduction.



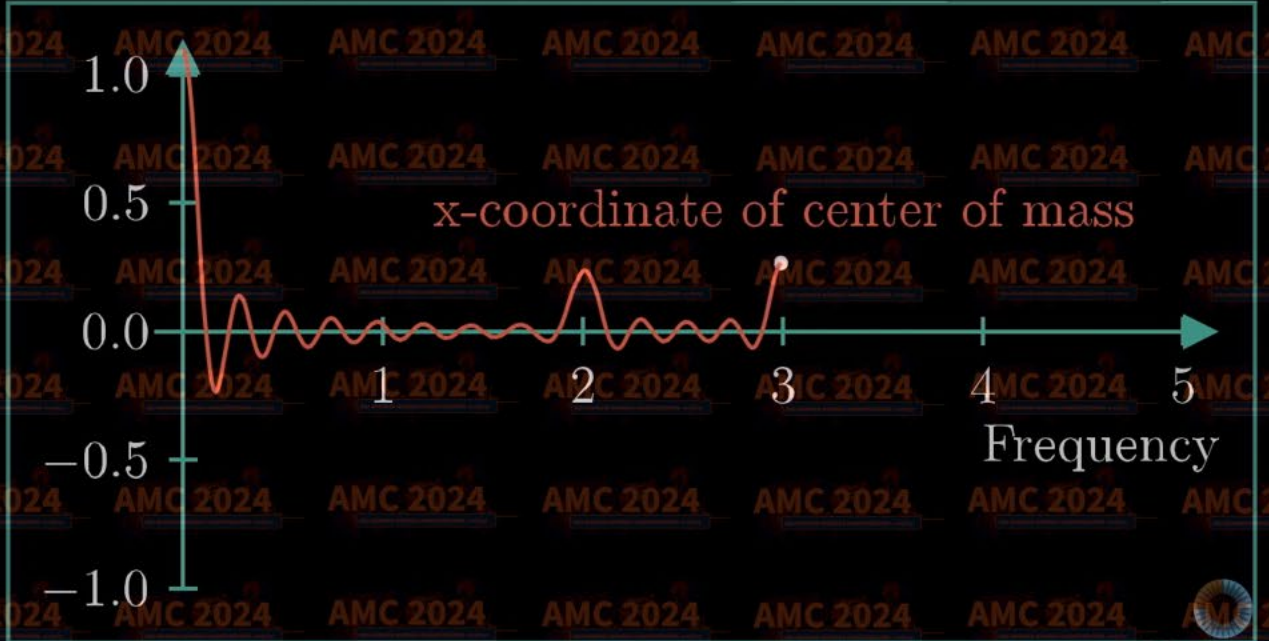
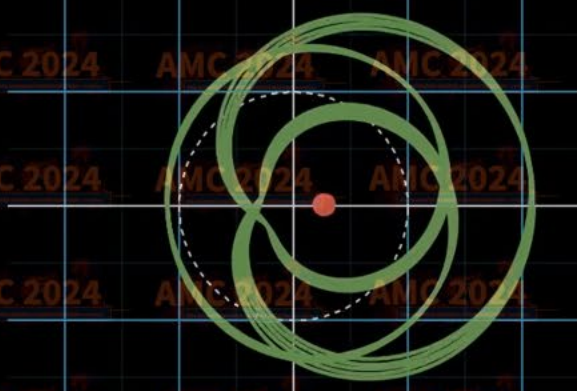
3Blue1Brown



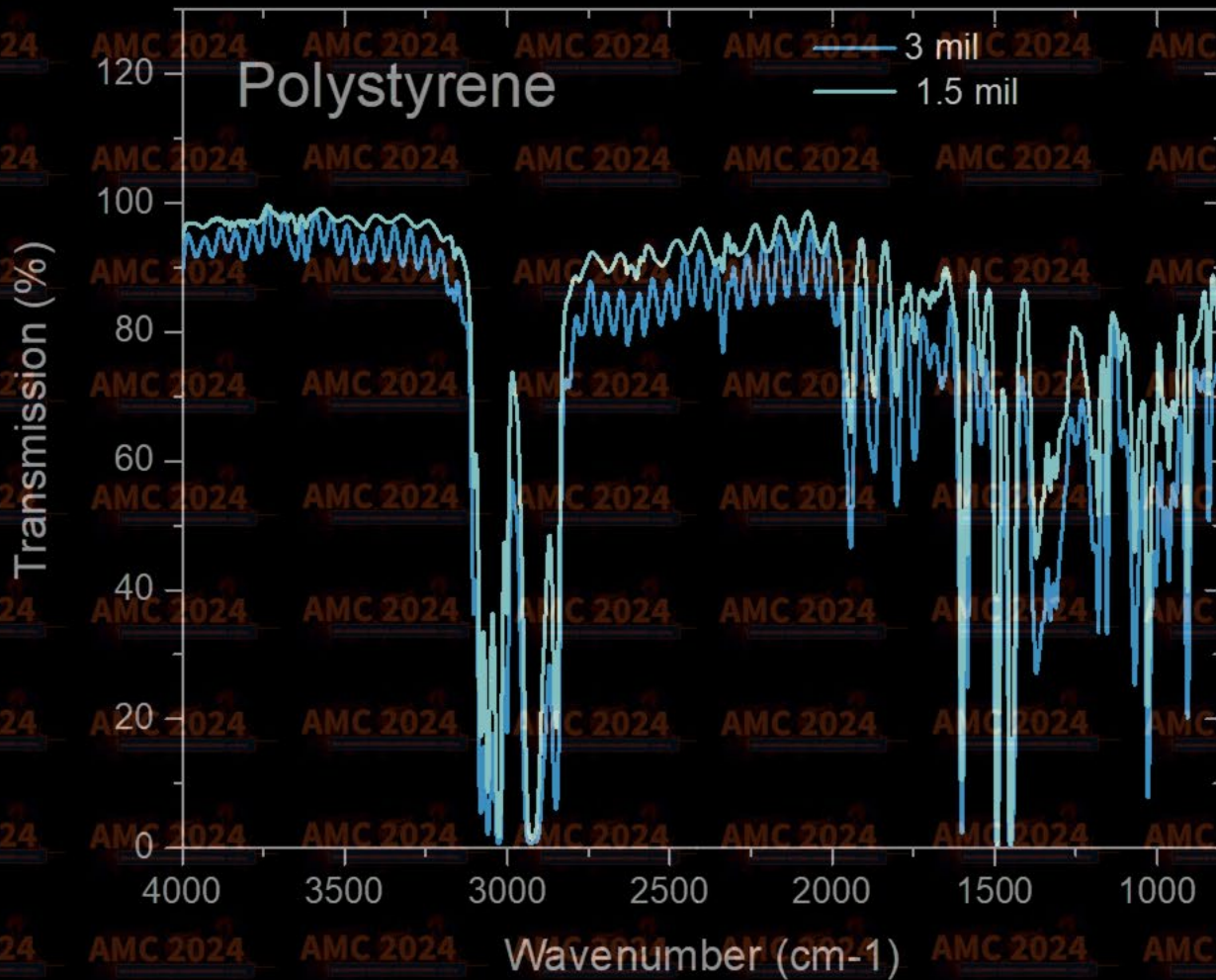
$2\text{ Hz} + 3\text{ Hz}$



2.99 cycles/second



Fourier Transform IR spectroscopy (FTIR)

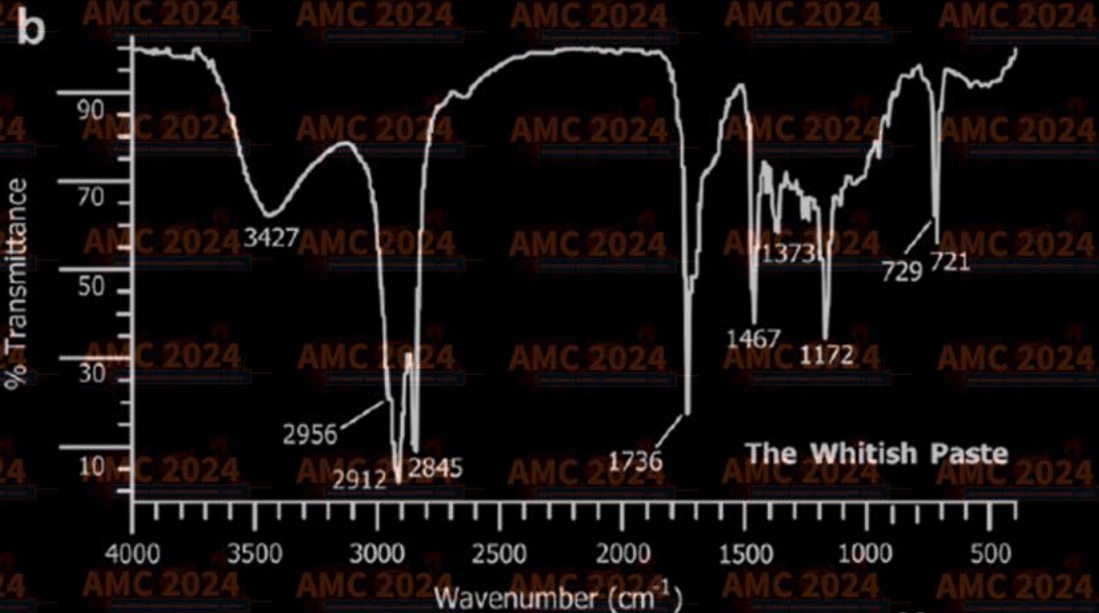
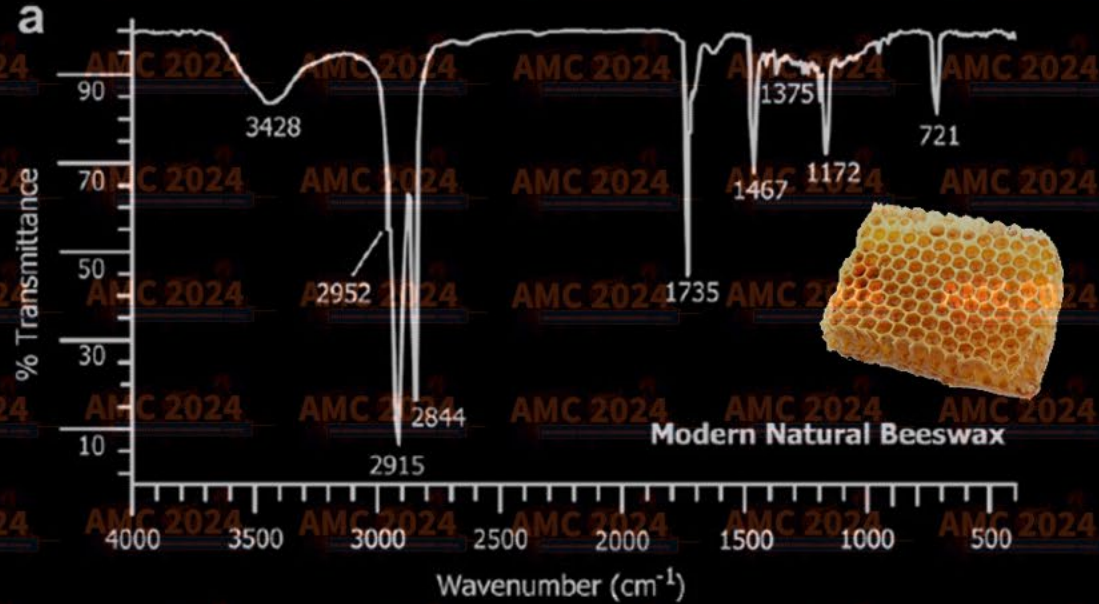
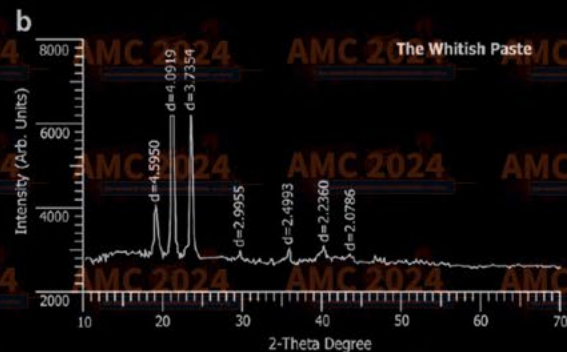
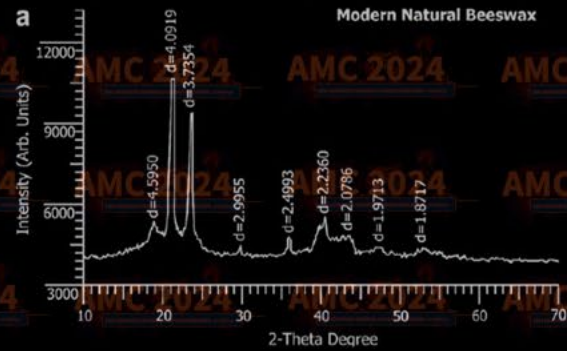
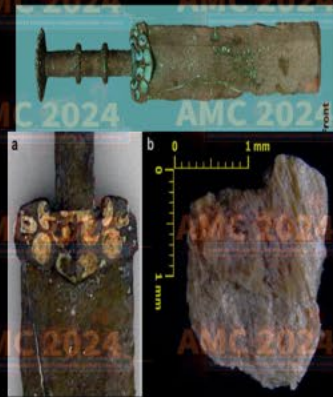


Fourier Transform IR spectroscopy (FTIR)

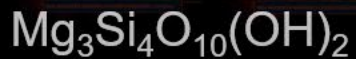
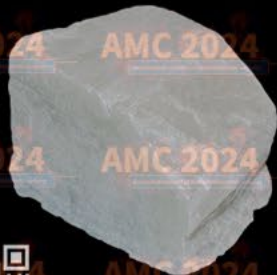
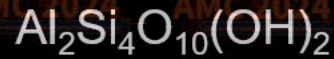
FTIR can be used to identify components in a mixture by comparison with reference spectra.

Discovery of beeswax as binding agent on a 6th-century BC Chinese turquoise-inlaid bronze sword

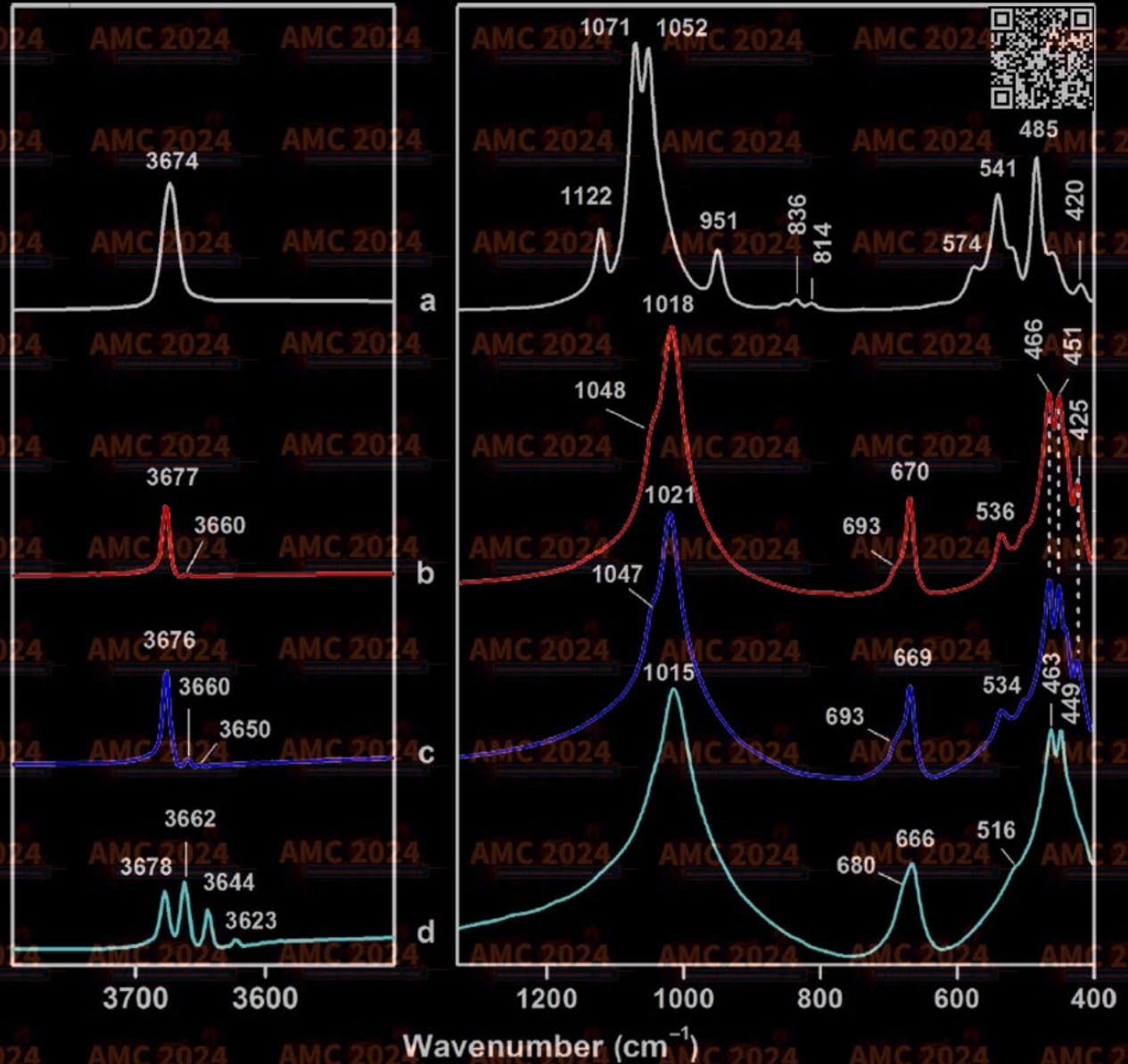
Wugan Luo, Tao Li, Changsui Wang, Fengchun Huang



Fourier Transform IR spectroscopy (FTIR)



Absorbance



Spectra from *Developments in Clay Science*, Vol. 8. Ch. 5



Spectrophotometry (UV-VIS-NIR) and FTIR



Strengths:

- Very little or simple sample preparation.
- Simplicity of use and data interpretation.
- Short acquisition time, for most cases.
- Non destructive.
- Broad range of photon energies.
- High sensitivity (~ 0.1 wt% typical for FTIR).

Complementary techniques:

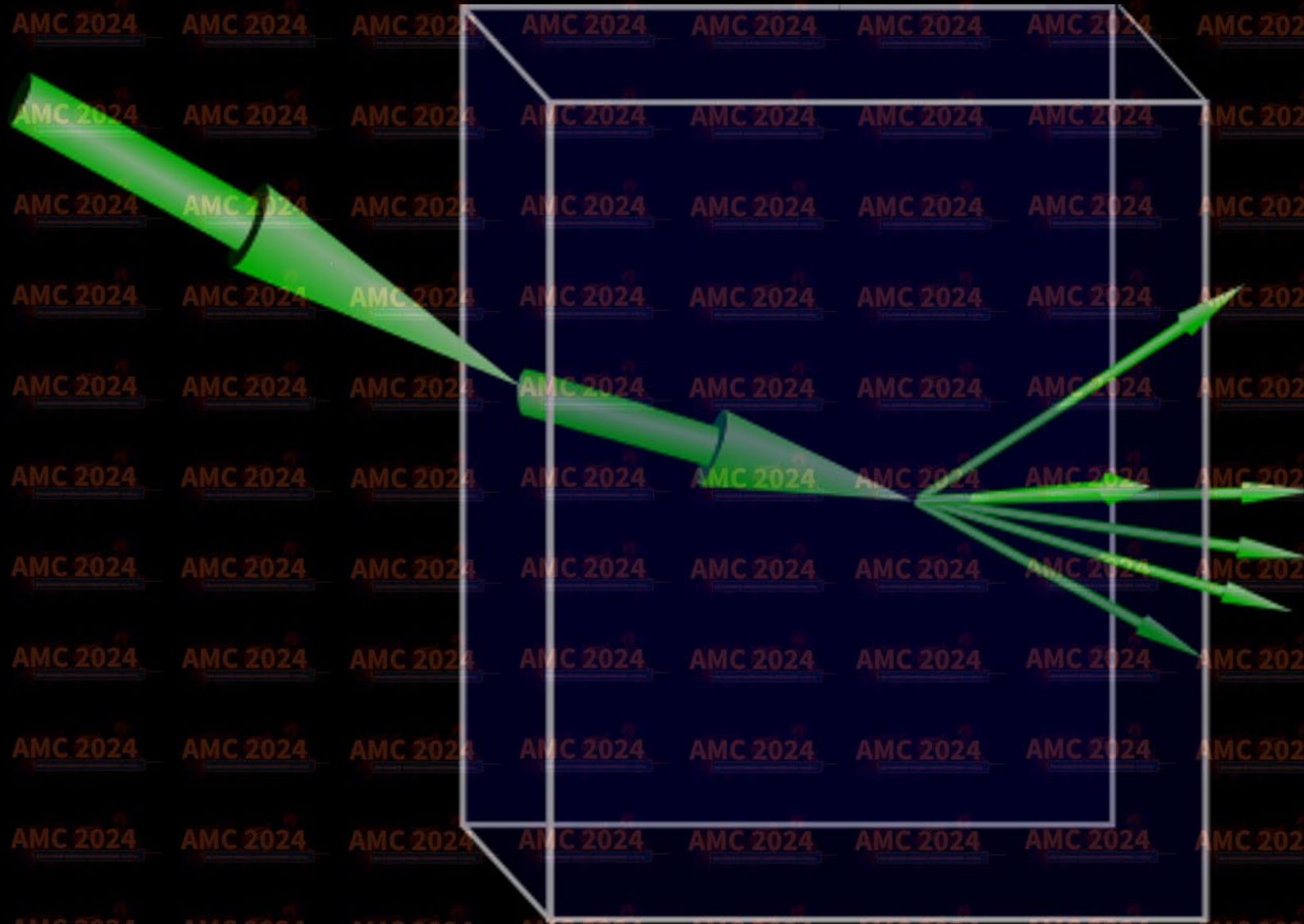
Raman, Electron Energy Loss Spectroscopy (EELS), Extended X-ray Absorption Fine Structure (EXAFS), XPS, Auger, SIMS, XRD, SFG.

Limitations:

- Reference sample is often needed for quantitative analysis.
- Many contributions to the spectrum are small and can be buried in the background.
- Usually, unambiguous chemical identification requires the use of complementary techniques.
- Limited spatial resolution.



Light scattering



Sir Chandrasekhara Venkata Raman



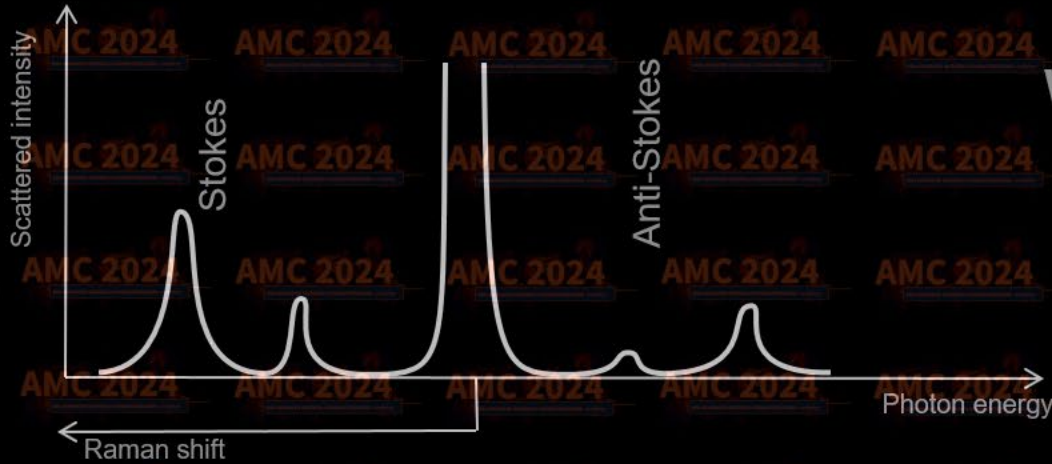
The Nobel Prize in Physics 1930 was awarded to Sir Venkata Raman *"for his work on the scattering of light and for the discovery of the effect named after him"*.



Sir Kariamanikkam Srinivasa Krishnan

Co-discoverer of Raman scattering, for which his mentor C. V. Raman was awarded the 1930 Nobel Prize in Physics

Raman spectroscopy



What is measured:

The light inelastically scattered by the material.

Basic principle:

The impinging light couples with the lattice vibrations (phonons) of the material, and a small portion of it is inelastically scattered. The difference between the energy of the scattered light and the incident beam is the energy absorbed or released by the phonons.

Excited state

Anti-Stokes

Rayleigh scattering

Stokes

Virtual states

Vibrational states

Ground state

Resonance Raman

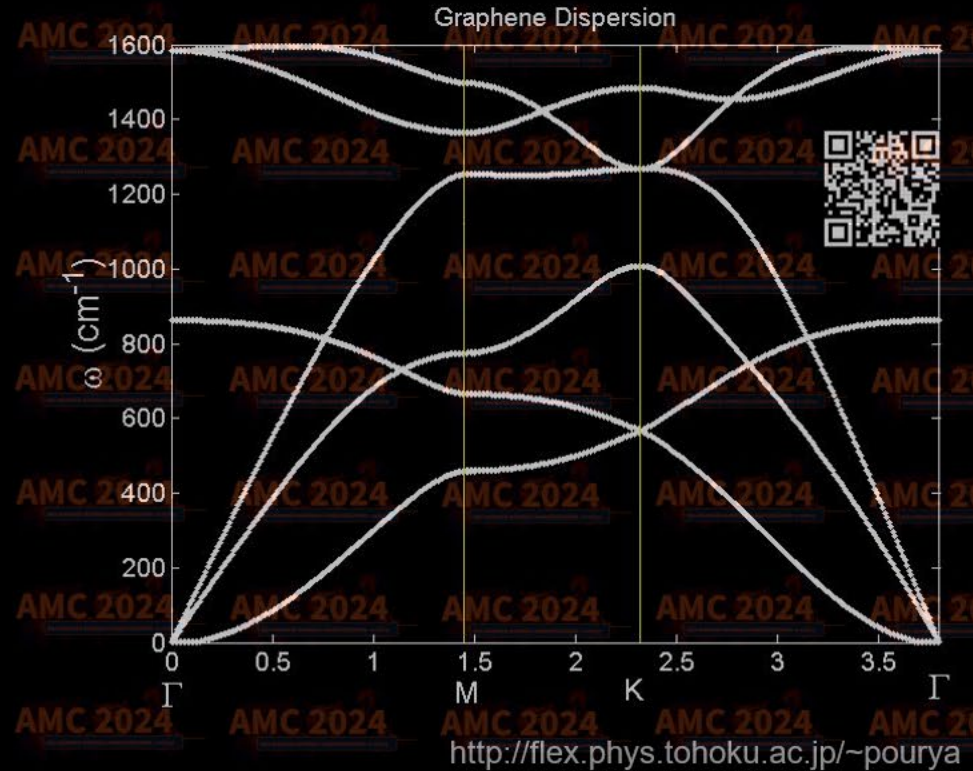
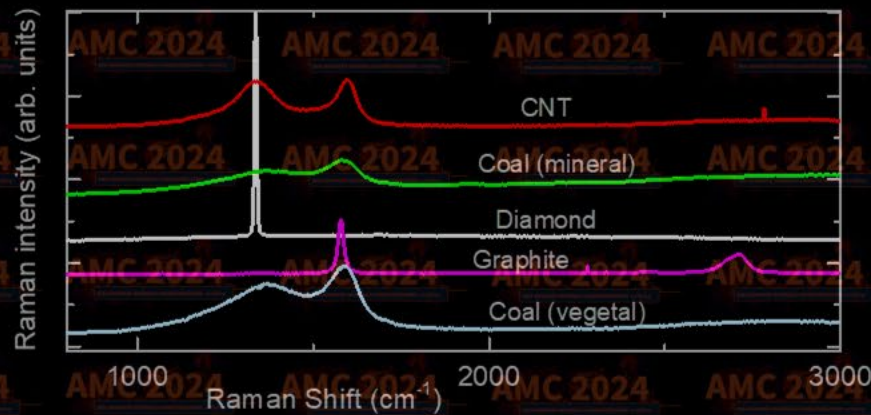
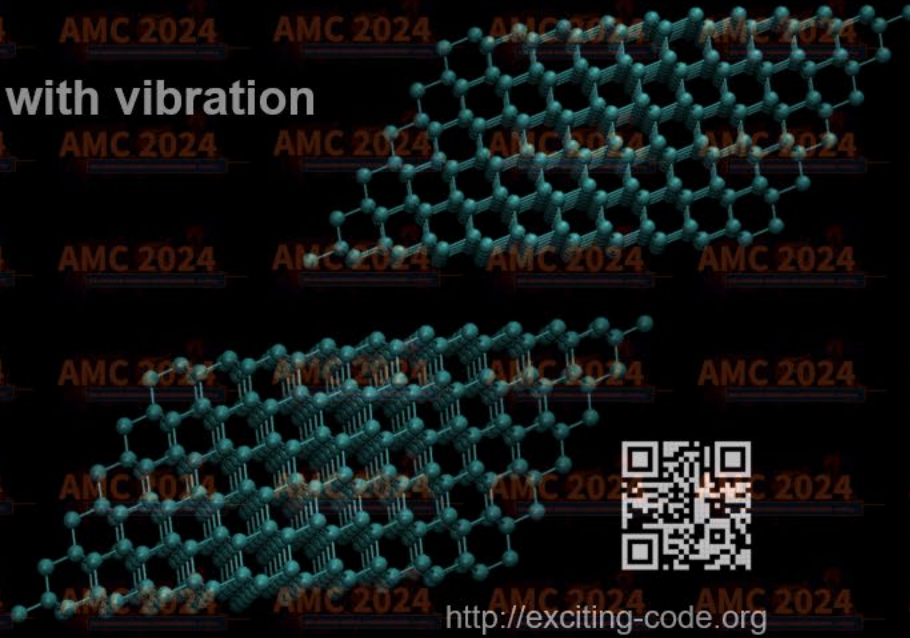
IR



Raman spectroscopy

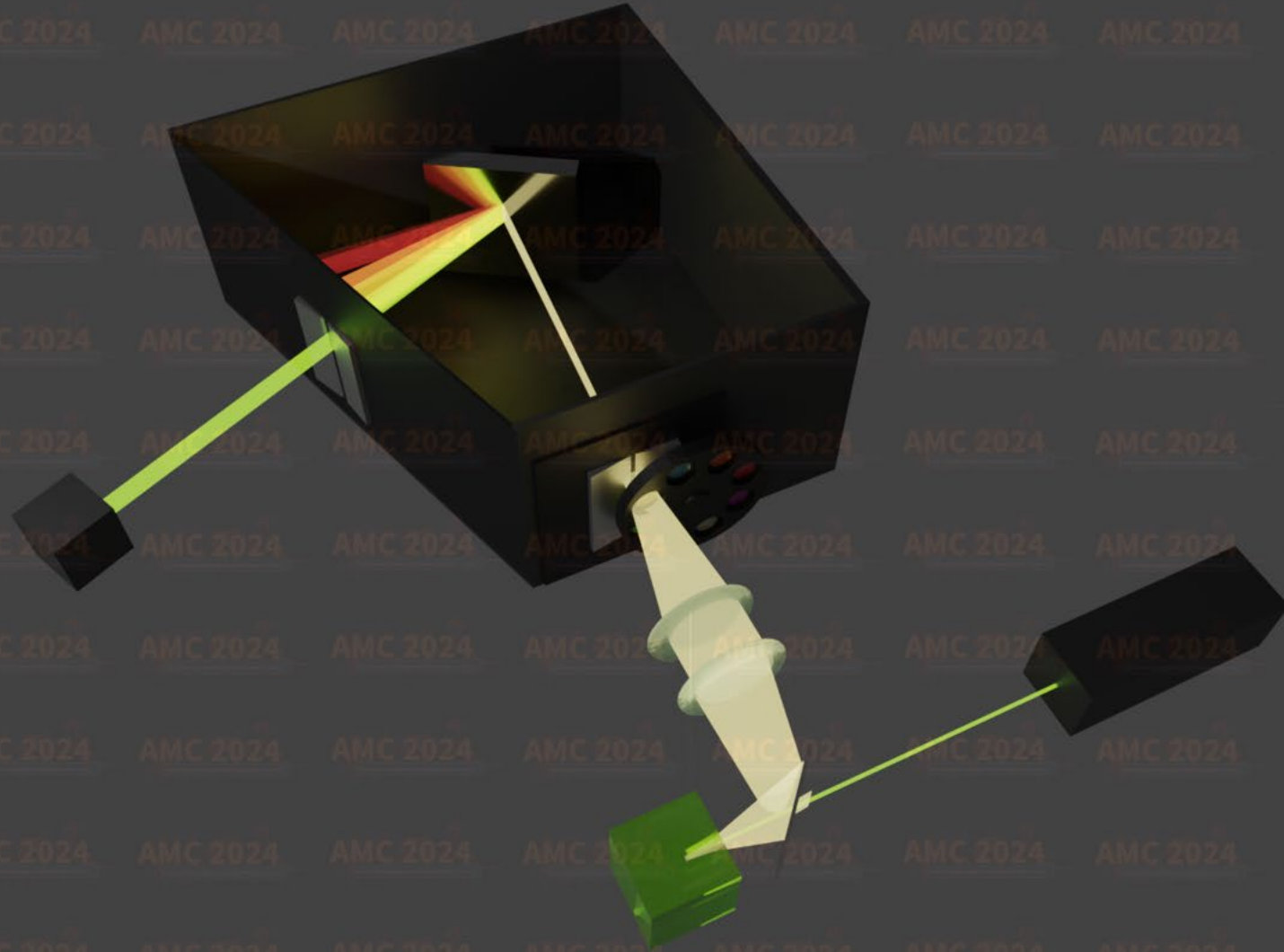
Impinging light couples with vibration modes of the material:

- Phonons
- Molecular vibrations



Raman spectroscopy

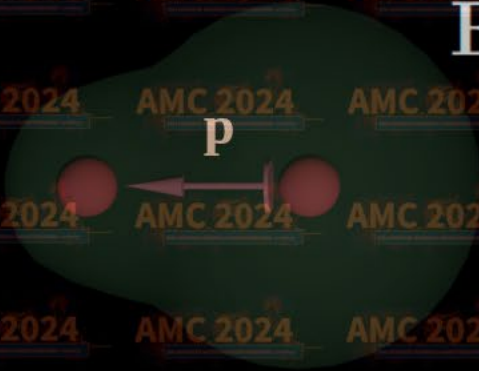
Instrumentation:



Raman spectroscopy



$$\mathbf{E} = \mathbf{E}_0 \cdot \cos(2\pi \cdot \nu_0 \cdot t)$$



$$\mathbf{p} = \alpha \cdot \mathbf{E} + \frac{1}{2} \cdot \beta \cdot \mathbf{E}^2 + \frac{1}{6} \cdot \gamma \cdot \mathbf{E}^3 + \dots$$

$$\alpha \sim 10^{10} \cdot \beta \sim 10^{20} \cdot \gamma$$

$$\mathbf{p} = \alpha \cdot \mathbf{E}_0 \cdot \cos(2\pi \cdot \nu_0 \cdot t)$$

Raman spectroscopy

The α tensor is dependent on the shape, strength, and dimensions of the chemical bond. Since chemical bonds change during vibrations, α is dependent on the vibrations of the molecule:

$$Q_k = Q_{k0} \cdot \cos(2\pi \cdot \nu_k \cdot t + \varphi_k)$$

$$\alpha = \alpha_o + \sum_k \left(\frac{\partial \alpha}{\partial Q_k} \right)_0 \cdot Q_k$$

$$\alpha_k = \alpha_0 + \alpha'_k \cdot Q_k$$

$$\alpha_k = \alpha_0 + \alpha'_k \cdot Q_{k0} \cdot \cos(2\pi \cdot \nu_k \cdot t + \varphi_k)$$

$$\mathbf{p} = \alpha_0 \cdot \mathbf{E}_0 \cdot \cos(2\pi \cdot \nu_0 \cdot t) +$$

$$+ \frac{1}{2} \cdot \alpha'_k \cdot Q_{k0} \cdot \mathbf{E}_0 \cdot [\cos(2\pi \cdot t \cdot (\nu_0 + \nu_k) + \varphi_k) +$$

$$+ \cos(2\pi \cdot t \cdot (\nu_0 - \nu_k) - \varphi_k)]$$

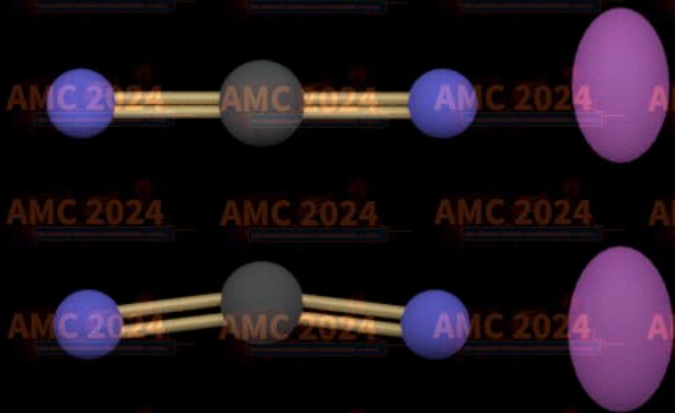
$$\alpha'_k = \left(\frac{\partial \alpha}{\partial Q_k} \right)_0 \neq 0$$

the dipole oscillates with three frequencies simultaneously, corresponding to the three possible scattering modes (Rayleigh, Stokes Raman and anti-Stokes Raman)

Raman spectroscopy

$$\alpha'_k = \left(\frac{\partial \alpha}{\partial Q_k} \right)_0 \neq 0$$

Raman active



$$\left. \frac{\partial \alpha}{\partial \xi} \right|_{\xi=0} \neq 0$$



$$\left. \frac{\partial \alpha}{\partial \xi} \right|_{\xi=0} = 0$$



Fourier Transform IR spectroscopy (FTIR)

IR active vibrations



Raman spectroscopy

Raman active vibrations

The intensity of the Raman scattering linked to a vibrational state depends on the change in the polarizability tensor



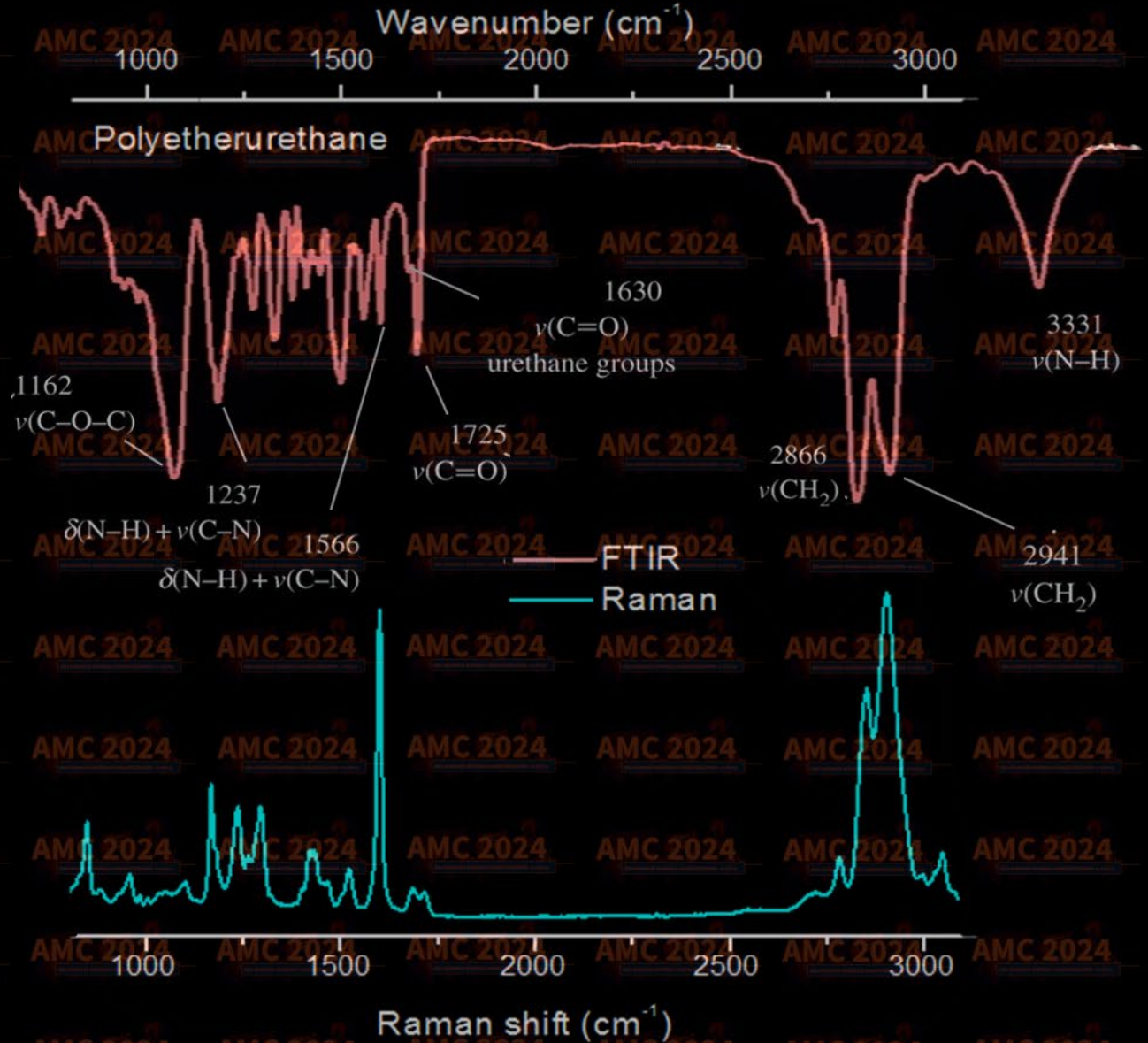
Raman spectroscopy

FTIR and Raman:

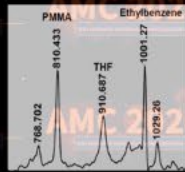
The two techniques are complementary
(different selection rules).

$$\Delta\mu \neq 0$$

$$\alpha'_k = \left(\frac{\partial \alpha}{\partial Q_k} \right)_0 \neq 0$$



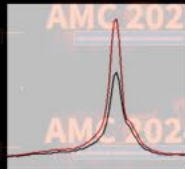
Studying the ... we can estimate ...



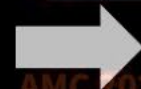
Characteristic Raman frequencies



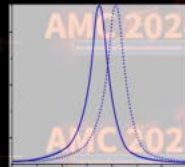
Identity and composition of materials



Raman peak intensity



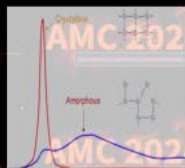
Volume of material probed



Raman peak frequency shift



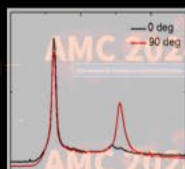
Strain, stress, crystal lattice distortion



Raman peak width



Crystallinity of material



Raman peak polarization dependency



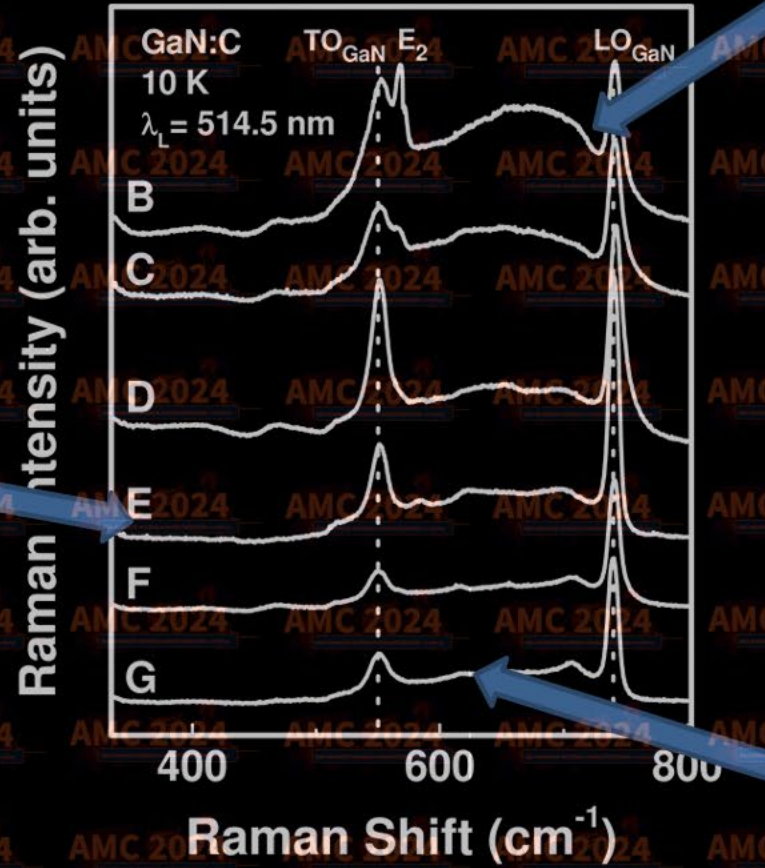
Crystal orientation and symmetry

Raman spectroscopy

Molecular and crystalline structure characterization

Presence of N vacancies yields poor crystallinity

Substitutional C fills N vacancies improving the crystallinity

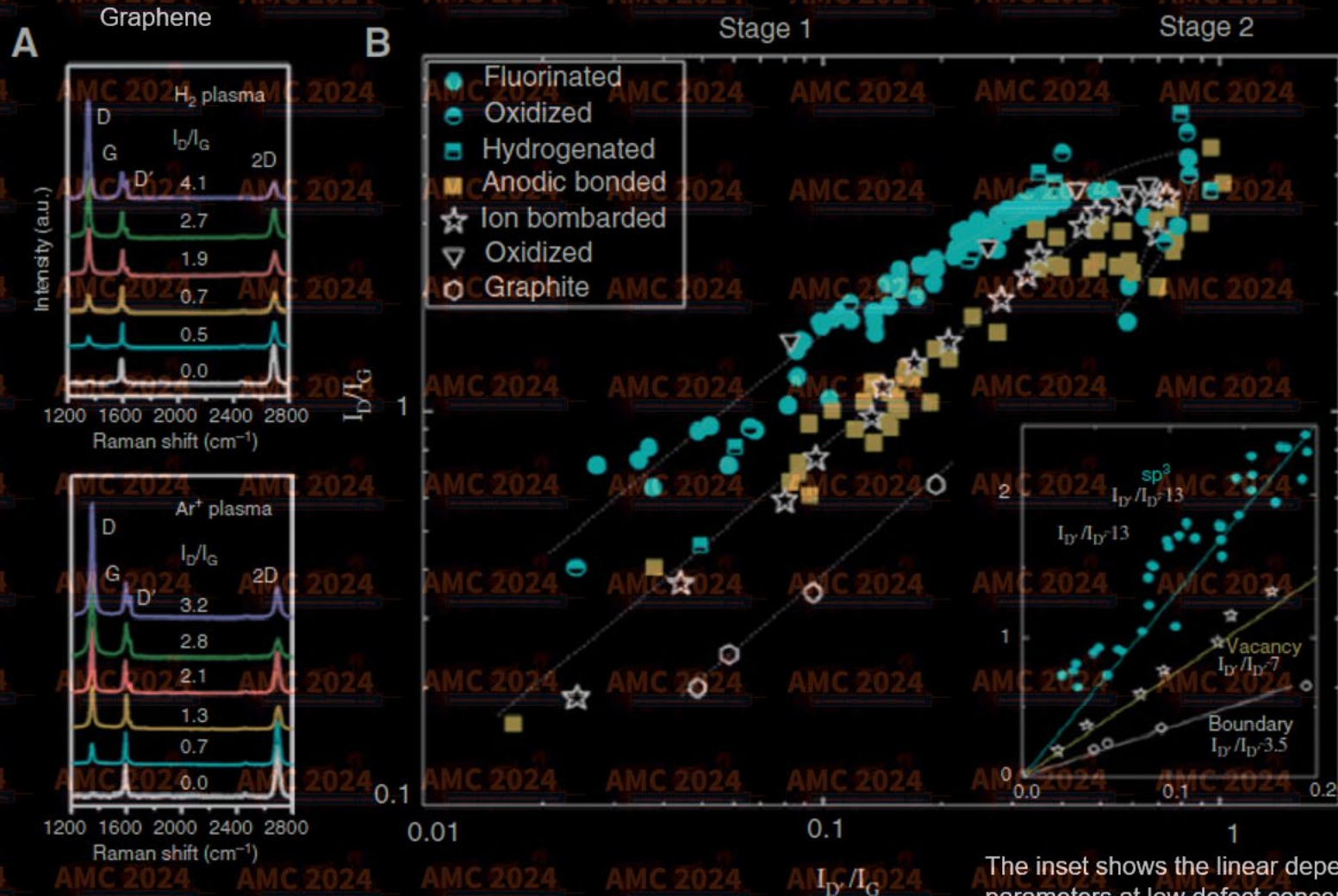


C incorporates interstitially causing a degradation of the crystal lattice

PHYSICAL REVIEW B 68, 155204 (2003)

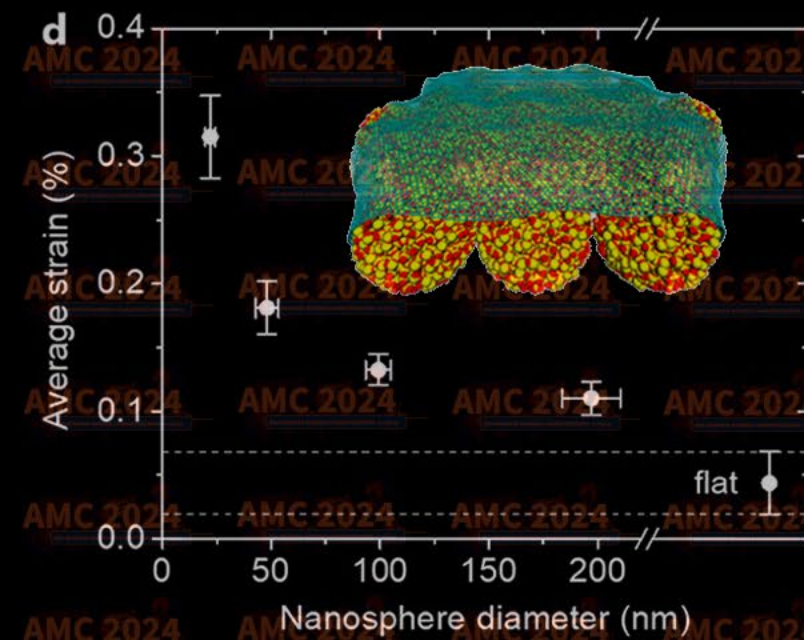
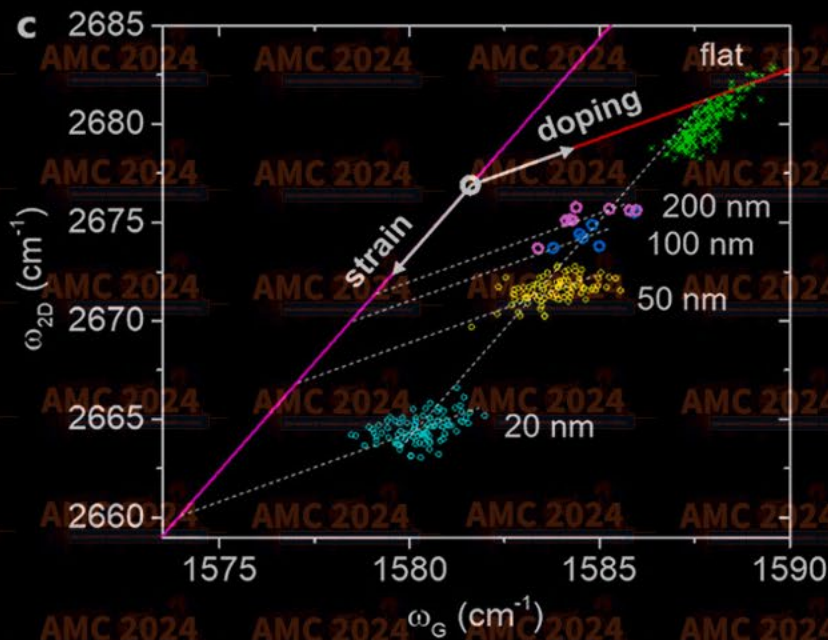
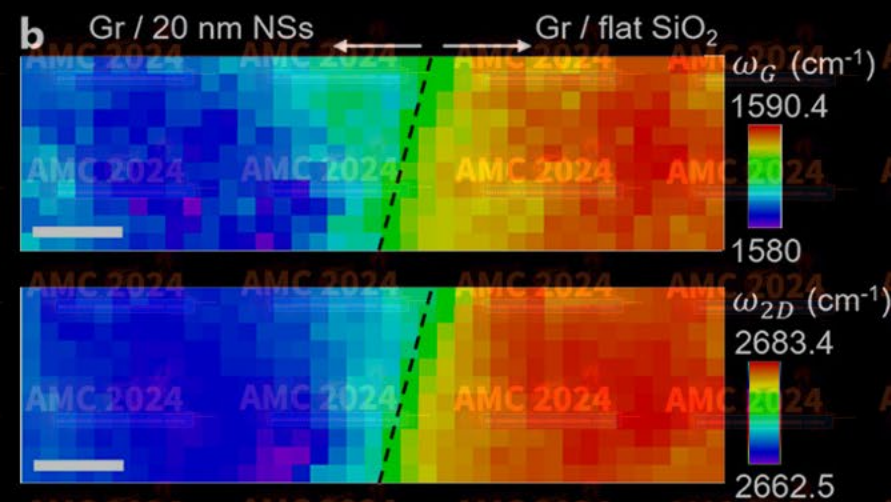
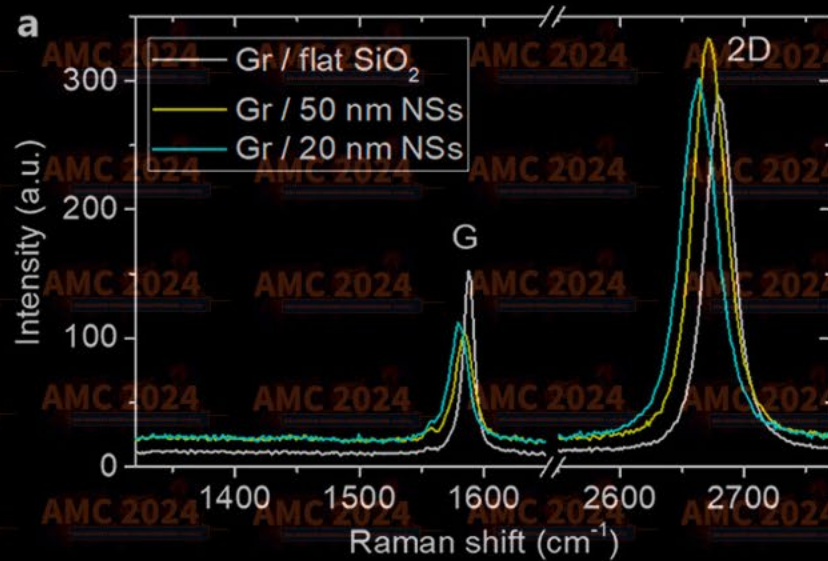


Crystalline structure and defect characterization



Raman spectroscopy

Strain/stress

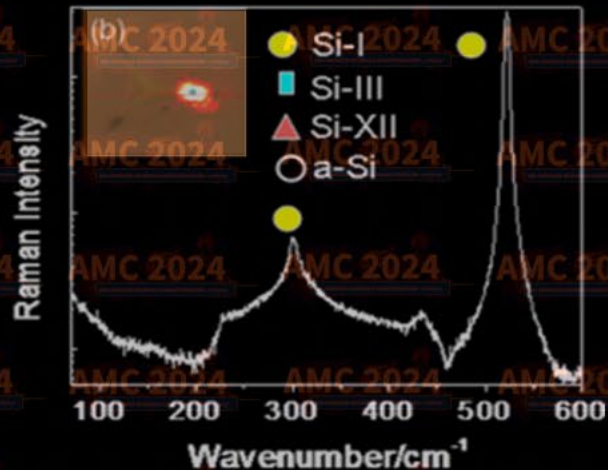


Raman spectroscopy

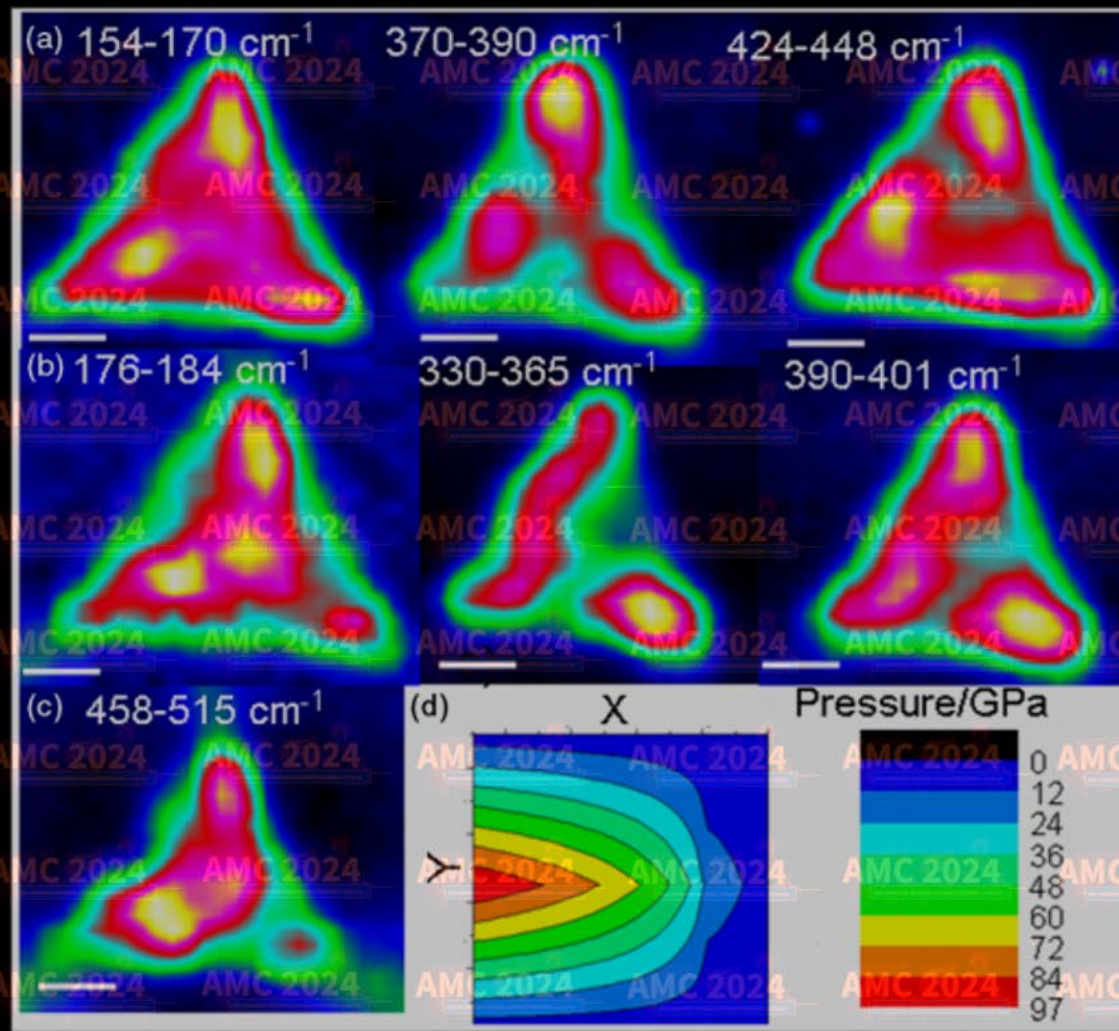
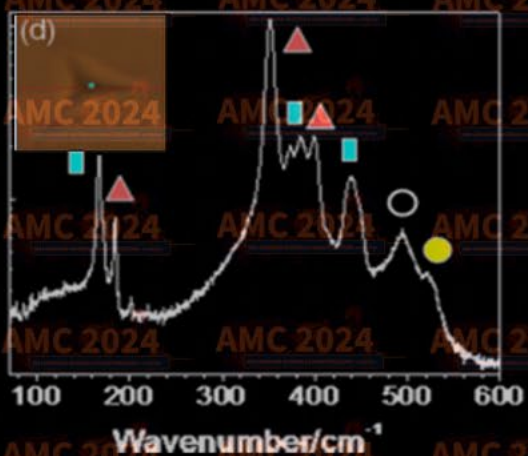
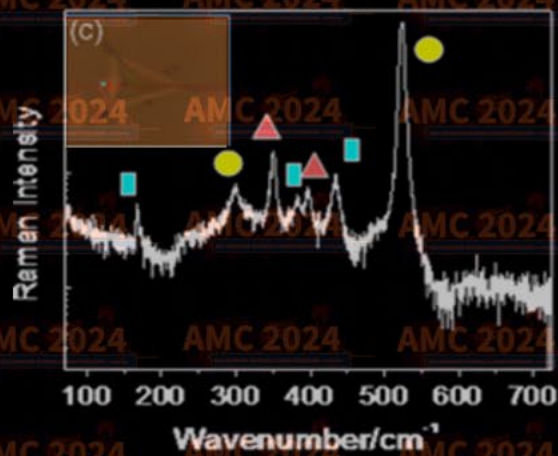
Phase transitions

(a) Different Raman Modes

Si-I (cm ⁻¹) [†]	Si-III (cm ⁻¹) [†]	Si-XII (cm ⁻¹) [†]
300, 520	166, 171	182
a-Si (cm ⁻¹) [†]	384	352
475, 510	432, 463	397



[†] Ref 2,3



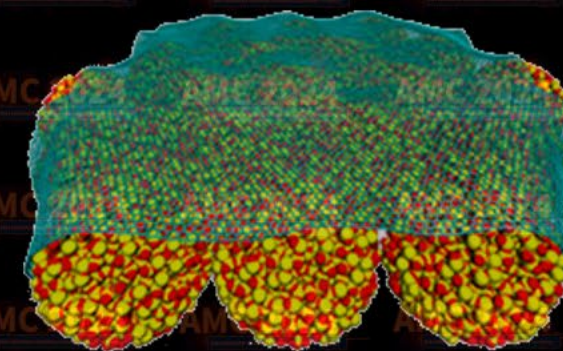
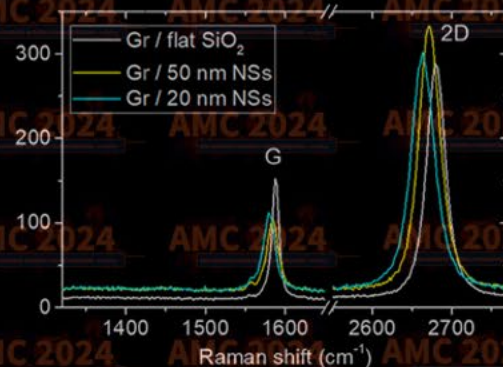
J. Raman Spectroscopy 41, 334 (2010)



Raman spectroscopy

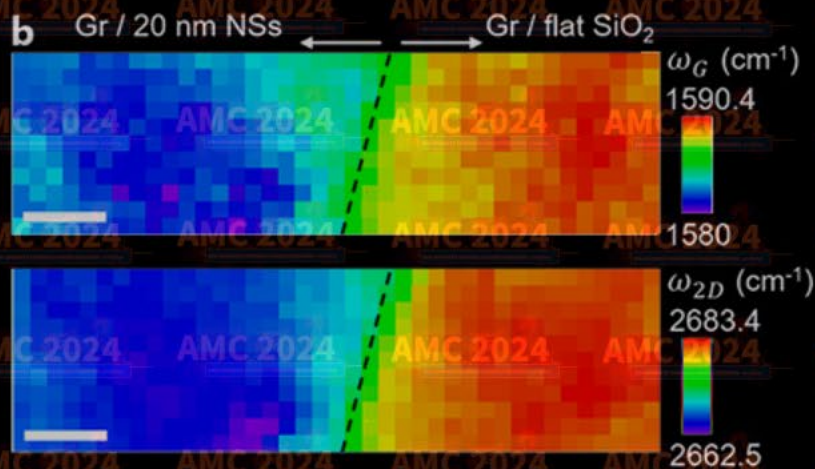
Primary Strengths:

- Very little sample preparation.
- Structural characterization.
- Non-destructive technique.
- Chemical information.
- Complementary to FTIR.



Primary Limitations:

- Expensive apparatus (for high spectral/spatial resolution and sensitivity).
- Weak signal, compared to fluorescence.
- Limited spatial resolution (diffraction limited).



Complementary techniques:

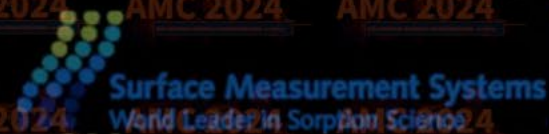
FTIR, EELS, Mass spectroscopy, EXAFS, XPS, AES, SIMS, XRD, SFG.

Thanks to our sponsors

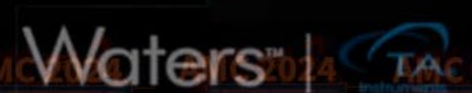
Platinum sponsors



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AMC 2024

2024 ADVANCED MATERIALS CHARACTERIZATION *workshop*

Optical Characterization Methods Part II

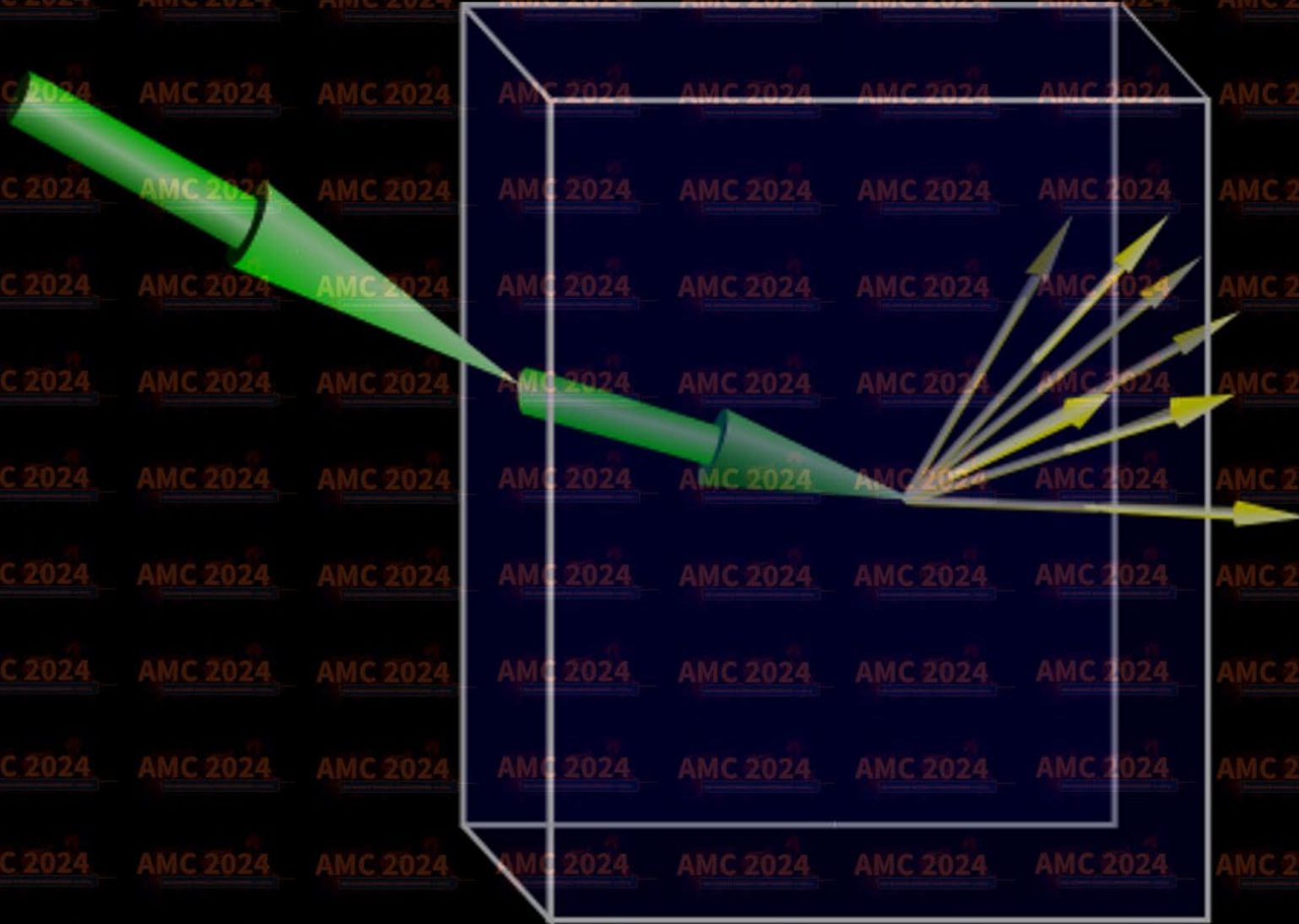
Julio A. N. T. Soares

Materials Research Laboratory
University of Illinois at Urbana-Champaign

go.illinois.edu/AMC2024



Luminescence



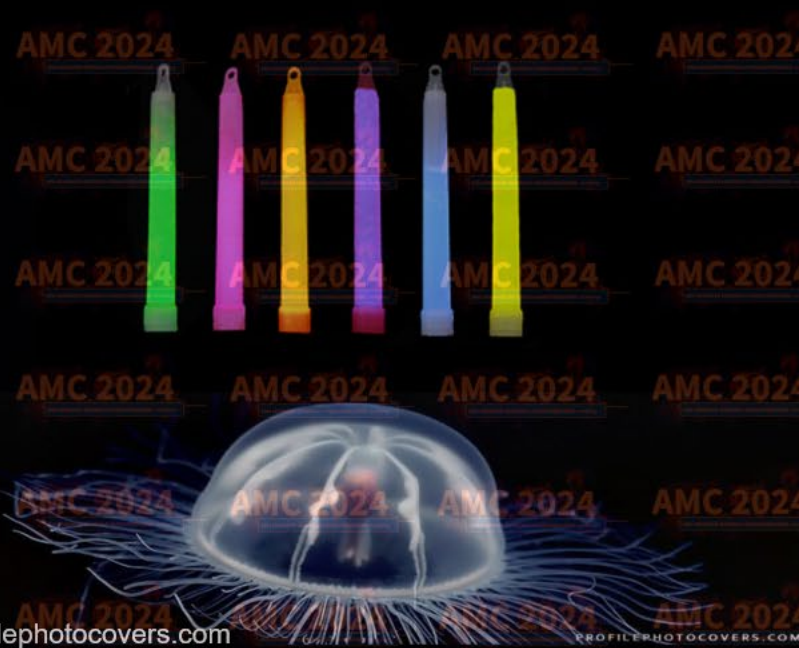
Luminescence

Lifetime: Phosphorescence, fluorescence

Mechanism: Photoluminescence, bioluminescence, chemoluminescence, thermoluminescence, piezoluminescence, etc.



Disney Pixar



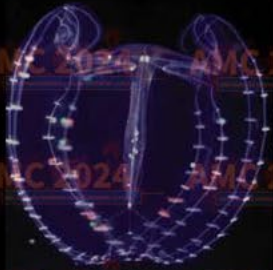
Charles Hedcock ©



Radim Schreiber



Profilephotocovers.com



Profilephotocovers.com

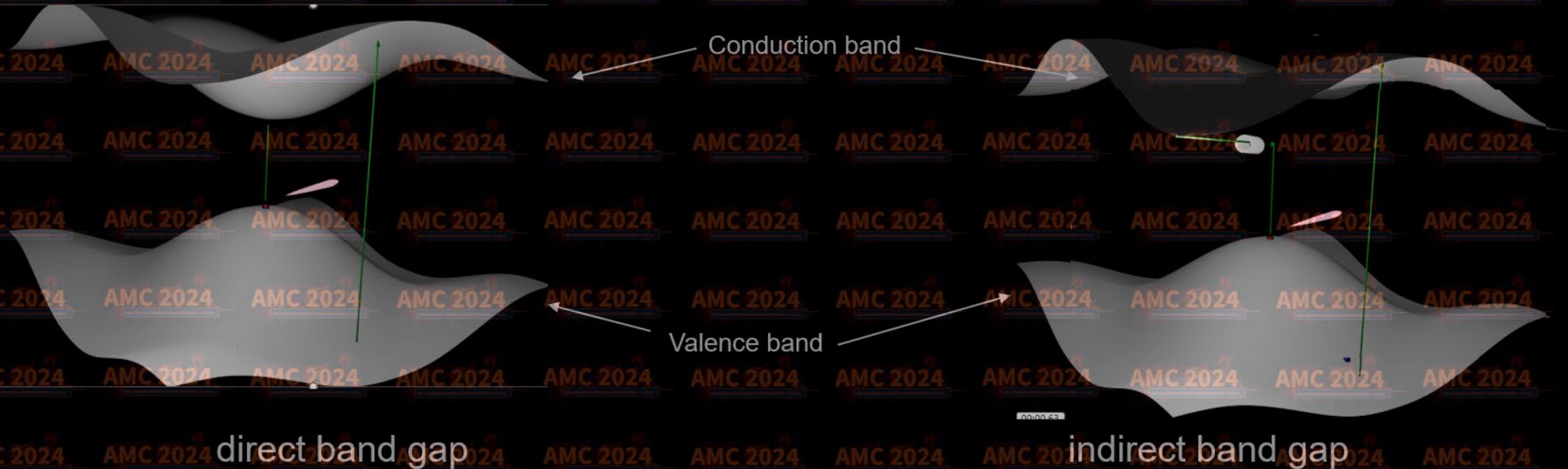


Photoluminescence

What is measured:

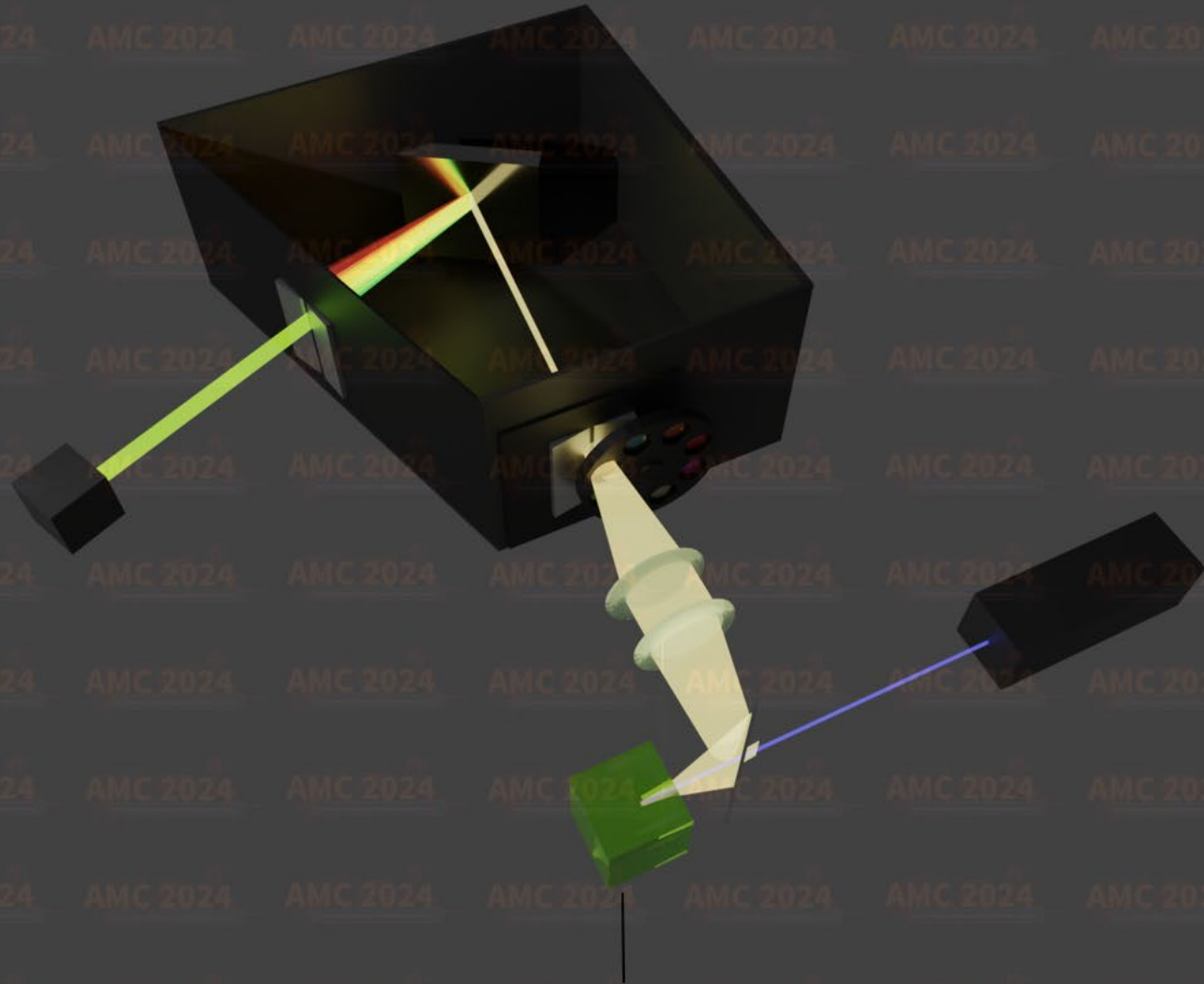
The emission spectra of materials due to radiative recombination following photo-excitation.

Basic principle:



Photoluminescence

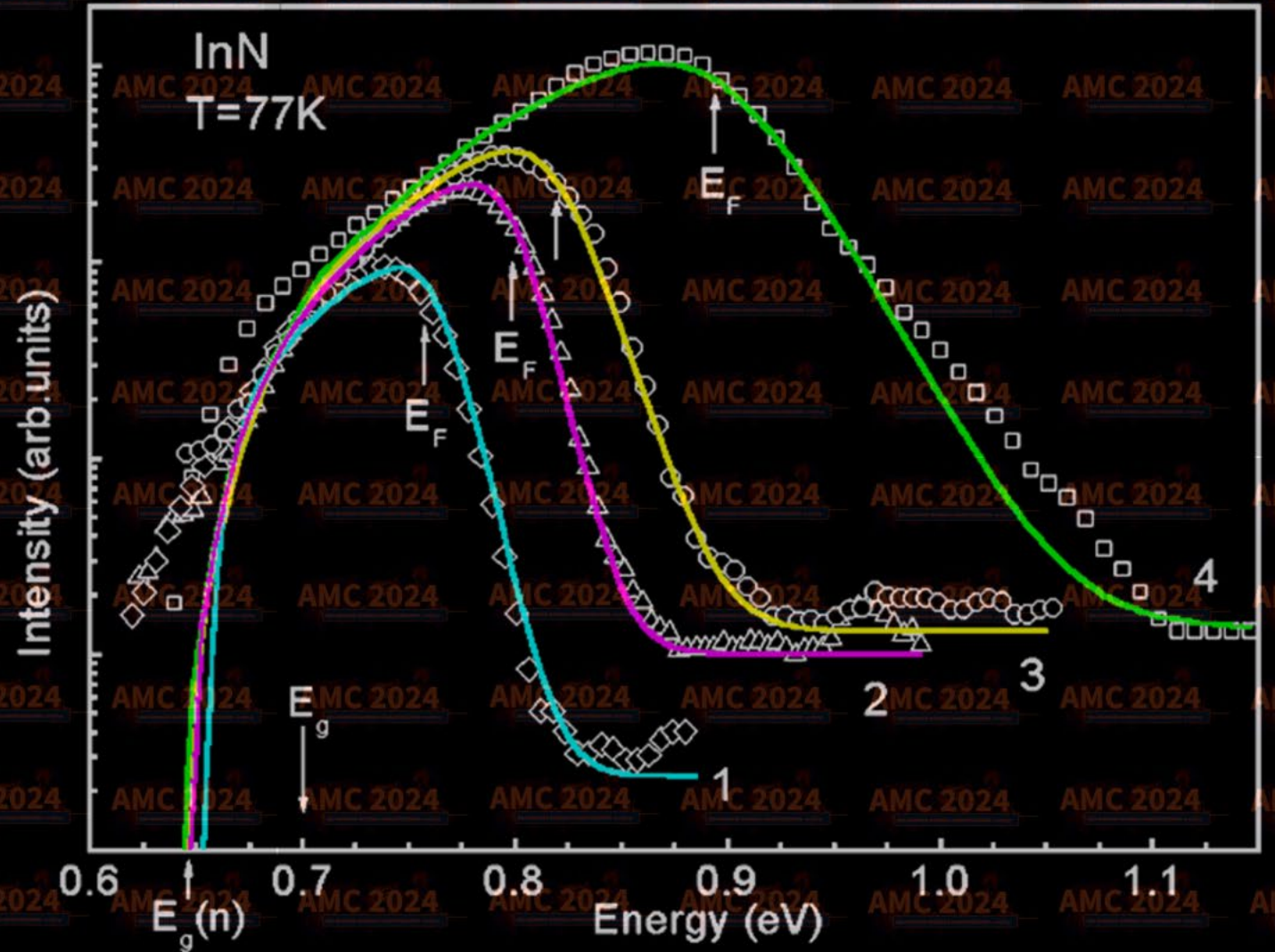
Instrumentation:



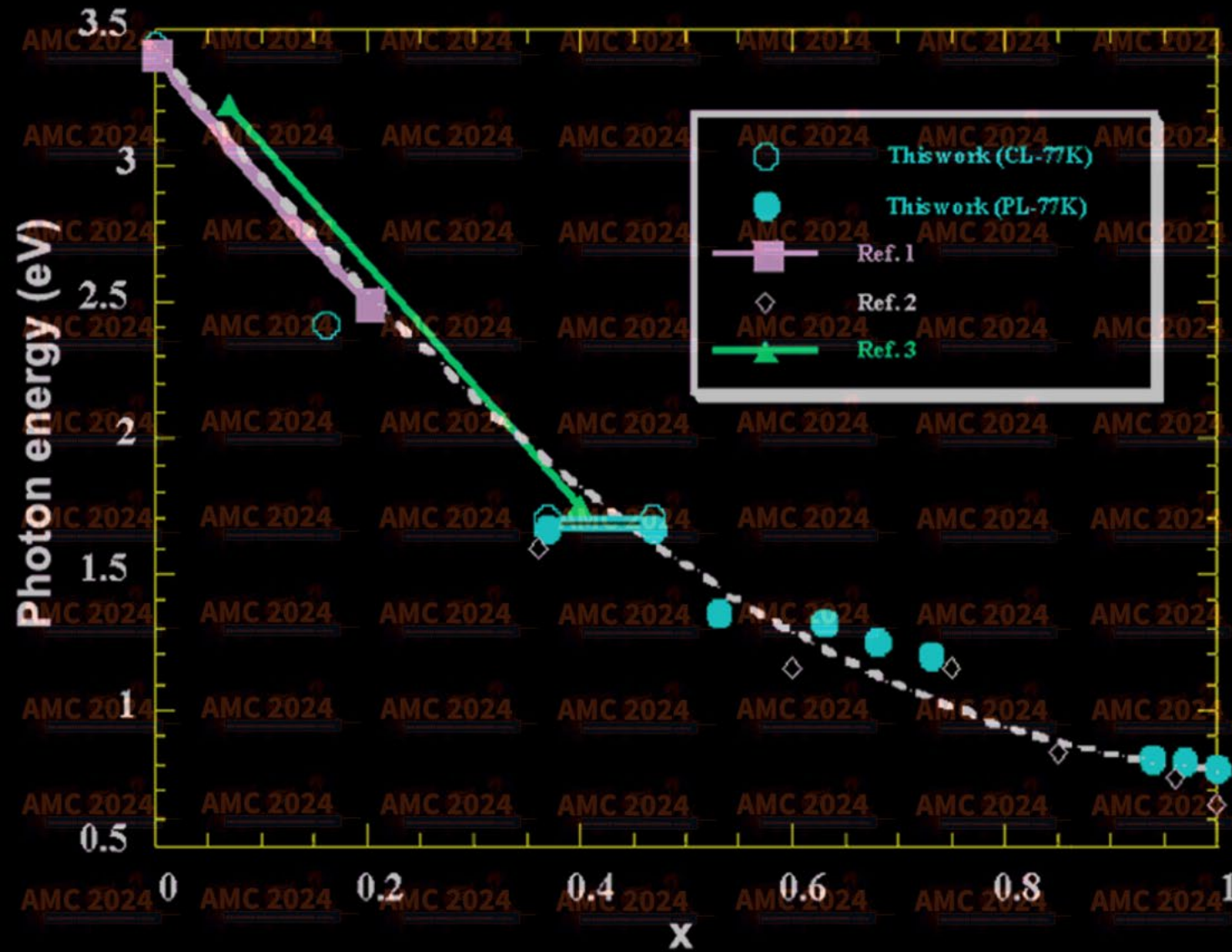
Carrier concentration

Photoluminescence spectra of InN layers with different carrier concentrations.

- 1 - $n = 6 \times 10^{18} \text{ cm}^{-3}$ (MOCVD);
- 2 - $n = 9 \times 10^{18} \text{ cm}^{-3}$ (MOMBE);
- 3 - $n = 1.1 \times 10^{19} \text{ cm}^{-3}$ (MOMBE);
- 4 - $n = 4.2 \times 10^{19} \text{ cm}^{-3}$ (PAMBE).



Photoluminescence



Alloy composition

$\text{In}_x\text{Ga}_{1-x}\text{N}$ alloys. Luminescence peak positions of cathodoluminescence and photoluminescence spectra vs. concentration x .

The plots of luminescence peak positions can be fitted to the curve

$$E_g(x) = 3.48 - 2.70x - bx(1-x)$$

with a bowing parameter of $b=2.3 \text{ eV}$

Ref.1 - Wetzel., *Appl. Phys. Lett.* **73**, 73 (1998).

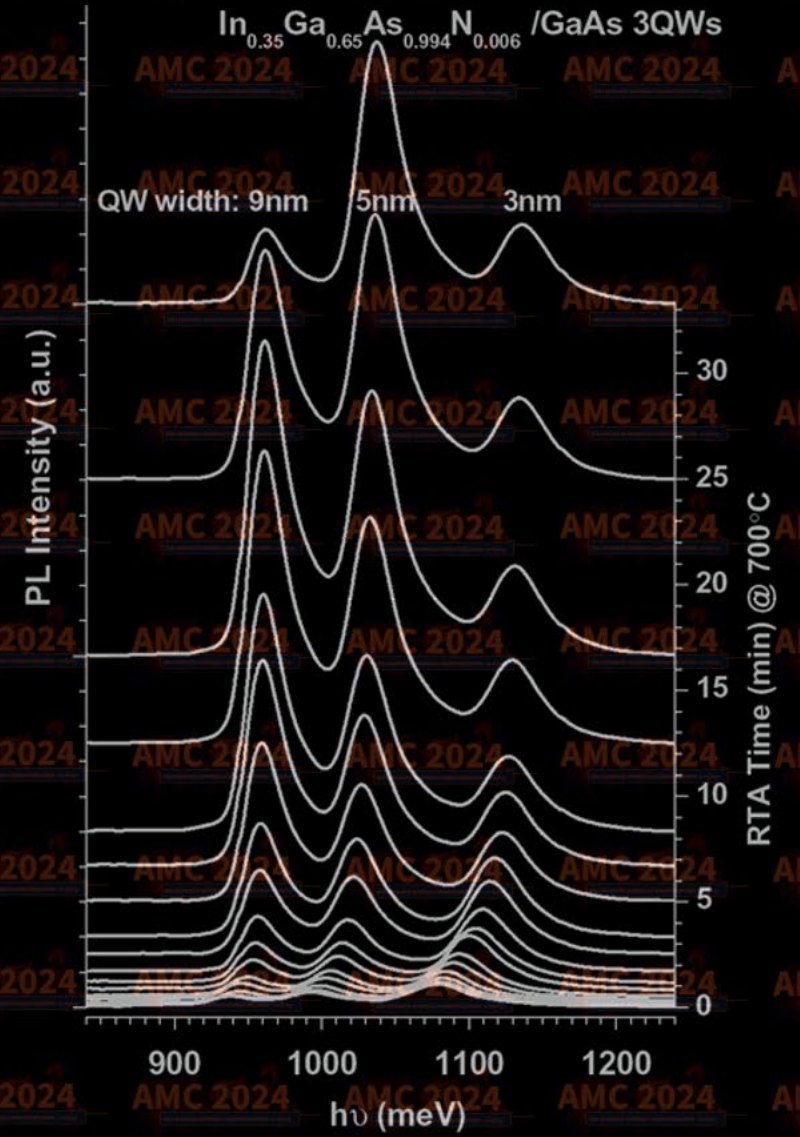
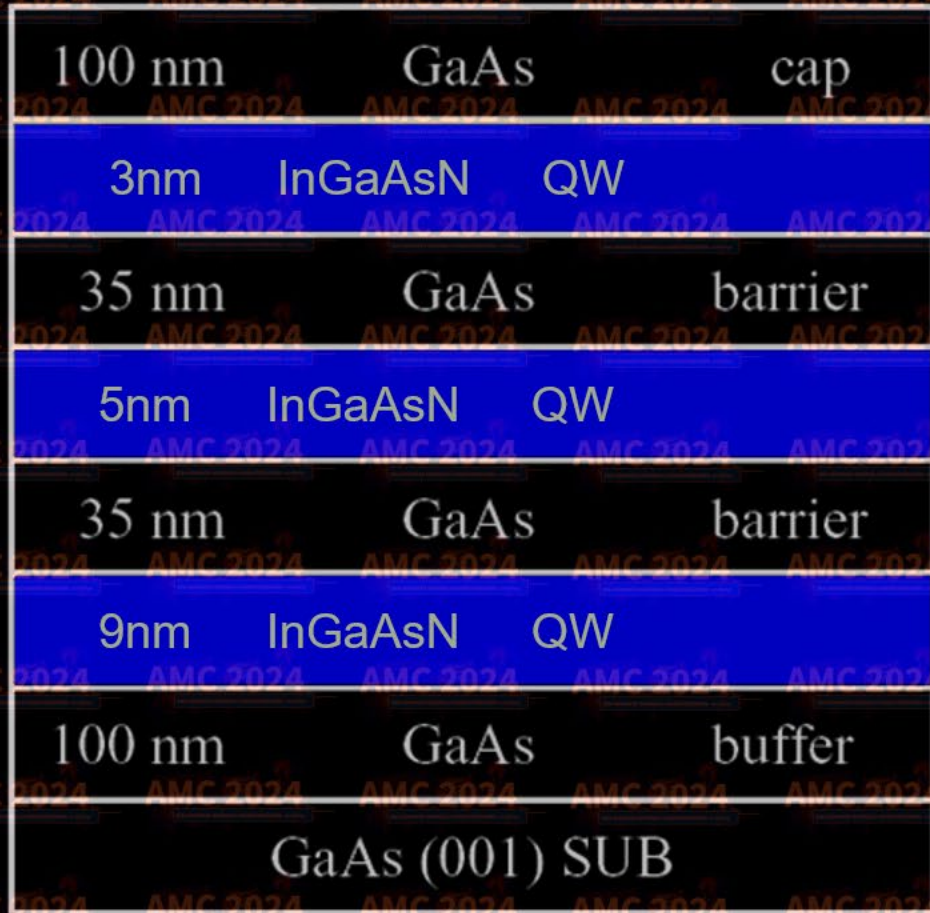
Ref.2 - V. Yu. Davydov., *Phys. Stat. Sol.* (b) **230**, R4 (2002).

Ref.3 - O'Donnel., *J. Phys. Condens. Matt.* **13**, 1994 (1998).

Extracted from *Phys. Stat. Sol.* (b) **234** (2002) 750

Width and quality of semiconductor quantum wells.

3-QWs

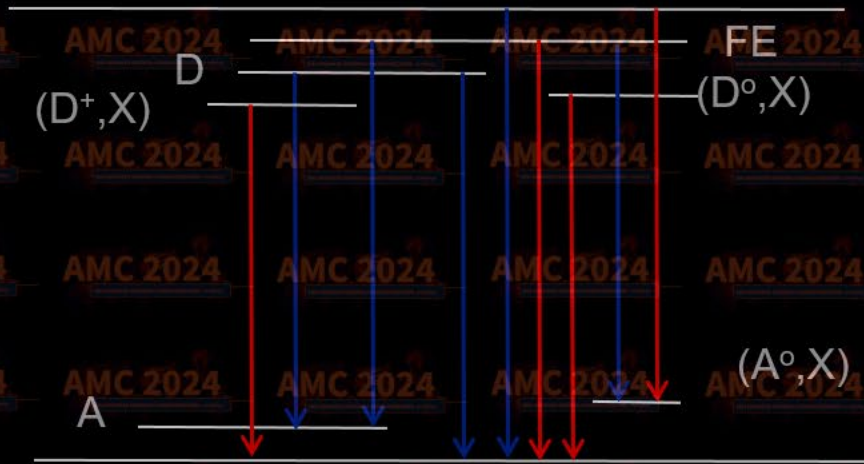


Journal of Crystal Growth 278 (2005) 259–263

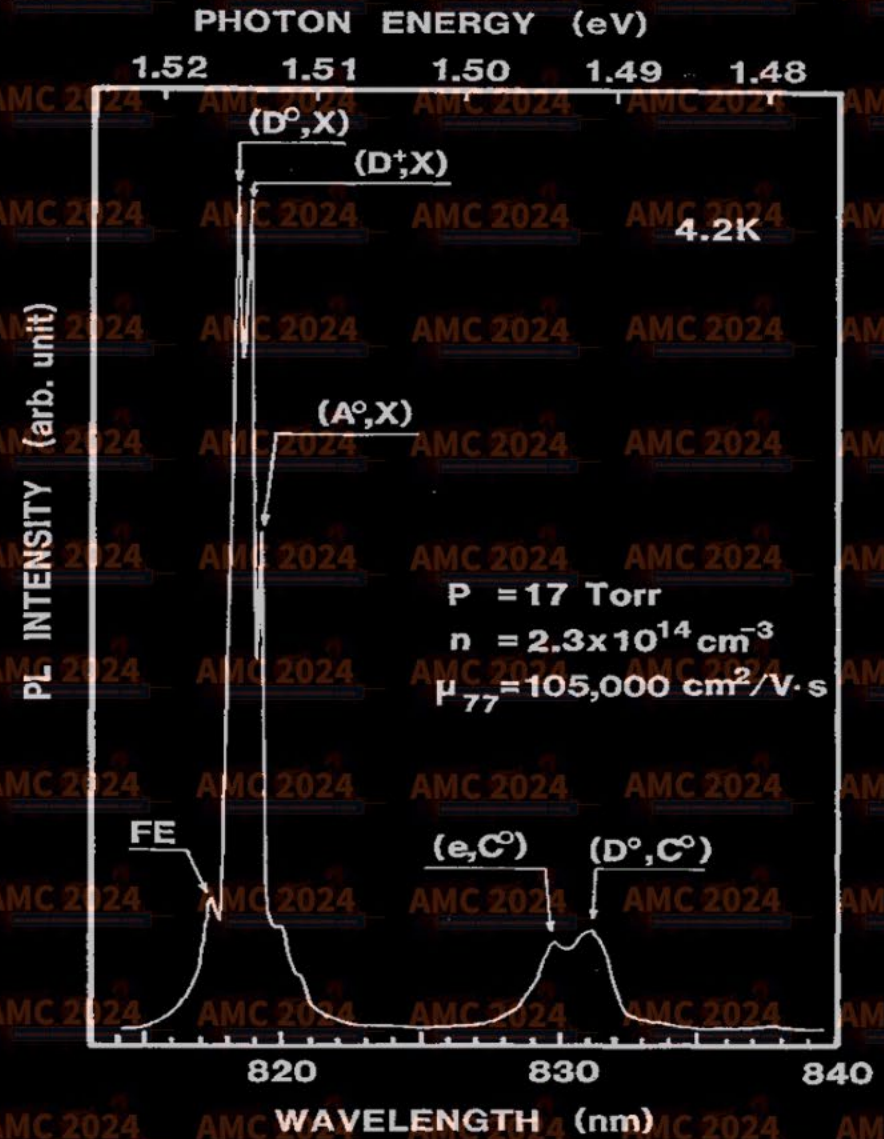
Photoluminescence

Defect luminescence in GaAs

Conduction band



Valence band



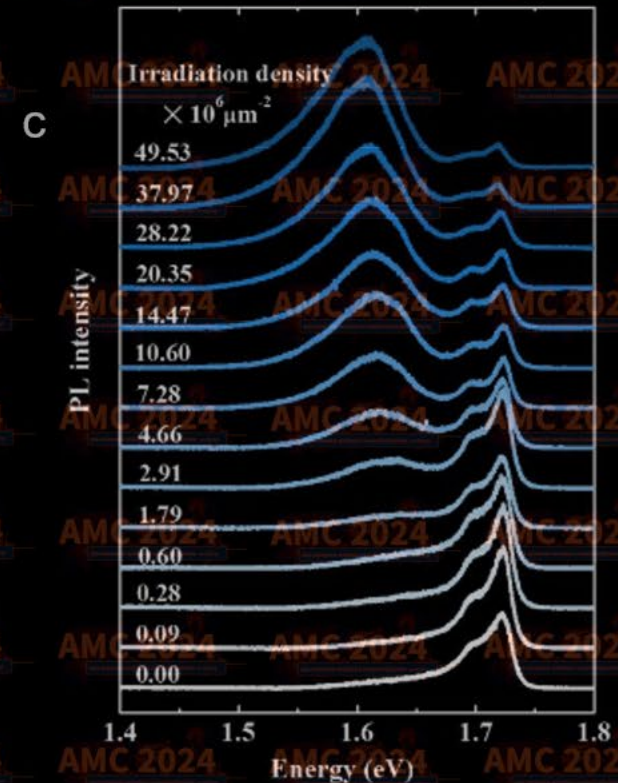
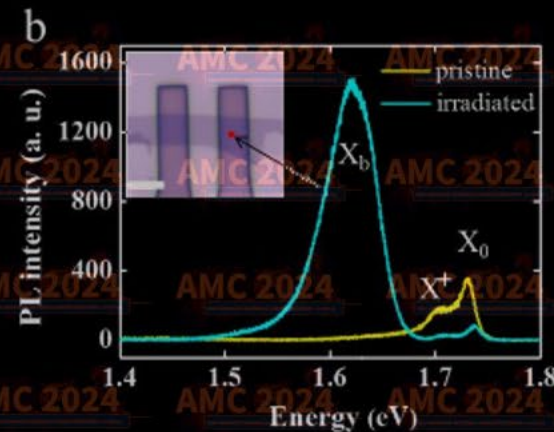
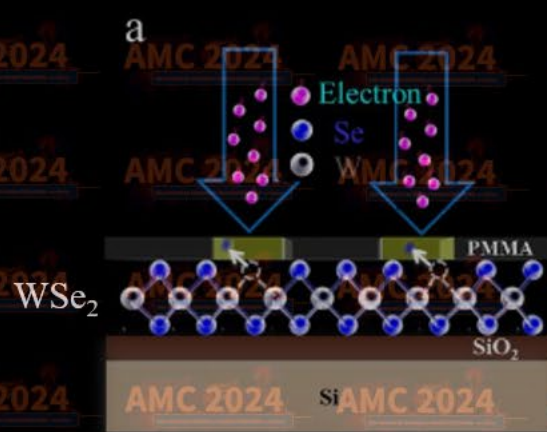
Jap. J. App. Phys. 23, L100 (1984)



Defects in 2D materials

Defect induced PL emission.

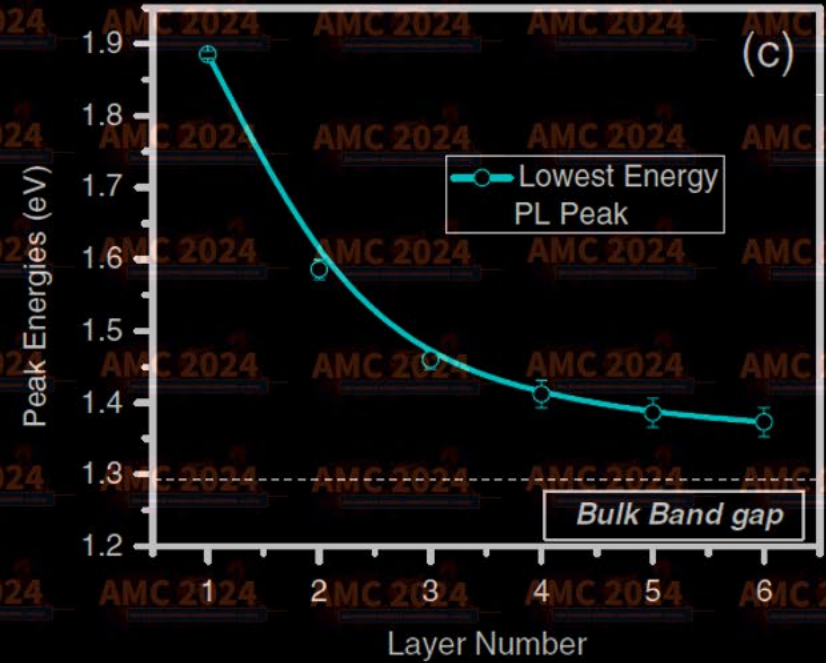
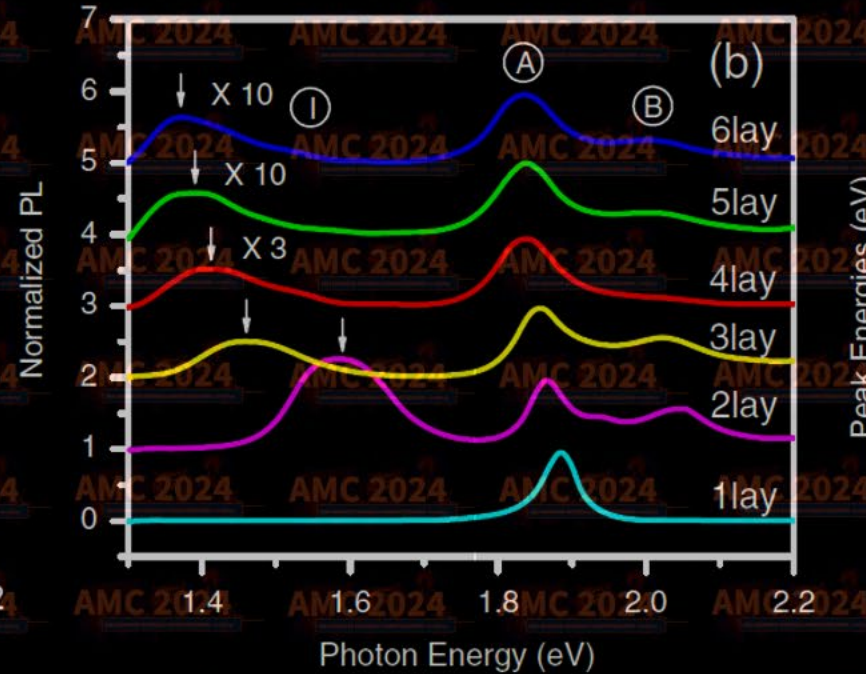
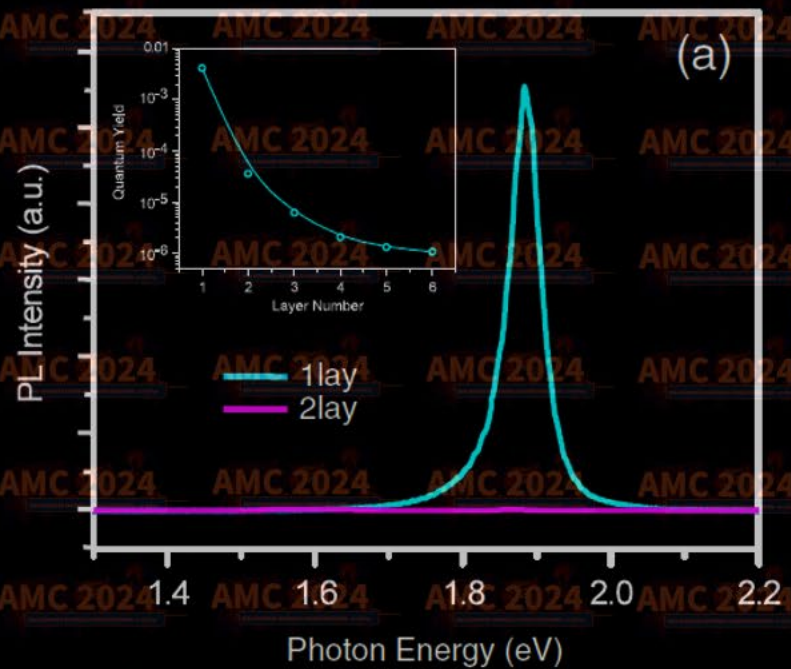
- Schematic diagram of electron beam irradiation on monolayer WSe₂ sample during the EBL process.
- PL spectrum of pristine monolayer WSe₂ and monolayer WSe₂ after EBL. The inset shows optical image of WSe₂ with PMMA patterned by EBL, scale bar is 5 μm
- PL spectra of a pristine WSe₂ under different e⁻ beam irradiation density.



arXiv:1608.02043

Number of layers in 2D materials

- PL spectra for mono- and bilayer MoS₂. Inset: PL QY of thin layers for N = 1–6.
- Normalized PL spectra by the intensity of peak A of thin layers of MoS₂ for N = 1–6. Feature I for N = 4–6 is magnified for clarity.
- Band-gap energy of thin layers of MoS₂, inferred from the energy of the PL feature I for N = 2–6 and from the energy of the PL peak A for N = 1. The dashed line represents the (indirect) band-gap energy of bulk MoS₂.

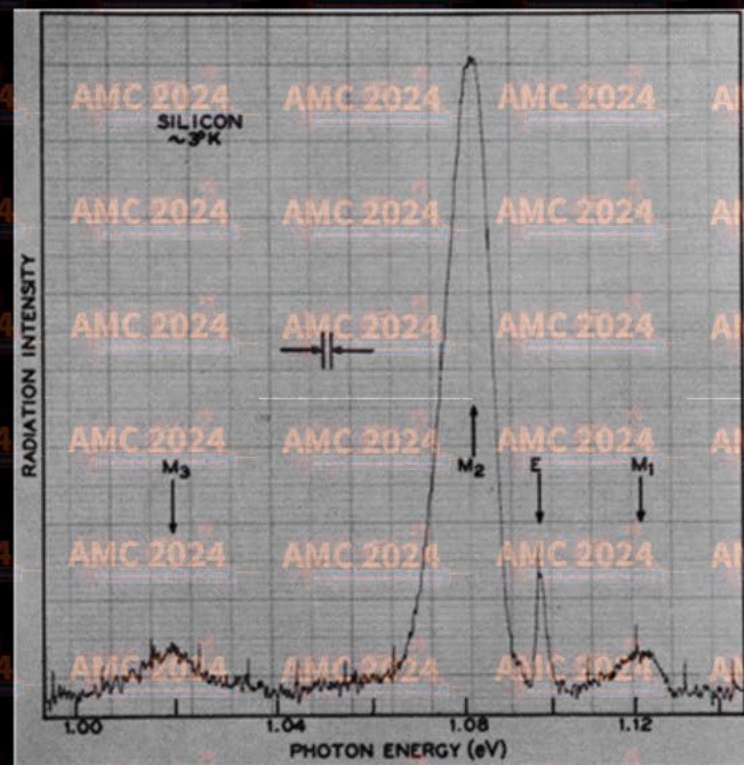
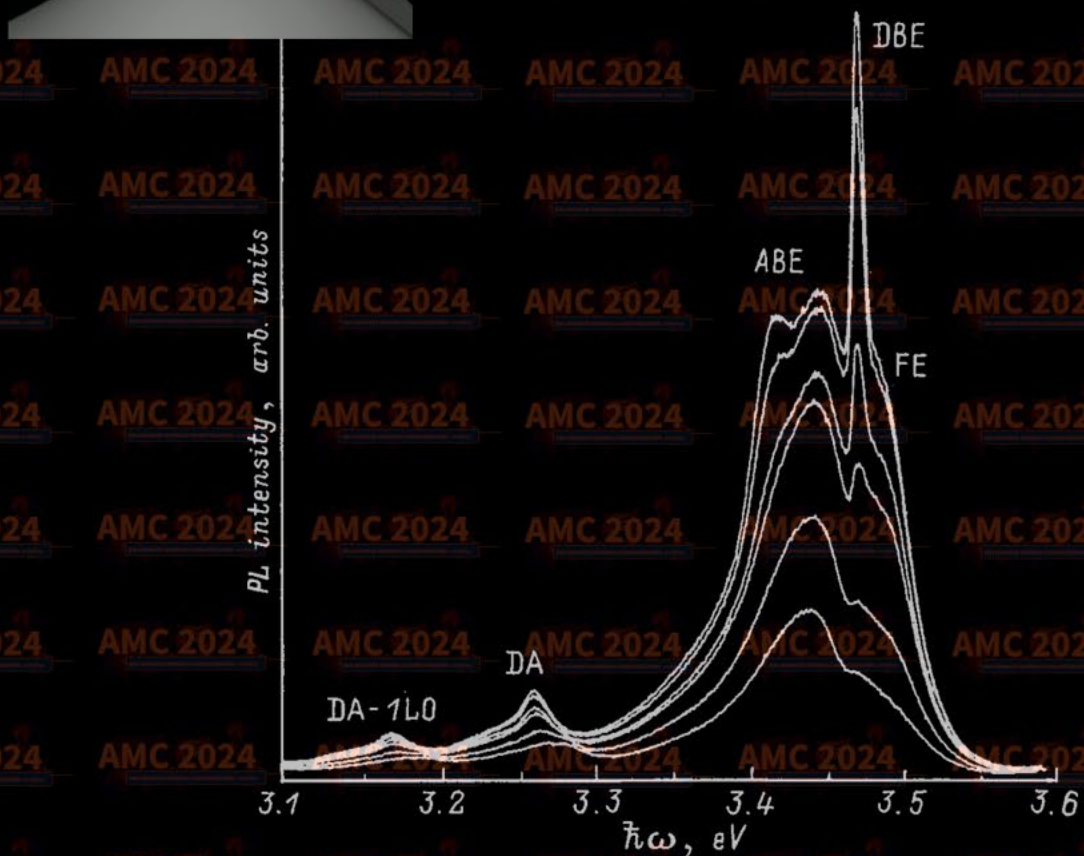


Phys. Rev. Lett. **105**, 136805 (2010)

Photoluminescence

Free-exciton and bound-exciton luminescence in GaN

Excitonic molecule luminescence in Si



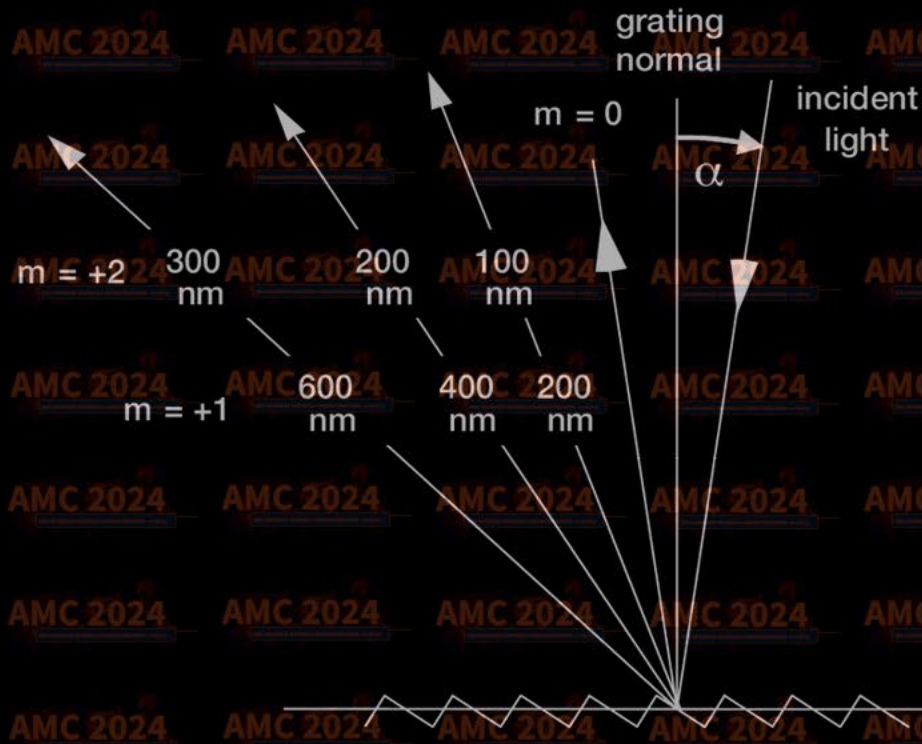
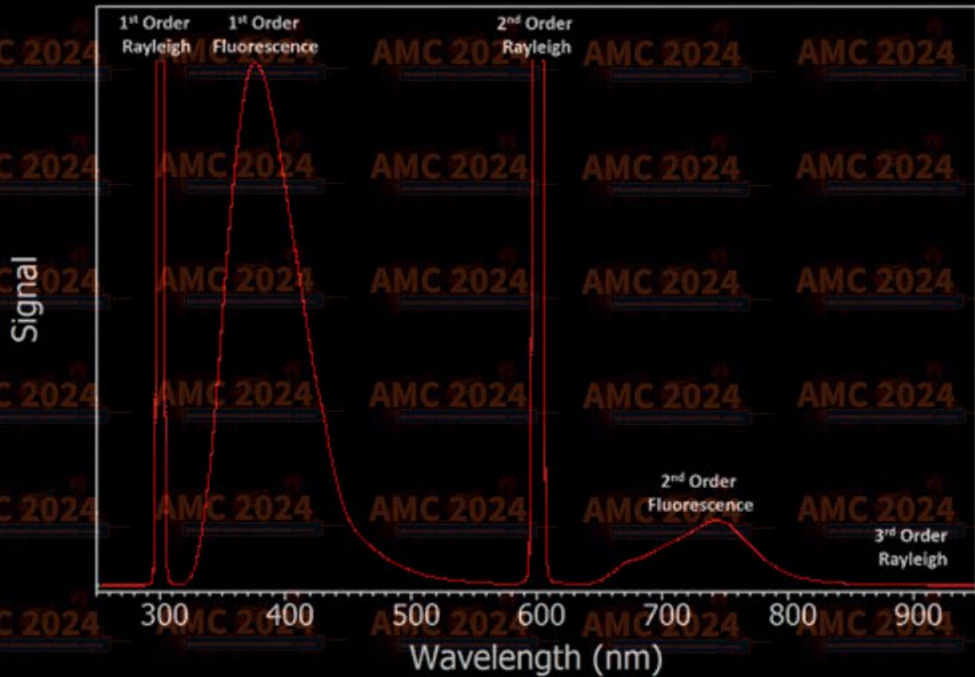
Spectrogram of a Si specimen at ~3 K. The horizontal axis is the energy of the emitted photons in eV. The vertical response is nearly proportional to the number of photons per unit energy interval. The specimen resistivity at room temperature was $9 \times 10^3 \Omega \text{ cm}$.

Low-temperature photoluminescence spectra of a sample of bulk GaN crystal at temperatures (from top to bottom) of 6, 10, 15, 20, 30, and 45 K. Excitation light comes from a DRSh- 250 lamp



Photoluminescence

Pitfalls, artifacts, corrections ...



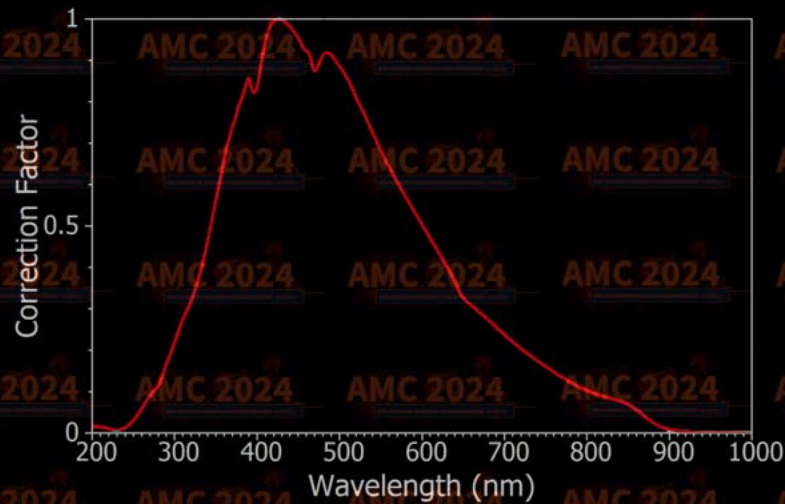
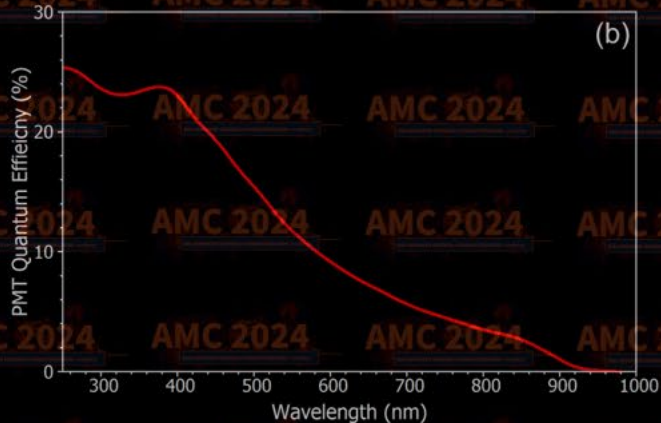
 www.newport.com

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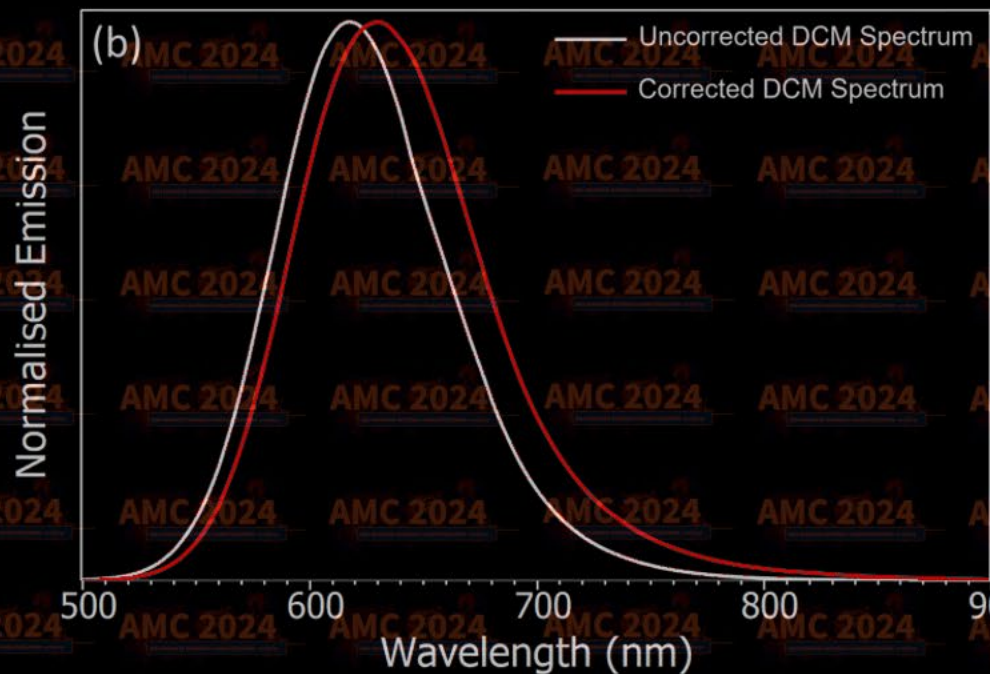
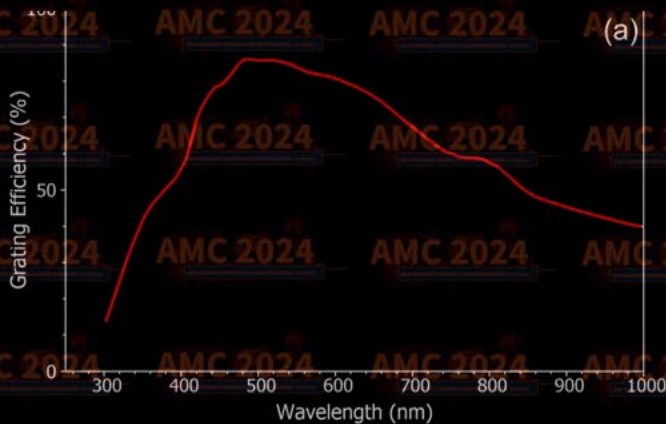


Photoluminescence

Pitfalls, artifacts, corrections ...



Non-ideal components introduce spectral distortions



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Photoluminescence

Strengths:

- Very little to none sample preparation.
- Non destructive technique.
- Very informative spectrum.

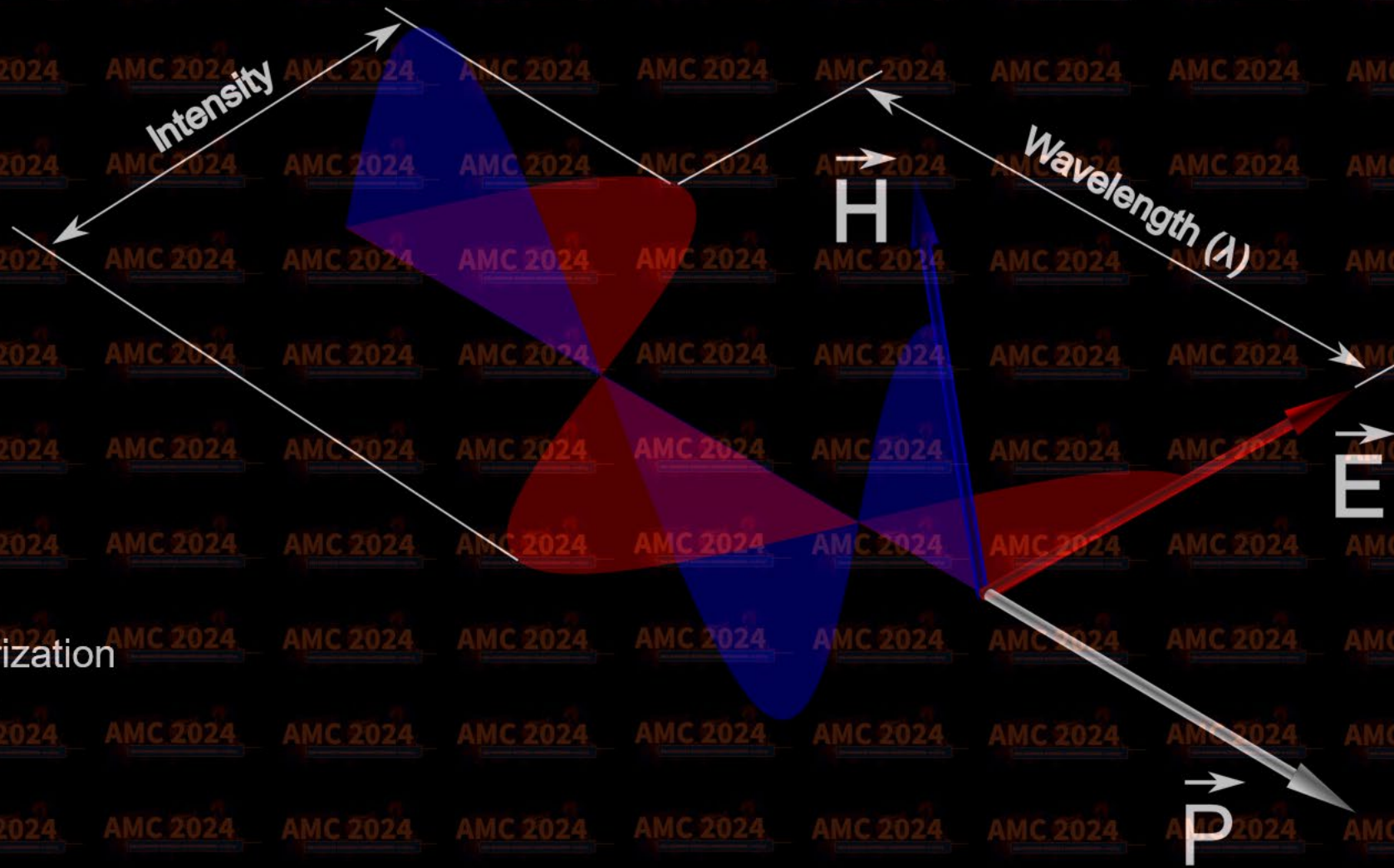
Limitations:

- Often requires low temperature.
- Data analysis may be complex.
- Many materials luminescence weakly.

Complementary techniques:
Ellipsometry, Modulation spectroscopies,
Spectrophotometry, Raman.



Light properties

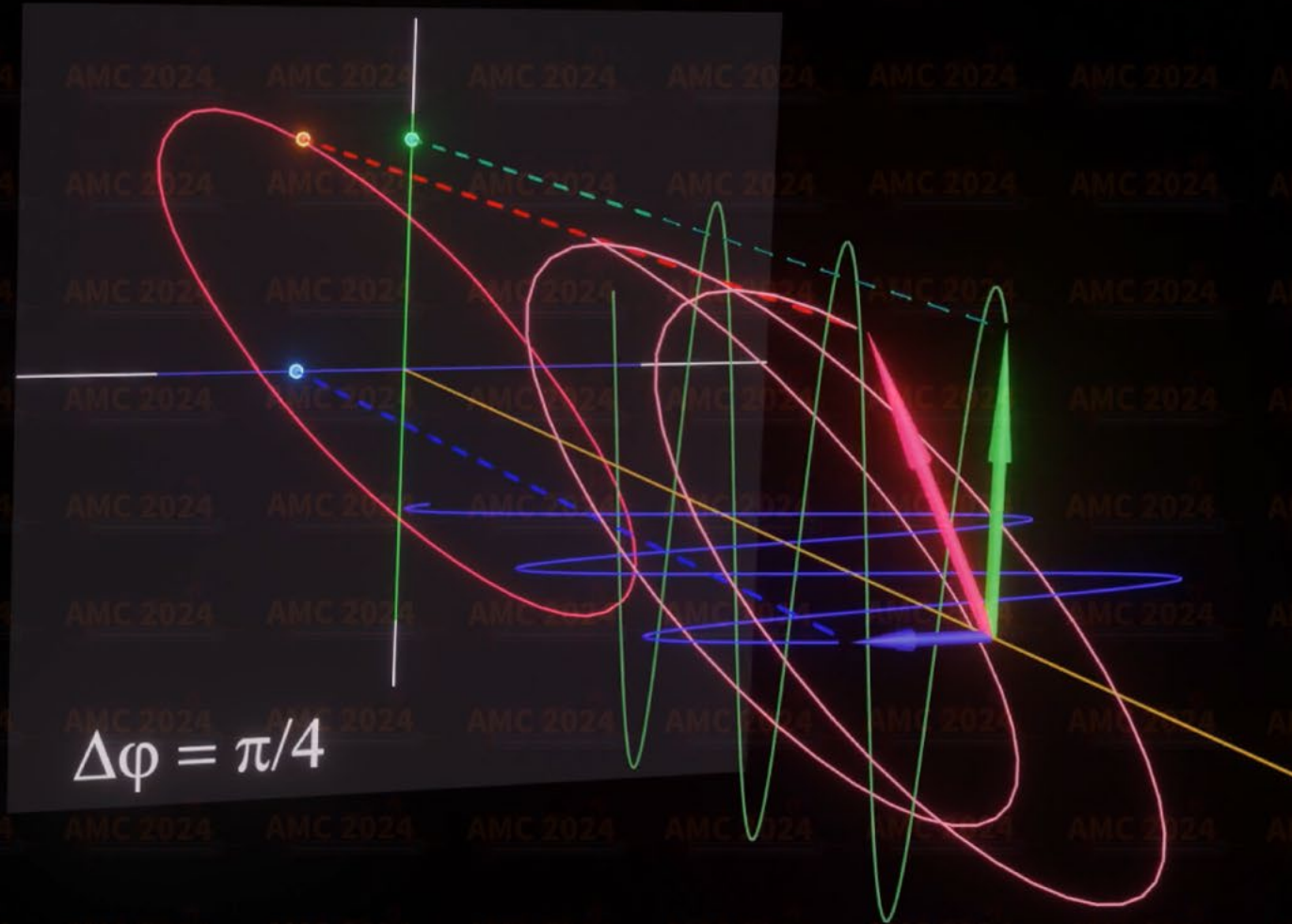


- Direction of propagation
- Electric field direction or polarization
- Photon energy or wavelength
- Intensity

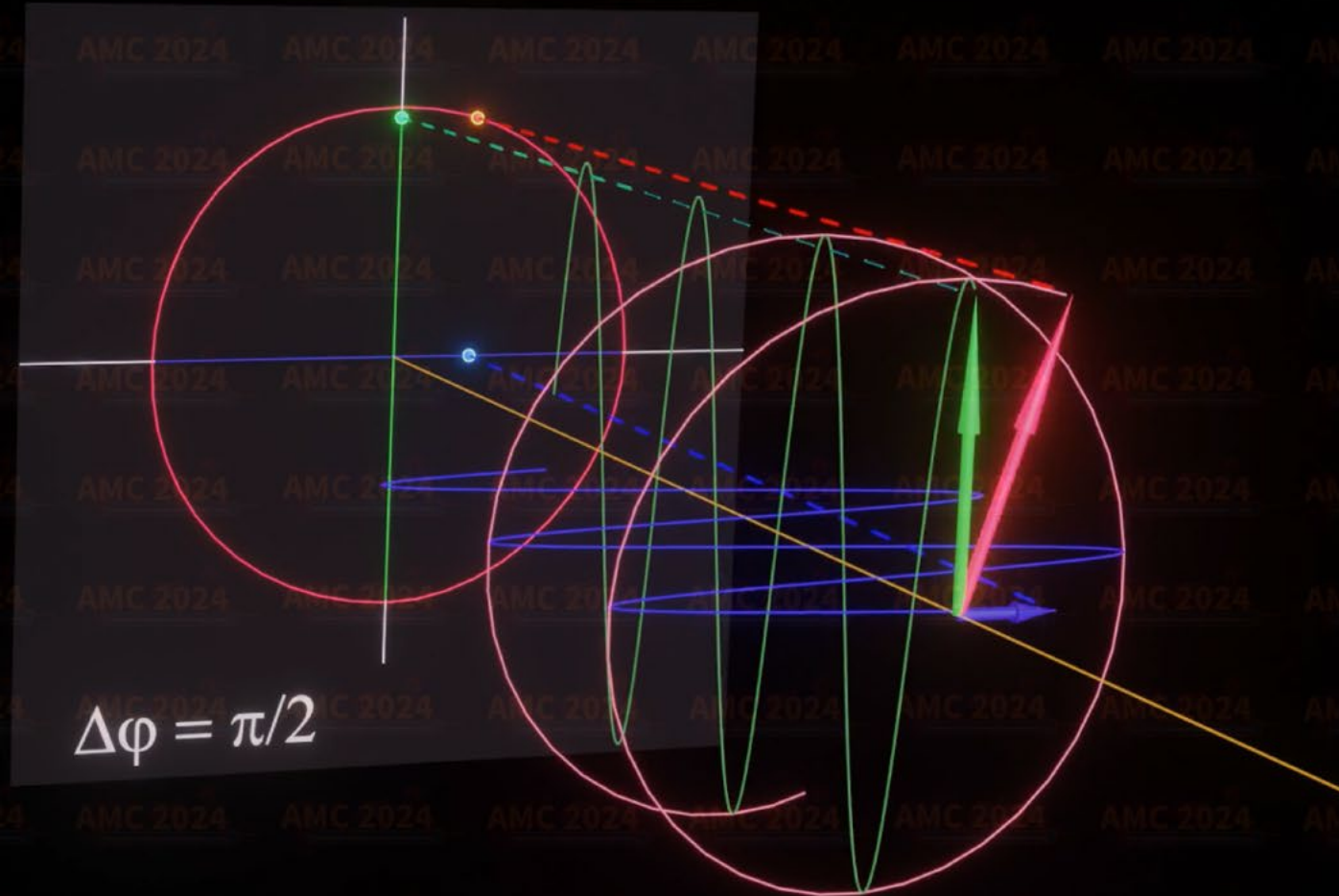
Polarization



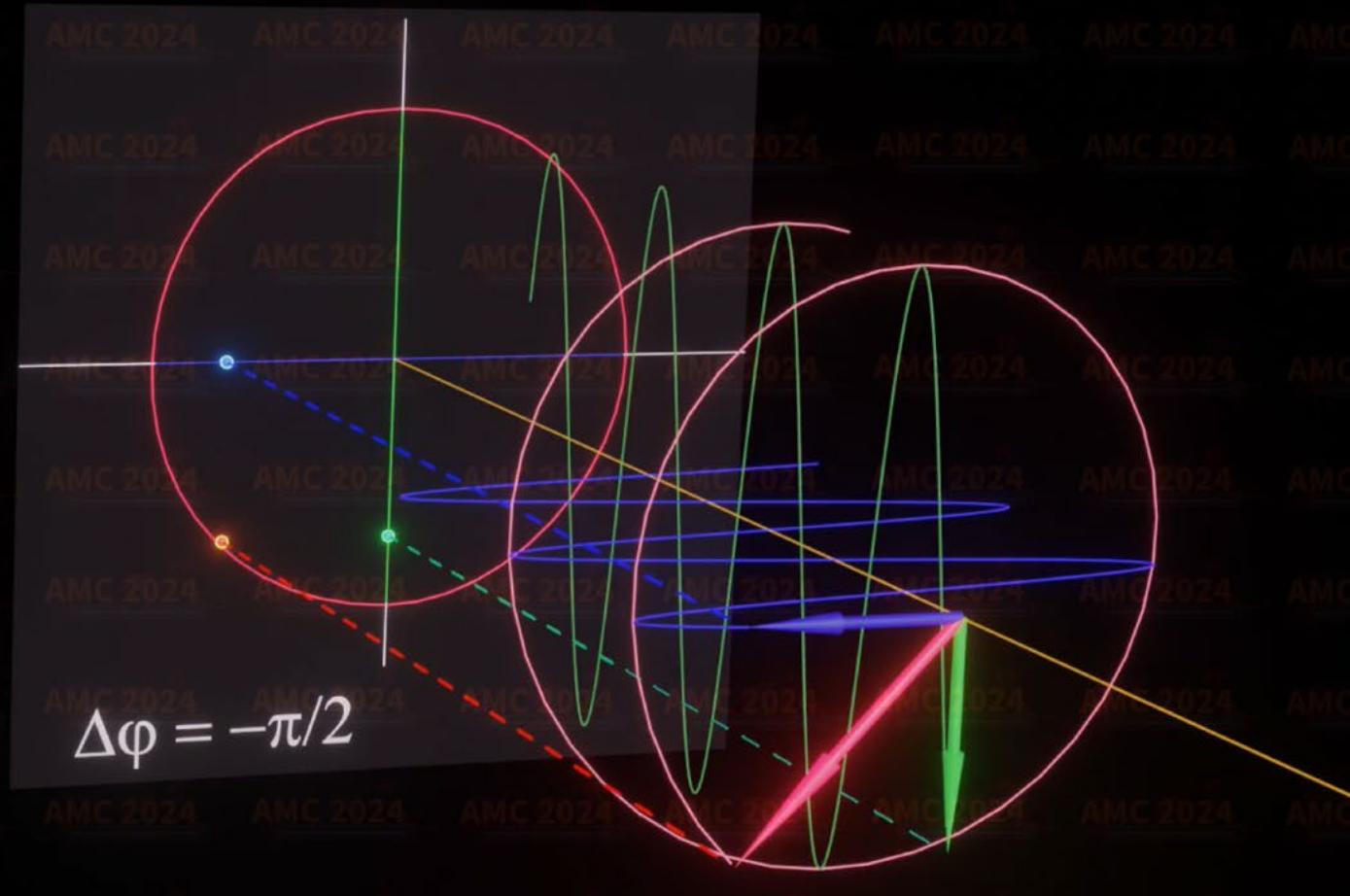
Polarization



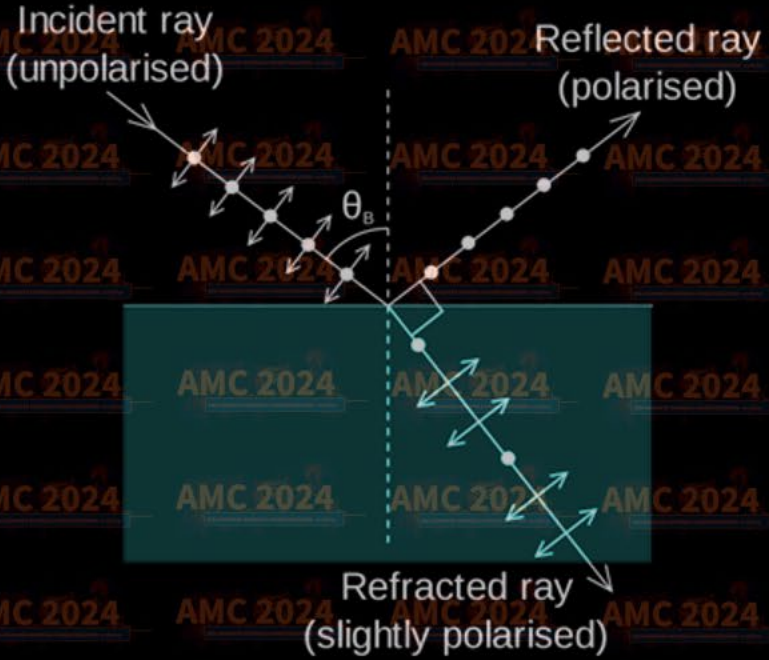
Polarization



Polarization



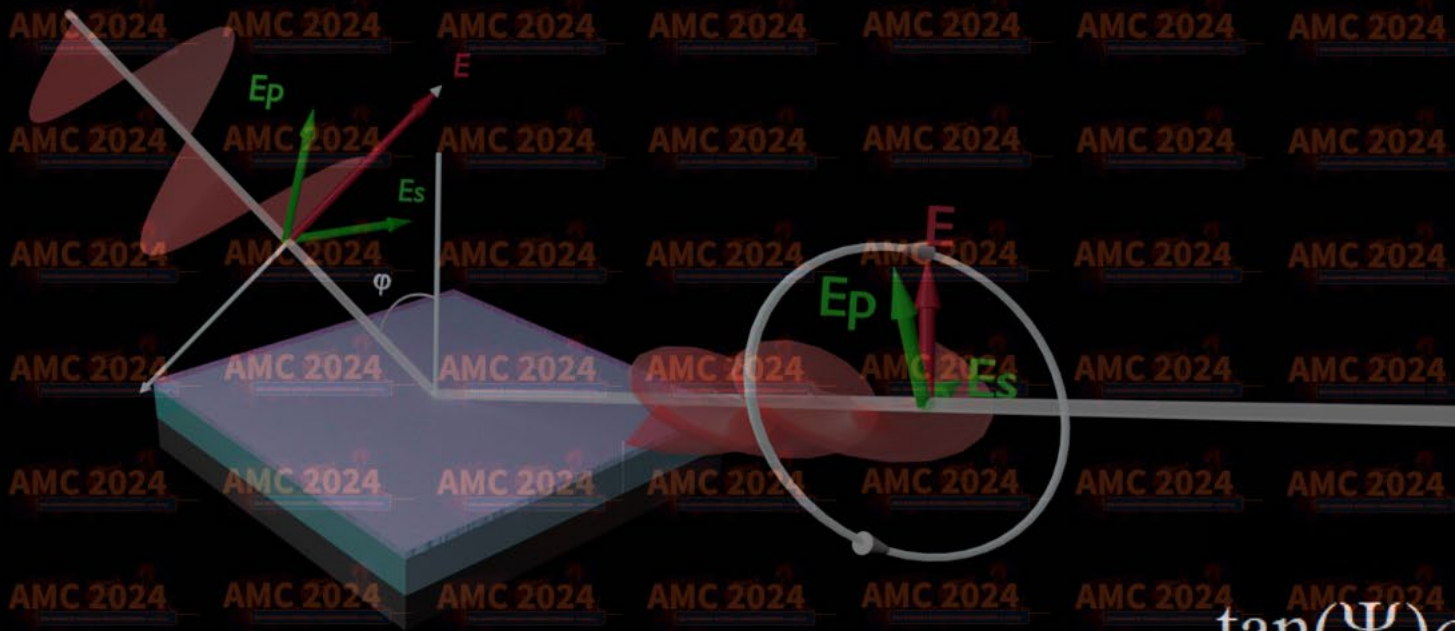
Polarization



Ellipsometry

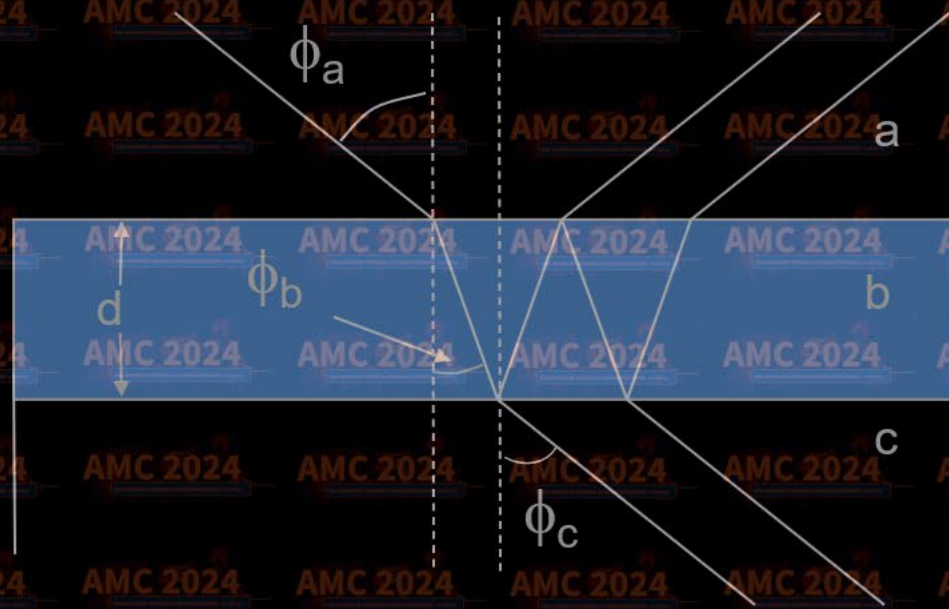
Basic principle:

The reflected light emerges from the surface elliptically polarized, i.e. its p and s polarization components are generally different in phase and amplitude.



$$\tan(\Psi)e^{i\Delta} = \frac{\tilde{R}_p}{\tilde{R}_s}$$

Ellipsometry



$$\tilde{n} = n + ik \quad \tilde{n}_1 \sin \phi_1 = \tilde{n}_2 \sin \phi_2$$

$$\tilde{r}_{12}^{p,s} = \frac{\tilde{n}_{2,1} \cos \phi_1 - \tilde{n}_{1,2} \cos \phi_2}{\tilde{n}_{2,1} \cos \phi_1 + \tilde{n}_{1,2} \cos \phi_2}$$

$$\tilde{R}_{p,s} = \frac{\tilde{r}_{ab}^{p,s} + \tilde{r}_{bc}^{p,s} e^{-2i\beta}}{1 + \tilde{r}_{ab}^{p,s} \tilde{r}_{bc}^{p,s} e^{-2i\beta}}$$

$$\beta = \frac{2\pi d}{\lambda} \tilde{n}_b \cos \phi_b$$

$$\tilde{R}_{p,s} = \frac{E_{p,s}^r}{E_{p,s}^i} e^{i(\delta_{p,s}^r - \delta_{p,s}^i)}$$

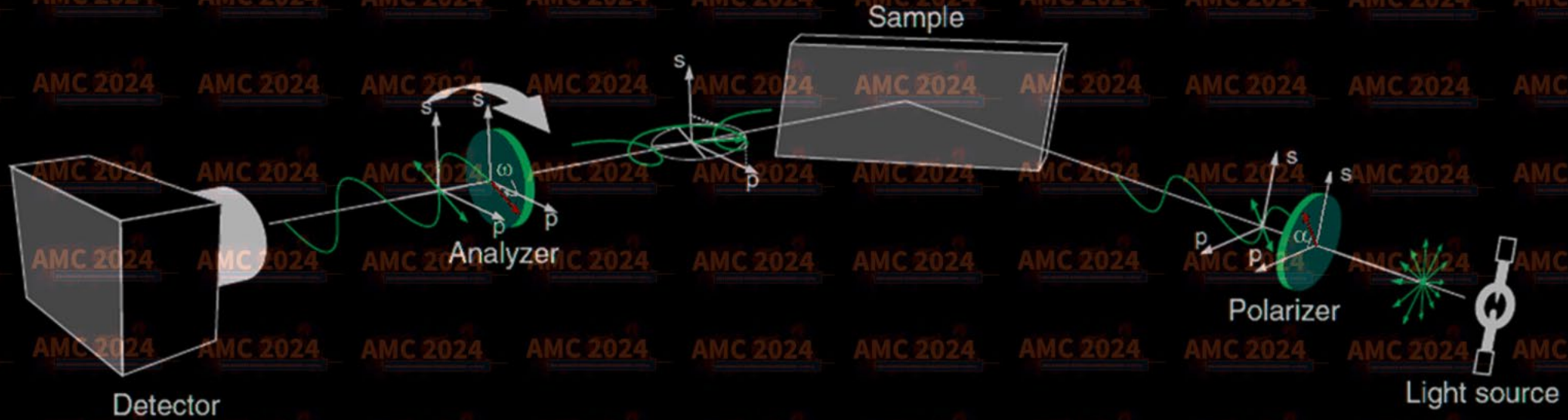
$$\tan(\Psi) e^{i\Delta} = \frac{\tilde{R}_p}{\tilde{R}_s} \Rightarrow \left\{ \begin{array}{l} \tan(\Psi) = \frac{|\tilde{R}_p|}{|\tilde{R}_s|} \\ \Delta = \delta^r - \delta^i \end{array} \right.$$



Ellipsometry

What is measured:

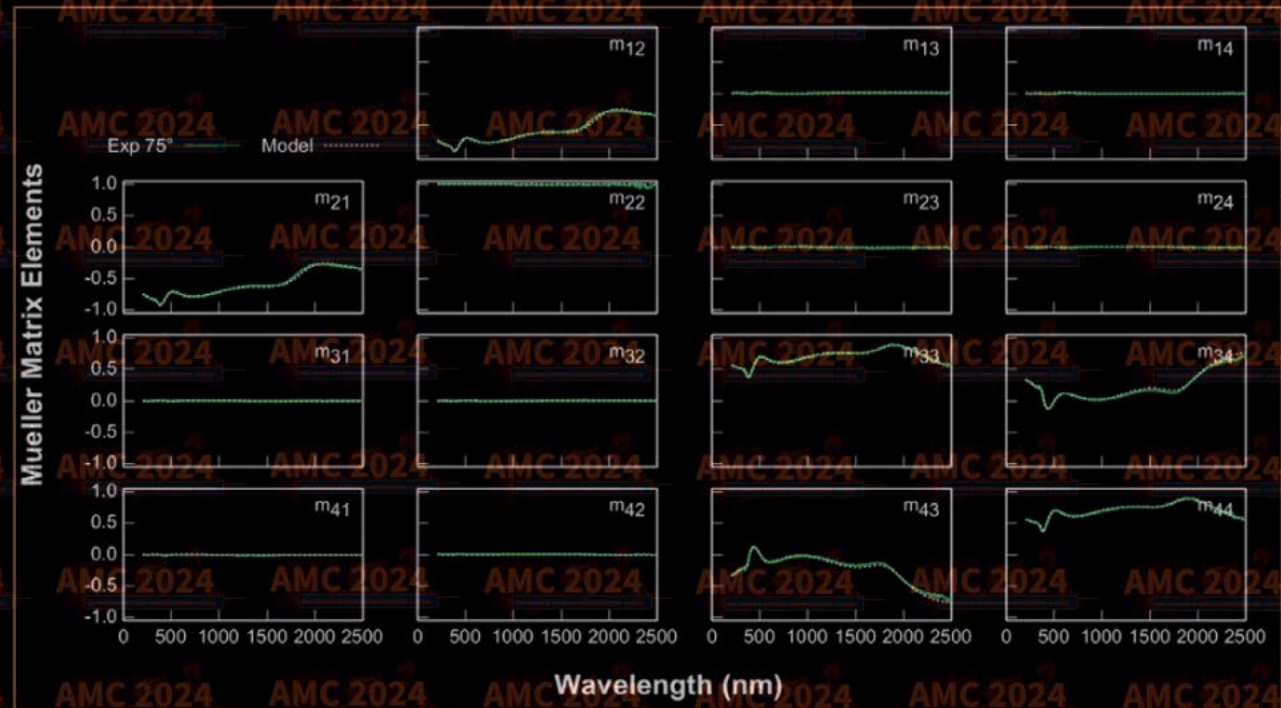
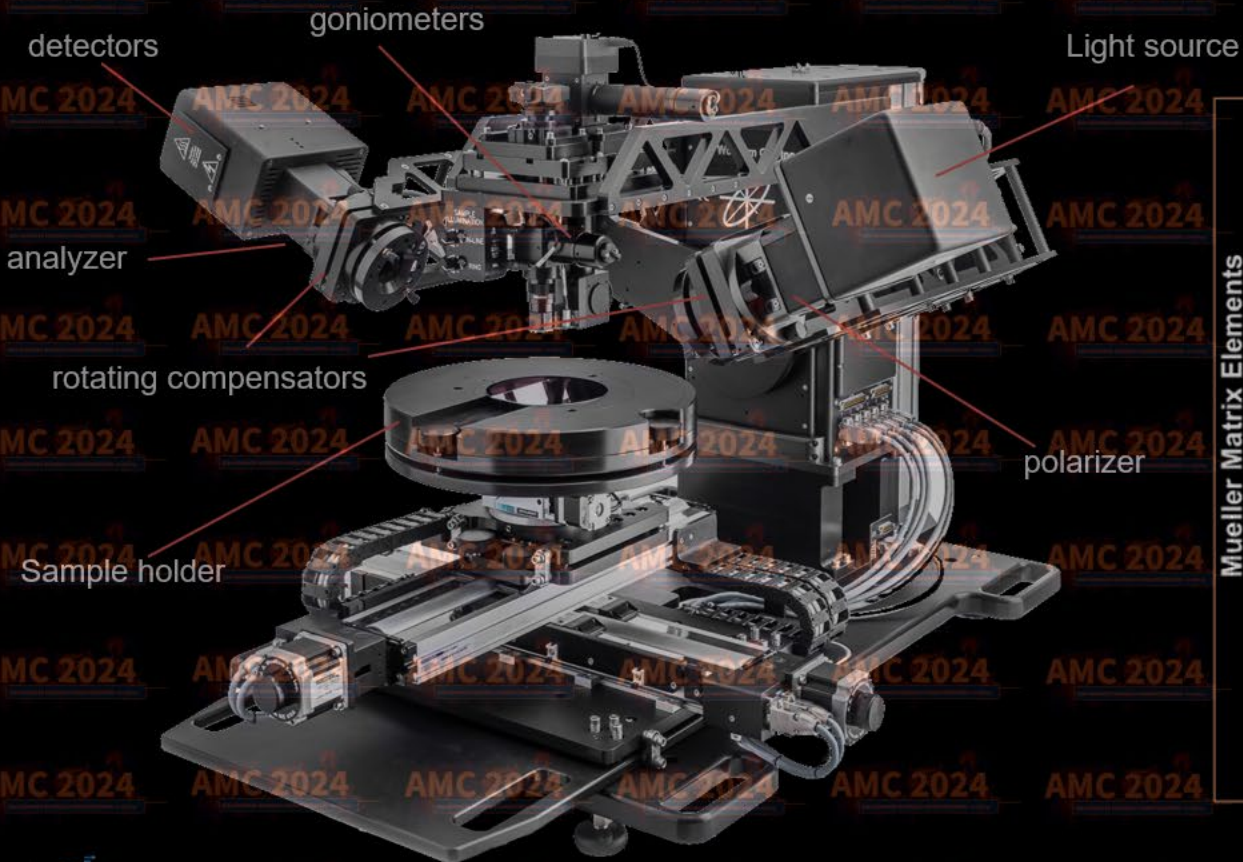
The changes in the polarization state of light upon reflection from a mirror like surface.



Ellipsometry

What is measured:

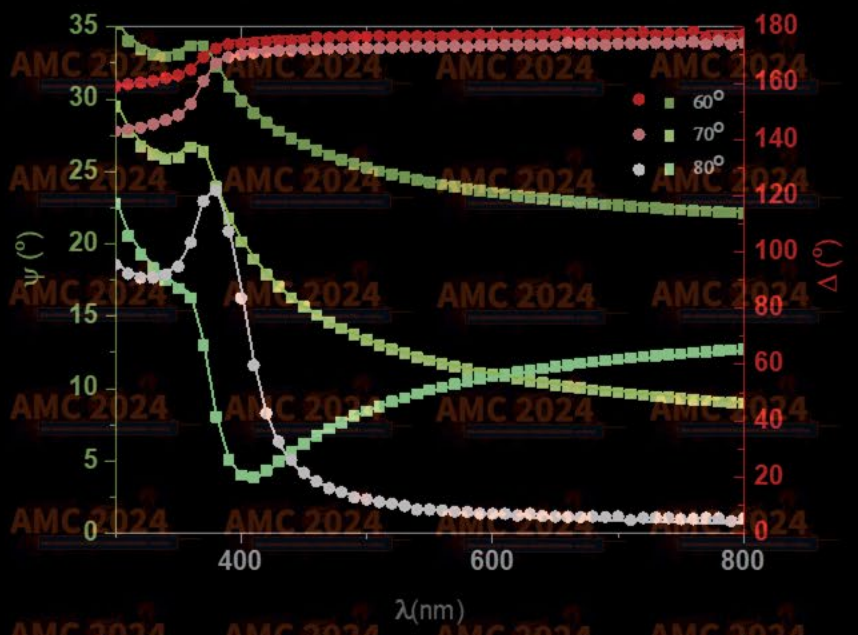
The changes in the polarization state of light upon reflection from a mirror like surface.



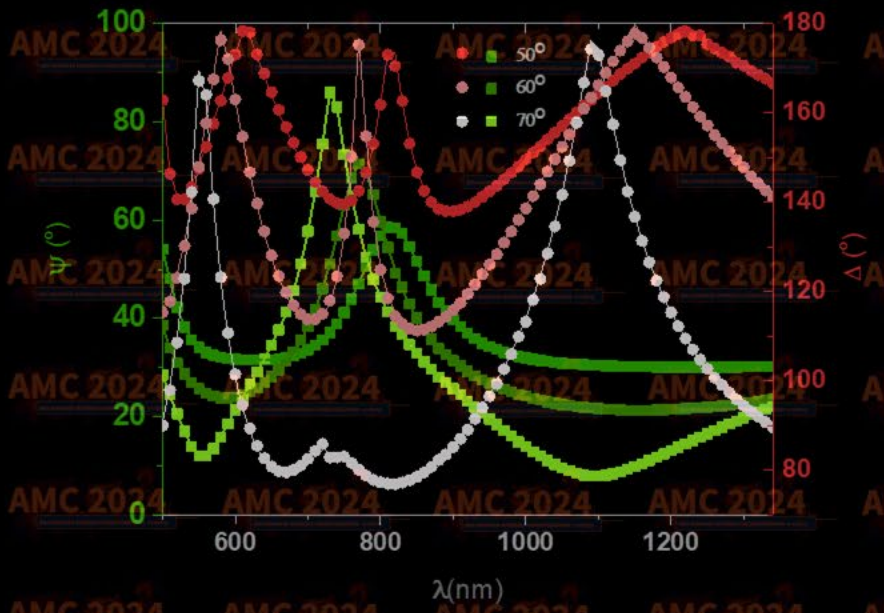
Ellipsometry

Applications

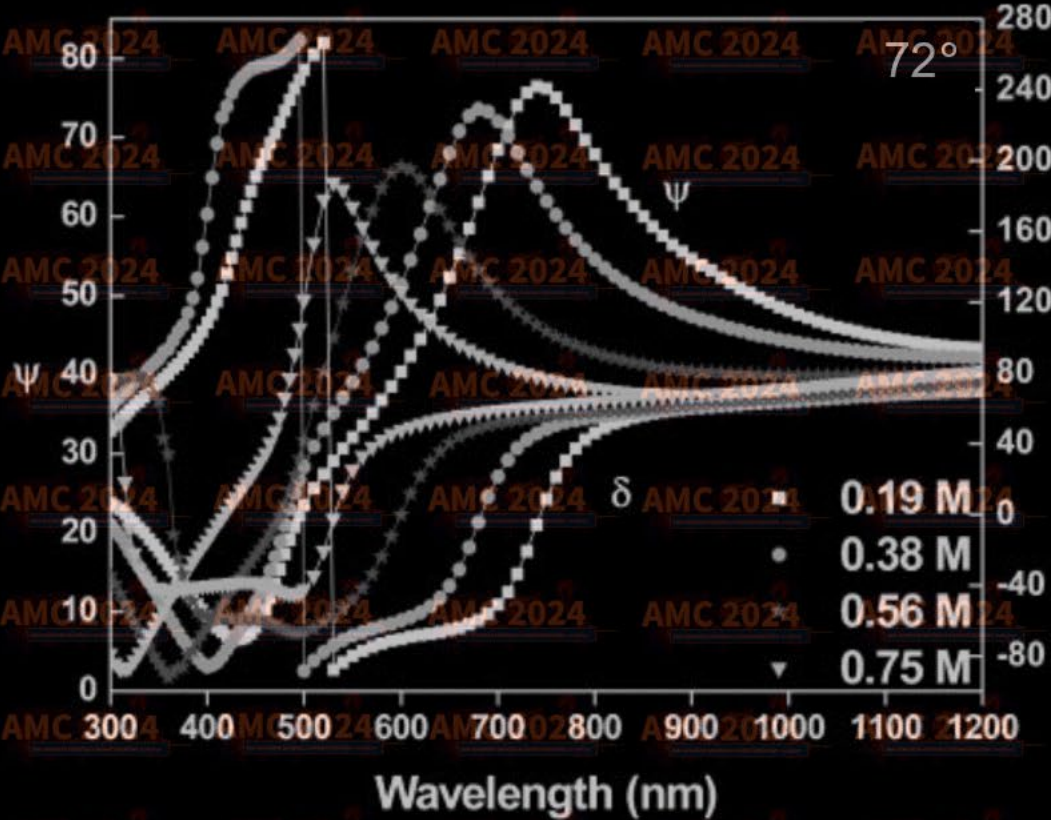
SiO₂ 18.7 ± 0.2 Å
Si



SiO₂ 4923.1 ± 0.2 Å
Si



Applications



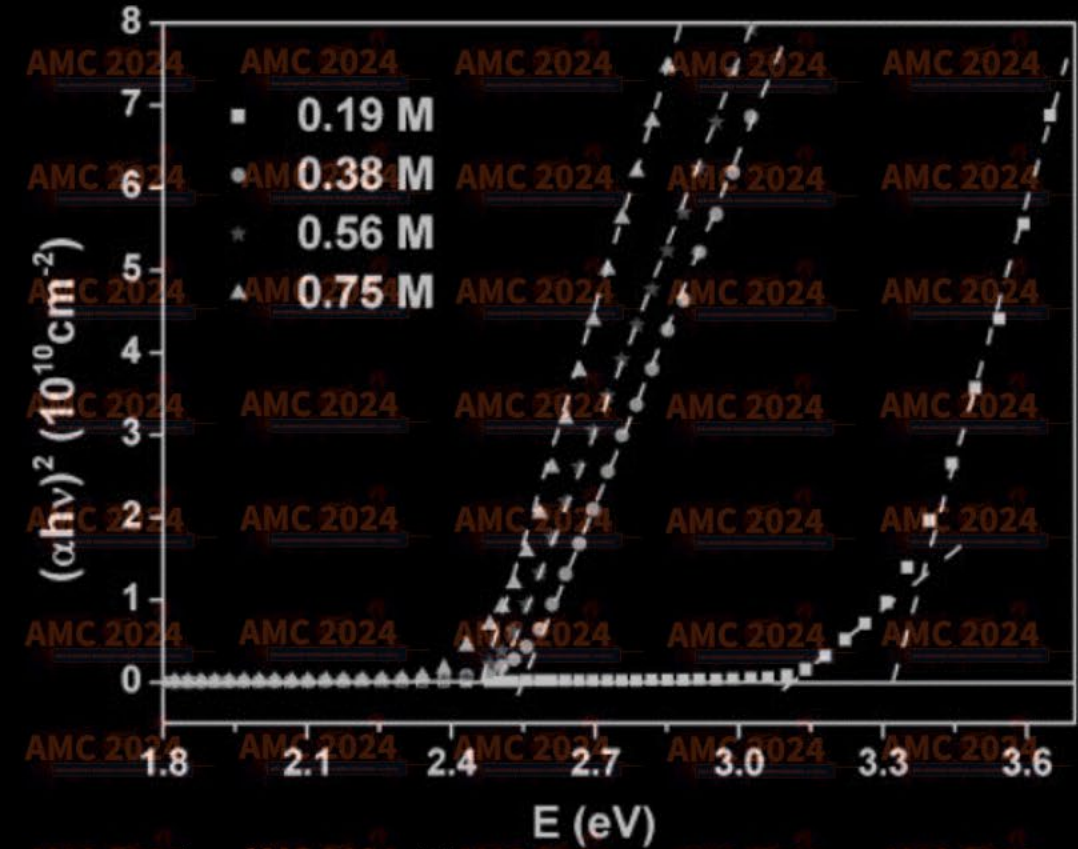
[NH ₄ OH] (M)	Thickness (nm)	Roughness (nm)	ZnS (%)	Band-gap (eV)
0.19	42.12	23.77	99.7	3.49
0.38	73.79	7.15	45.5	2.52
0.56	50.89	5.94	32.3	2.45
0.75	18.59	4.54	5.2	2.43

Ellipsometric $\Psi(\lambda)$ and $\Delta(\lambda)$ spectra of $\text{Cd}_{1-x}\text{Zn}_x\text{S}$ thin films deposited under the different concentration of ammonia: 0.19, 0.38, 0.56, and 0.75 M

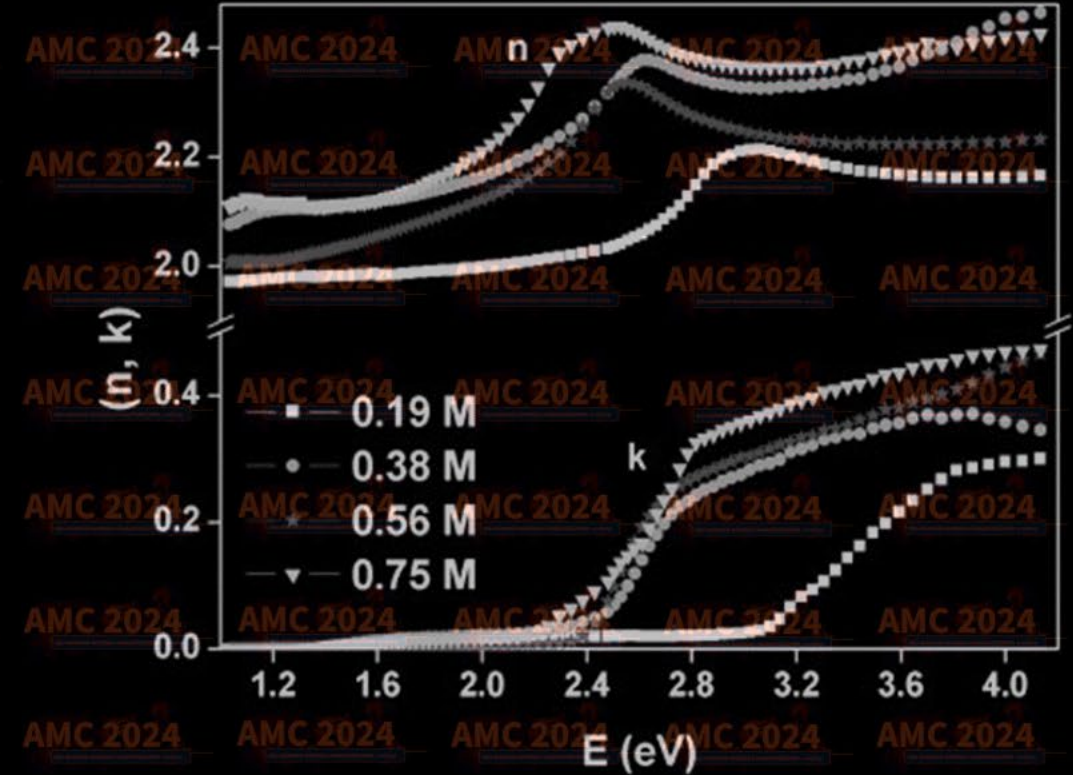
Jpn. J. Appl. Phys. 49 (2010) 081202

Ellipsometry

Applications



- Composition
- Surface roughness
- Film thickness
- Band gap energy
- Optical constants (dielectric function)



Jpn. J. Appl. Phys. 49 (2010) 081202



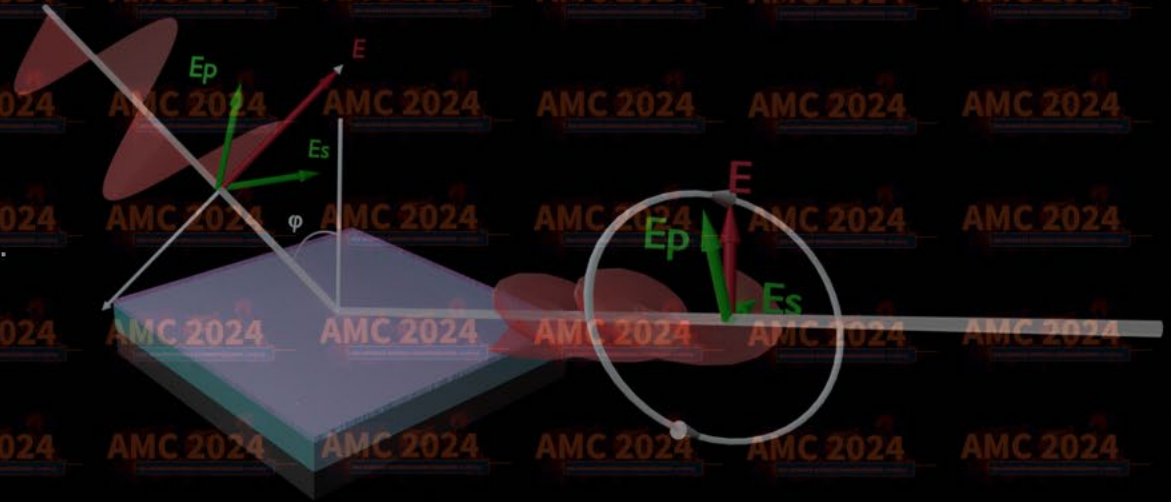
Ellipsometry

Strengths:

- Fast.
- Measures a ratio of two intensity values and a phase.
 - Highly accurate (even in low light levels).
 - No reference sample necessary.
 - Not susceptible to scatter, lamp or purge fluctuations.
 - Increased sensitivity, especially to ultrathin films (<10nm).
- Can be used in-situ.

Limitations:

- Flat and parallel surface and interfaces with measurable reflectivity.
- A realistic physical model of the sample is required to obtain most useful information.



Complementary techniques:

PL, Modulation spectroscopies, X-Ray Photoelectron Spectroscopy, Secondary Ion Mass Spectroscopy, XRD, Hall effect.

Optical microscopy

Von Leeuwenhoek
microscope
ca. late 1600's



Early microscope
"The Far Side" by Gary Larson.



Hand-held microscope ca. early 1700's

Hooke microscope
ca. 1670



British microscope
ca. 1850



Zeiss microscope
ca. 1930

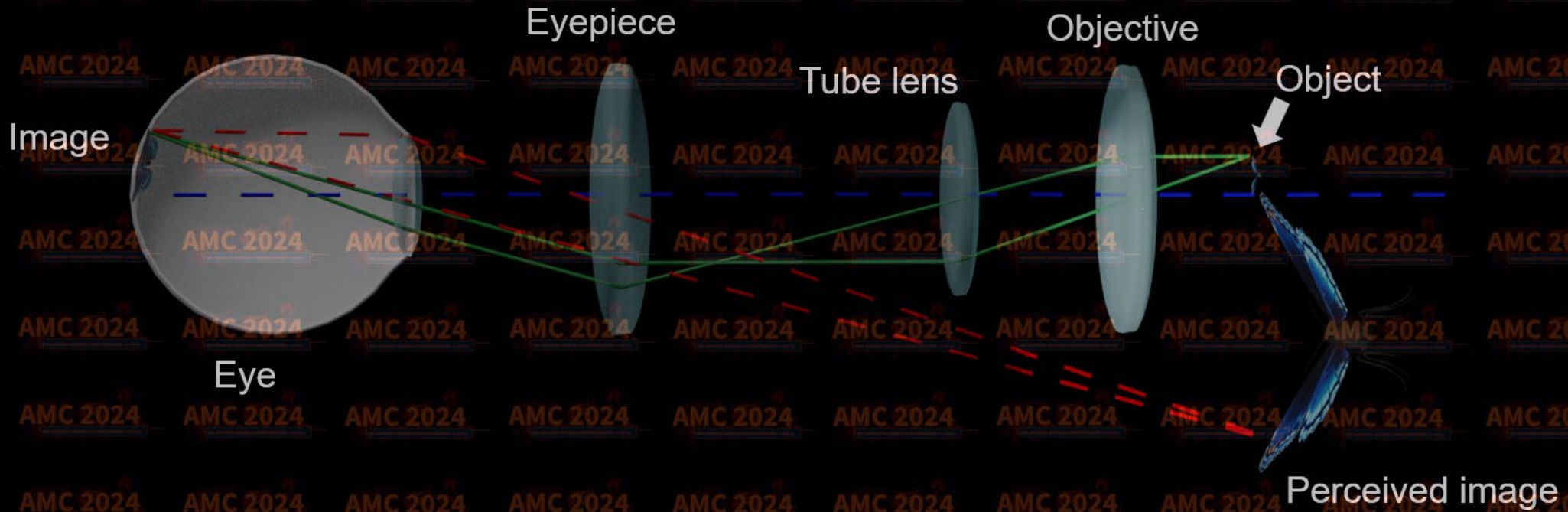


Modern scientific microscope



Optical microscopy

"Conventional" Optical Microscopy

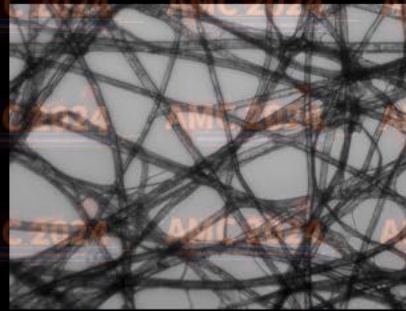


Optical microscopy

Phase contrast



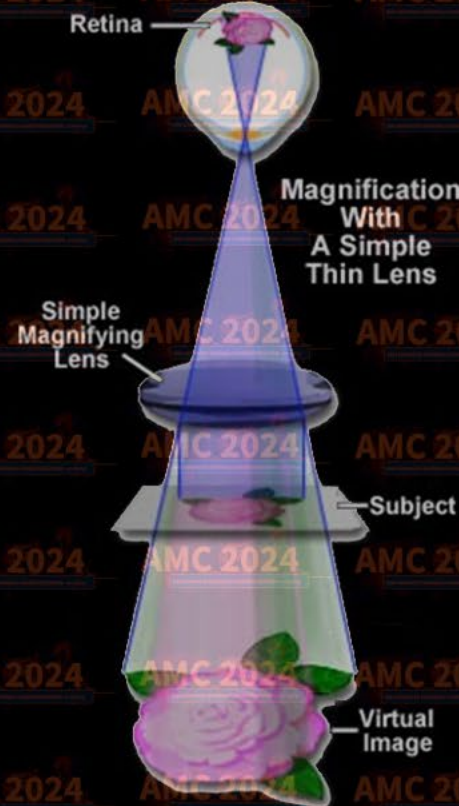
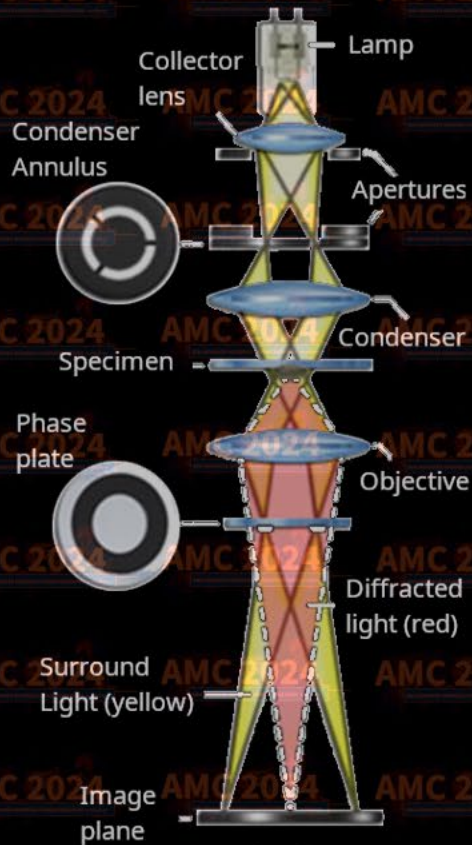
Bright field



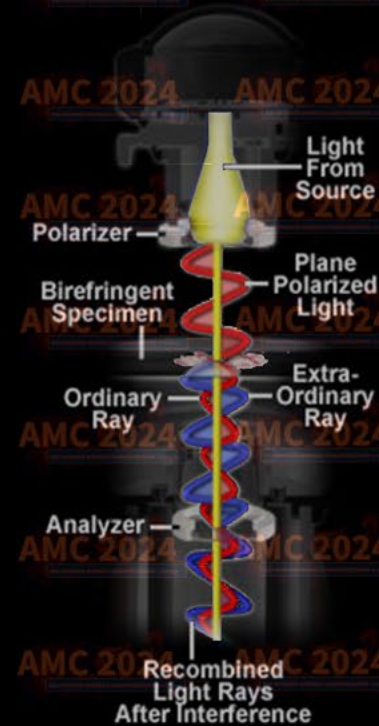
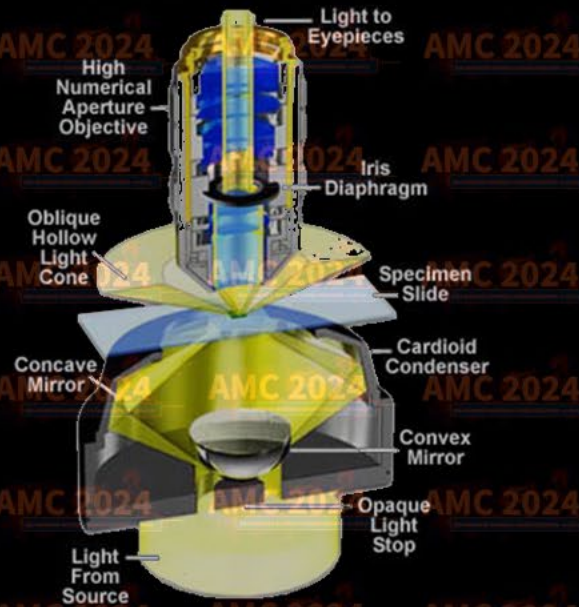
Dark field



Polarizing

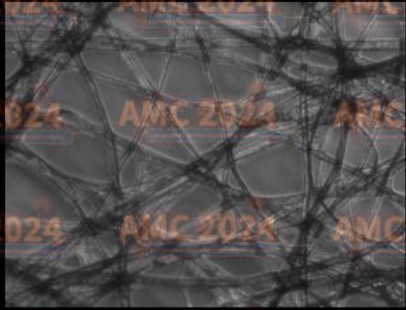


Magnification With A Simple Thin Lens

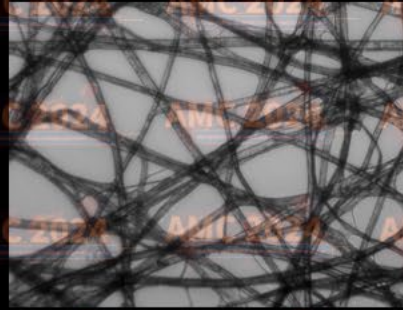


Optical microscopy

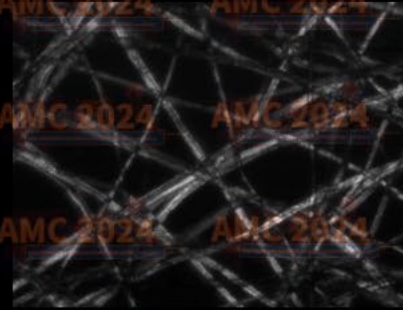
Phase contrast



Bright field



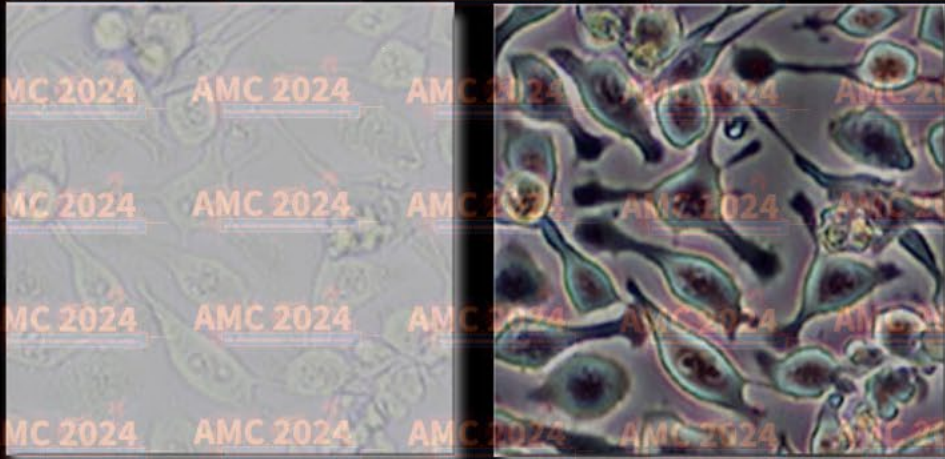
Dark field



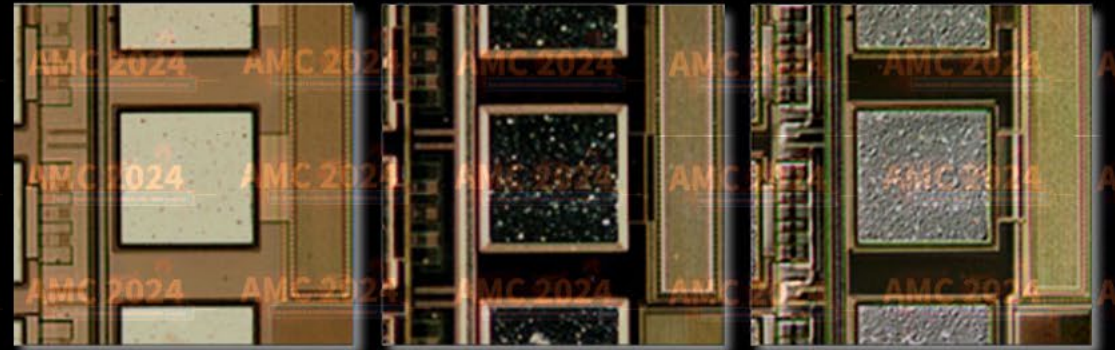
Polarizing



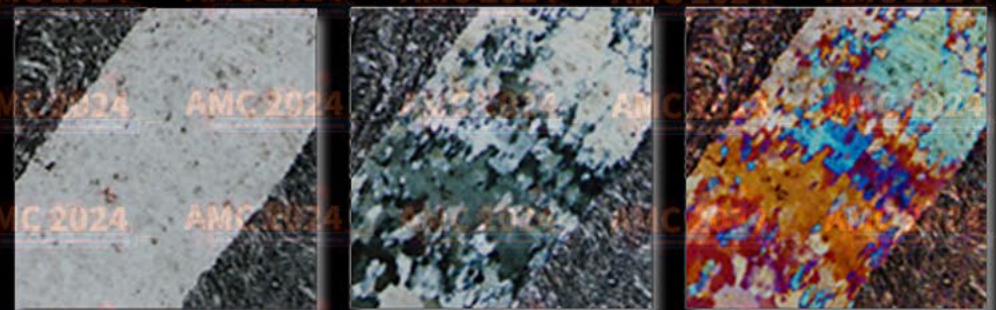
Living Cells in Brightfield and Phase Contrast



Integrated Circuit in Brightfield, Darkfield, and DIC with Reflected Light



Phyllite Thin Section in Polarized Light

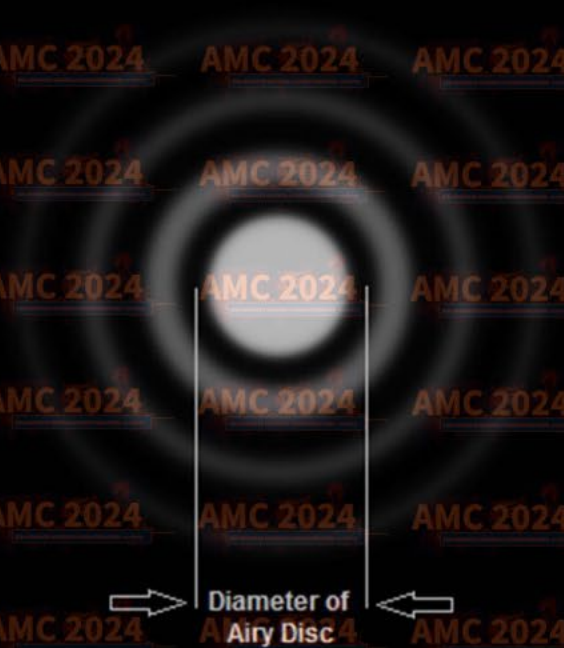


Resolution

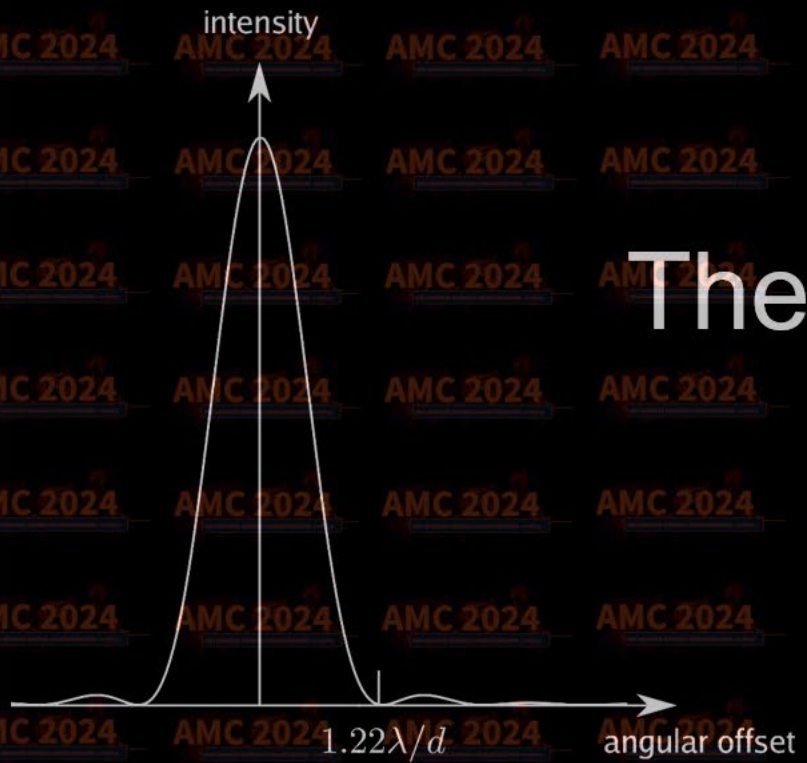
- But how small a thing can we see?



Lateral resolution



Diameter of Airy Disc



The Airy pattern

Lateral resolution

$$NA = (n)\sin(\mu)$$

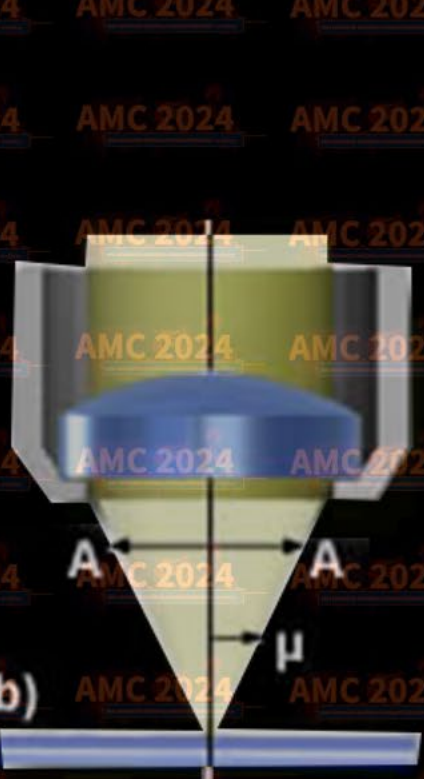
(a) $\mu = 7^\circ$ $NA = 0.12$

(b) $\mu = 20^\circ$ $NA = 0.34$

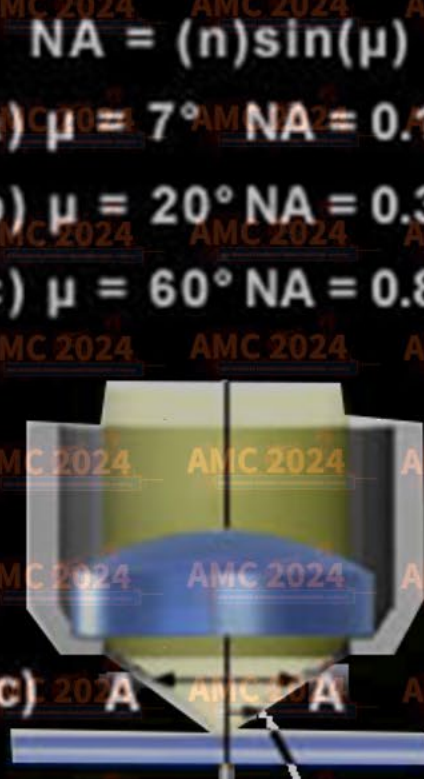
(c) $\mu = 60^\circ$ $NA = 0.87$



(a)



(b)



(c)

Lateral resolution



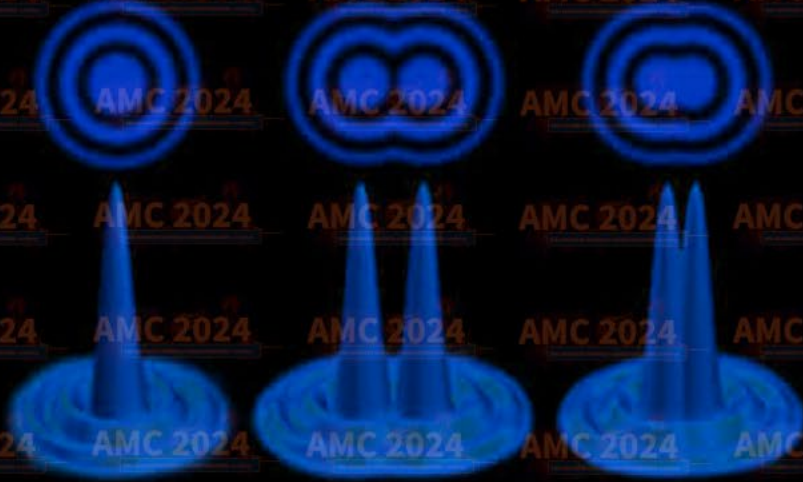
Numerical aperture

M. W. Davidson and M. Abramowitz

Lateral resolution

Resolution

Airy Discs



Intensity Distributions

$$d \approx \frac{0.61\lambda}{NA}$$

Rayleigh criterion

Rayleigh limit

$$d = \frac{0.61 \cdot \lambda}{NA}$$

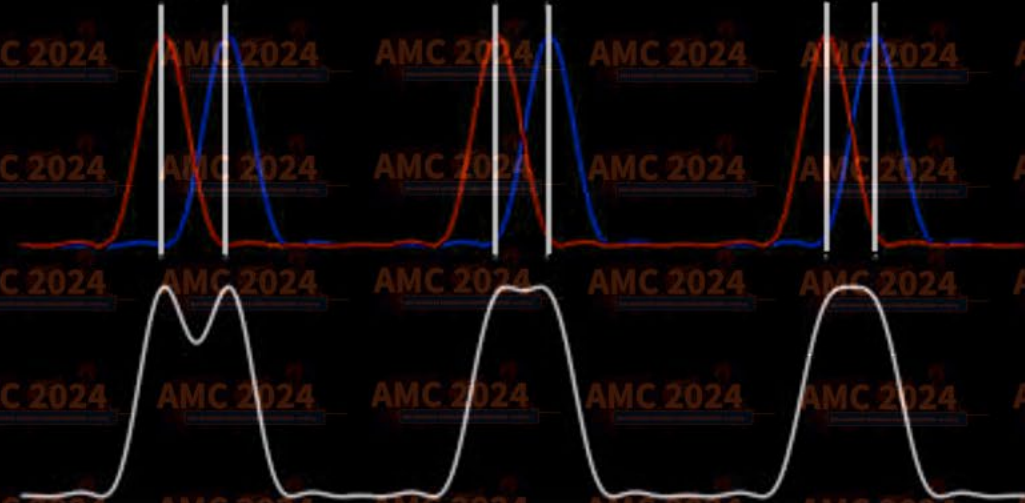
Abbe limit

$$d = \frac{0.50 \cdot \lambda}{NA}$$

Sparrow limit

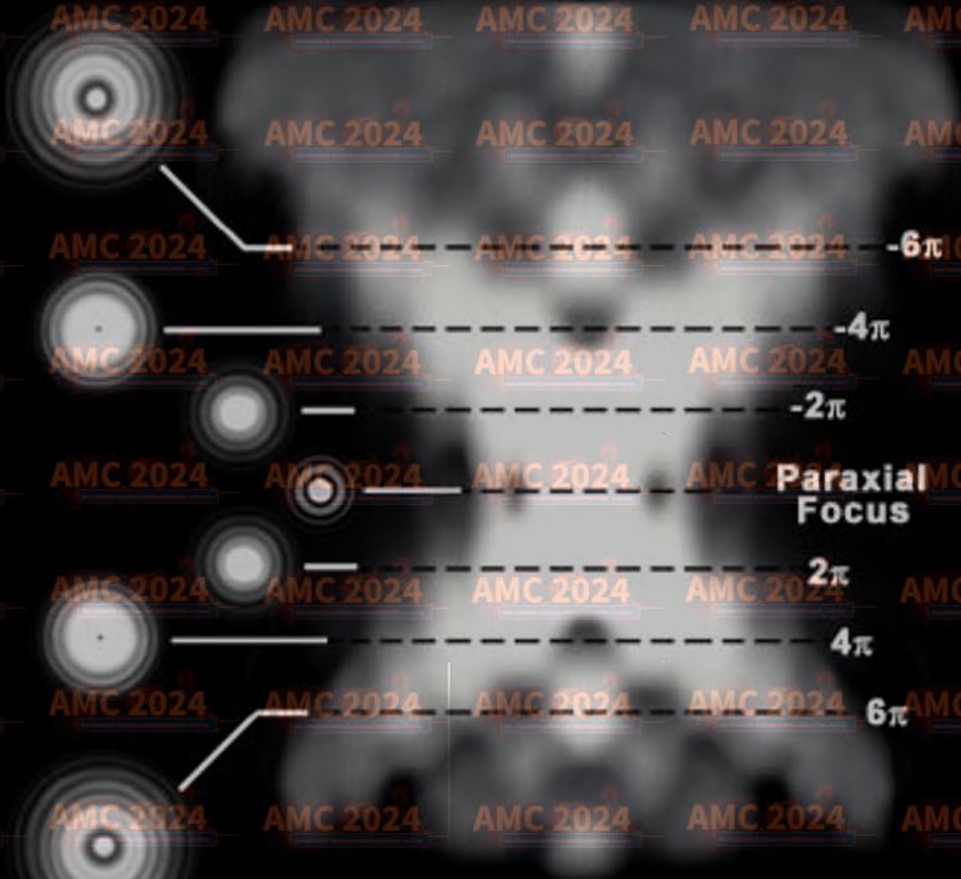
$$d = \frac{0.47 \cdot \lambda}{NA}$$

Abbé criterion



Depth resolution

Axial Intensity Distribution

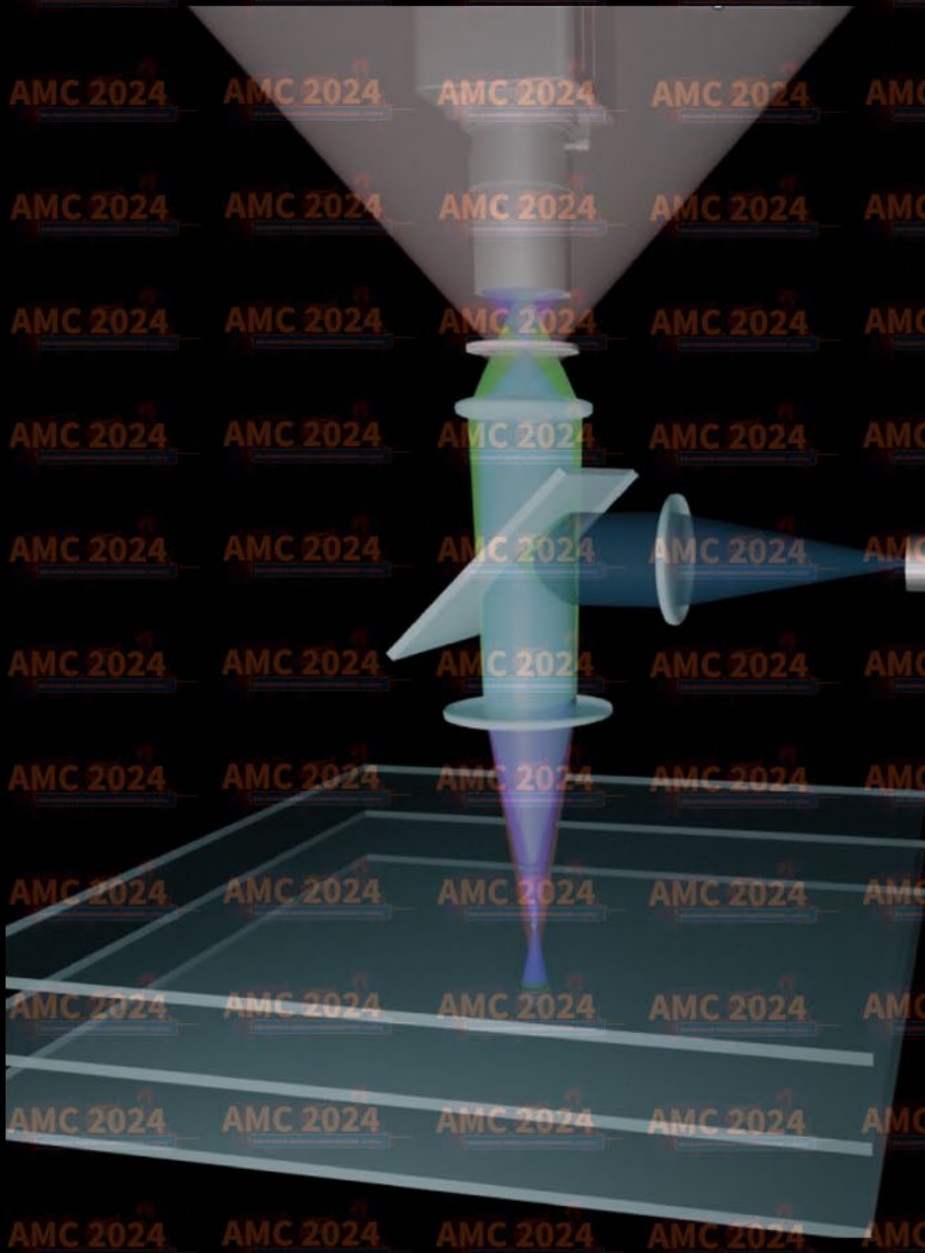


Figure



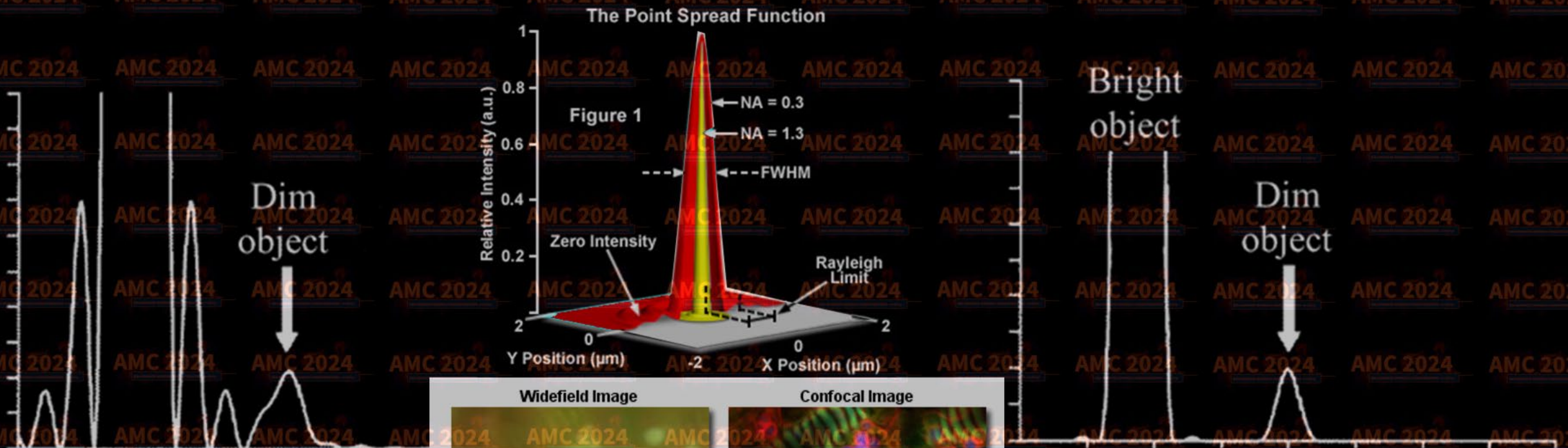
Confocal microscopy

- Increased contrast \Rightarrow 200:1.
- Slightly increased in plane resolution (1.5 x)
- Significantly increased resolution along the optical axis.
- Scanning image formation.



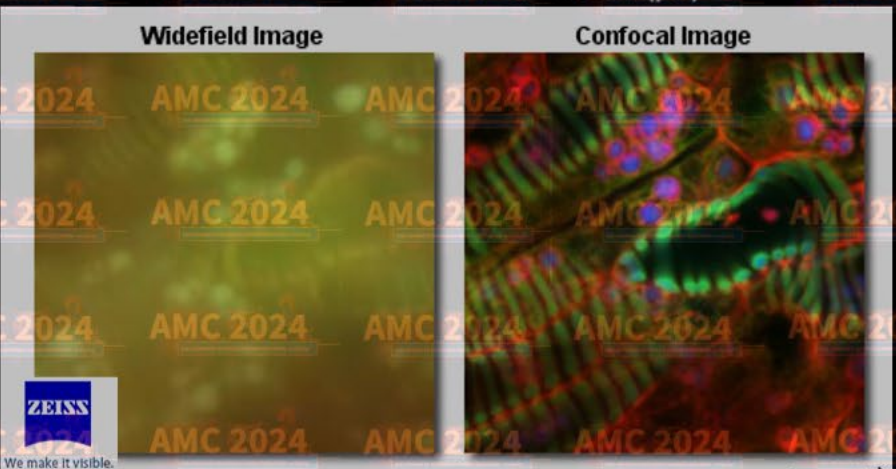
Confocal microscopy

The relation of the first ring maximum amplitude to the amplitude in the center is 2% in case of conventional point spreading function (PSF) in a focal plane, while in case of a confocal microscope this relation is 0.04%.



$$r_{\text{resel}} = 0.61 \frac{\lambda}{n \sin \theta} = 1.22 \frac{\lambda'}{D} F$$

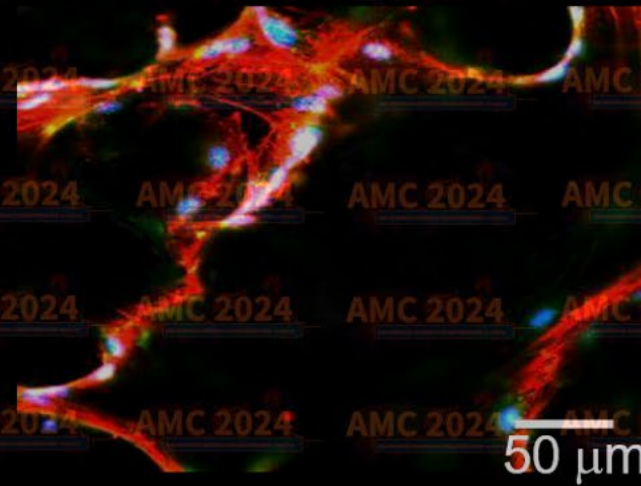
$$r_{\text{conf}} = 0.44 \frac{\lambda}{n \sin \theta} = 0.88 \frac{\lambda'}{D} F$$



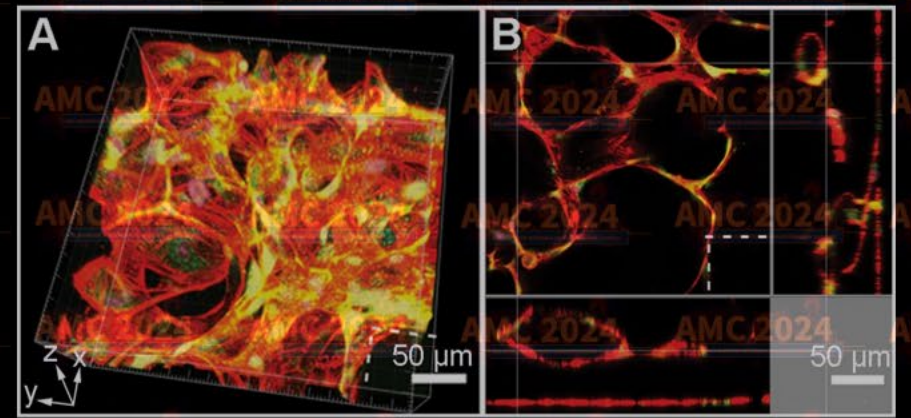
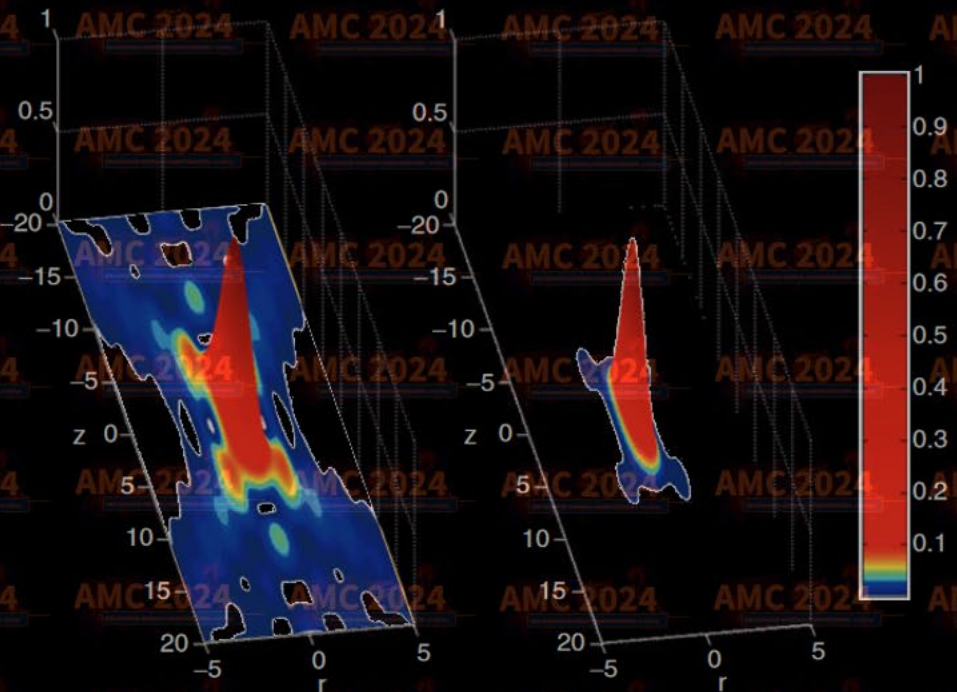
Confocal microscopy combined with spectroscopy

Widefield
microscope
PSF

Confocal
microscope
PSF

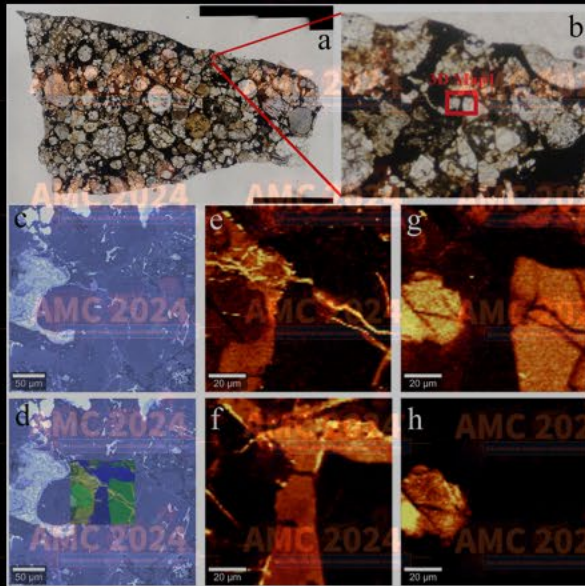


Confocal microscopy reconstruction of a 3D capillary bed

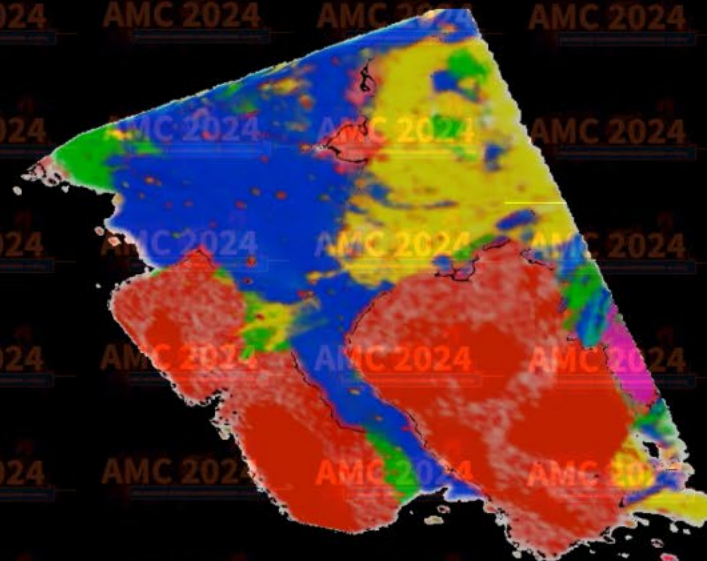
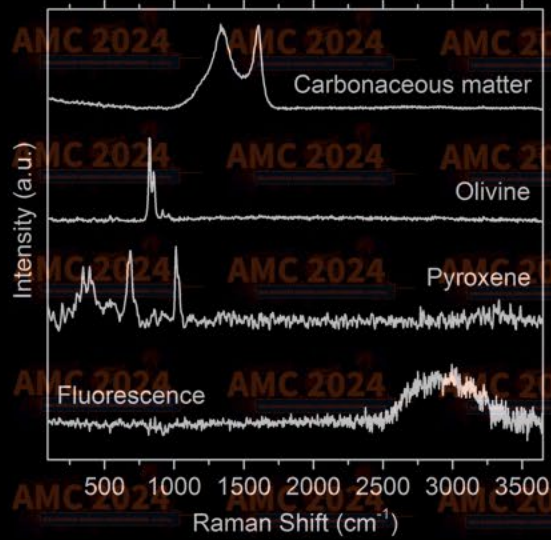


PLOS ONE 7(12): e50582 (2012)

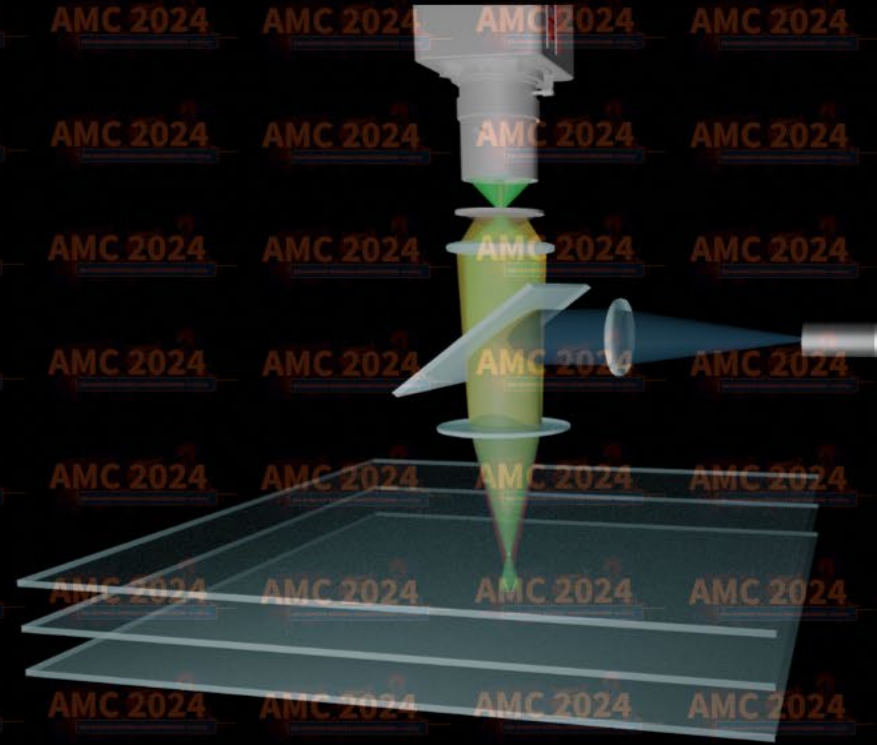
Confocal microscopy combined with spectroscopy



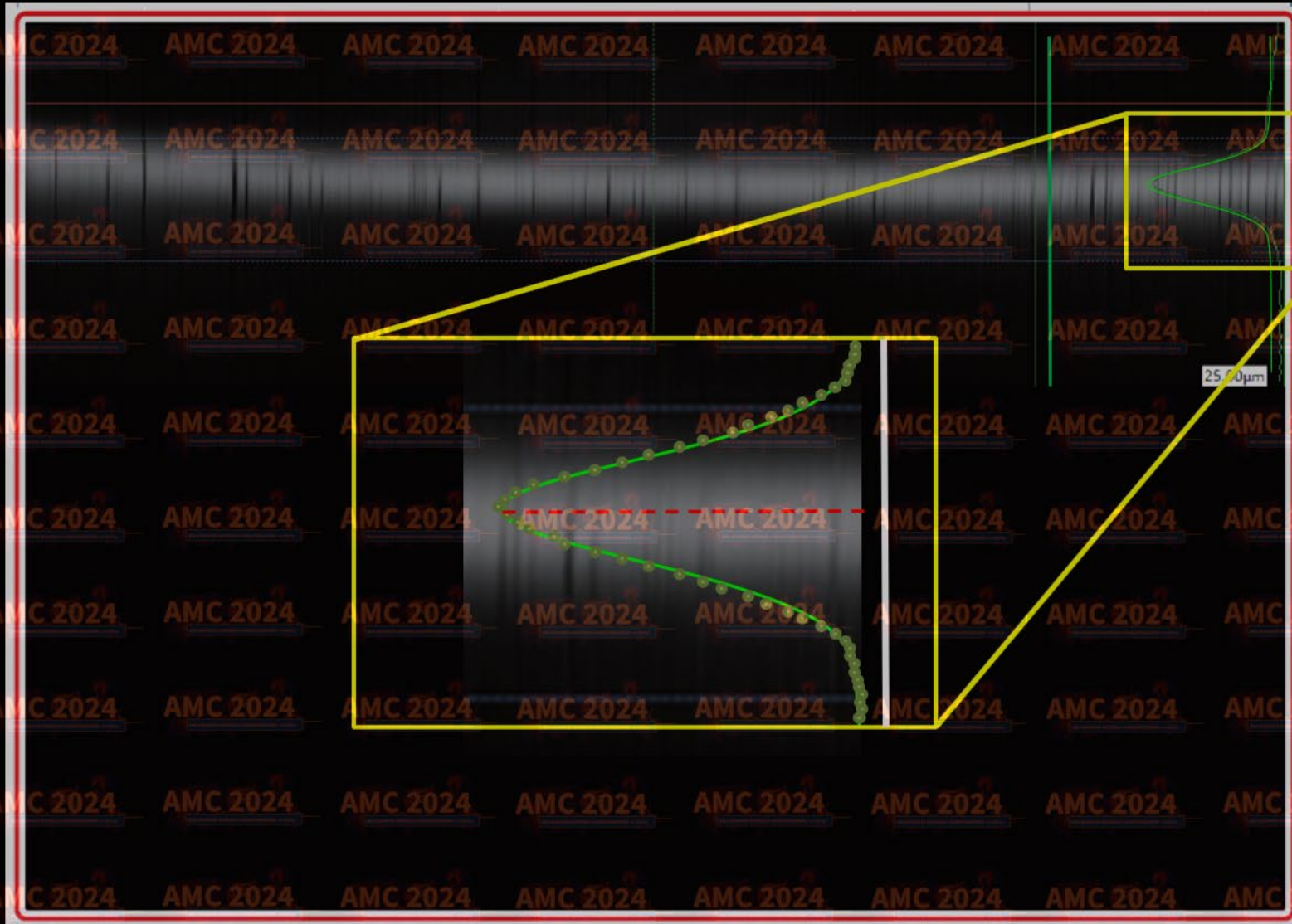
Chemical composition
Component identification
Components distribution



Confocal microscopy z-stack

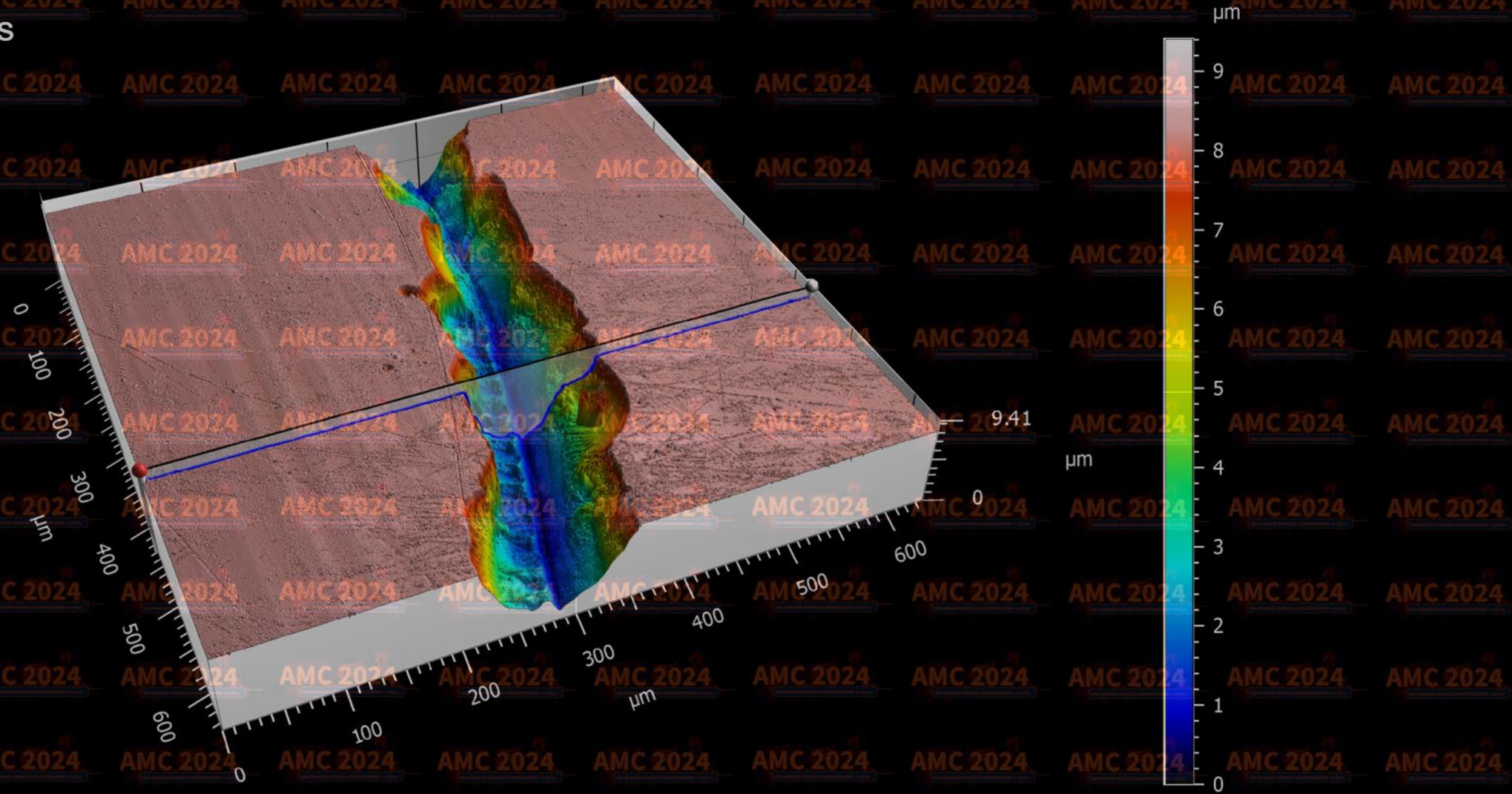


Confocal microscopy for measuring topography



Confocal microscopy

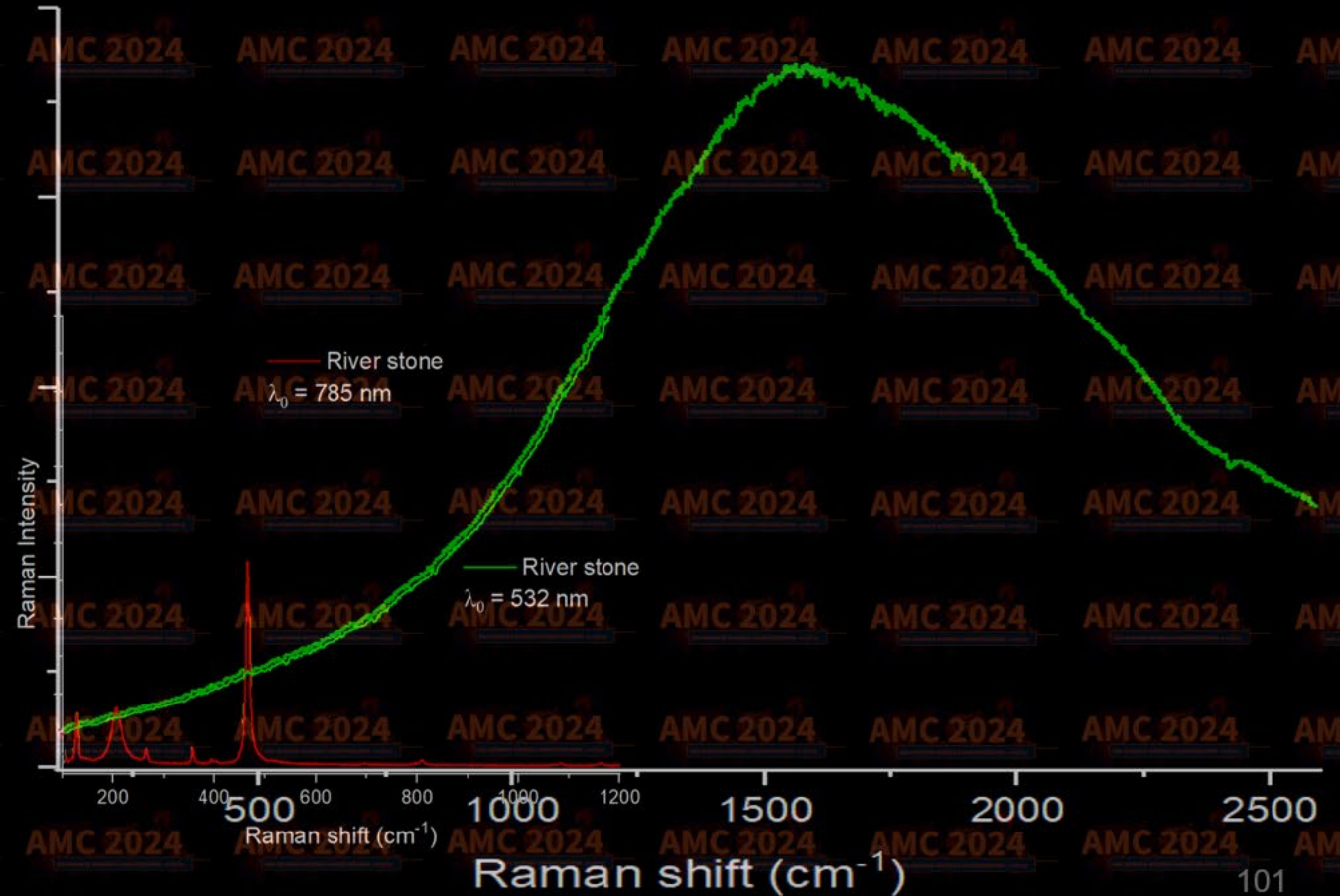
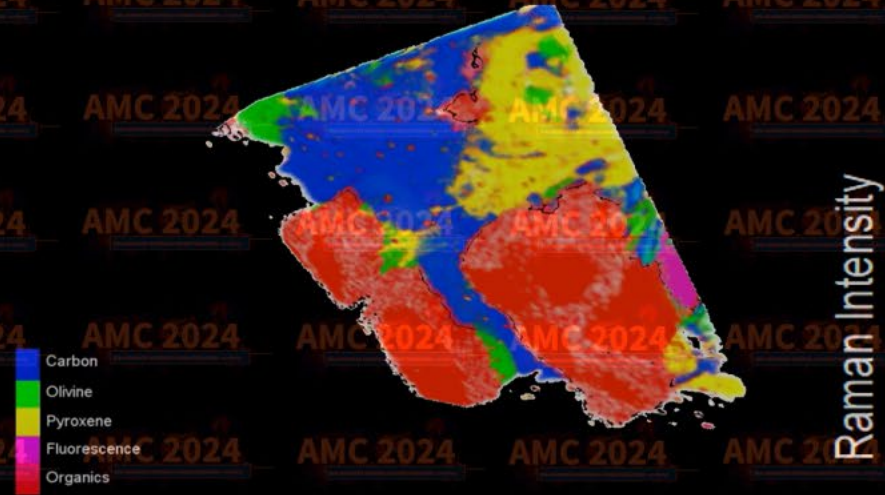
Scratch on glass



Raman spectroscopy

Primary Limitations:

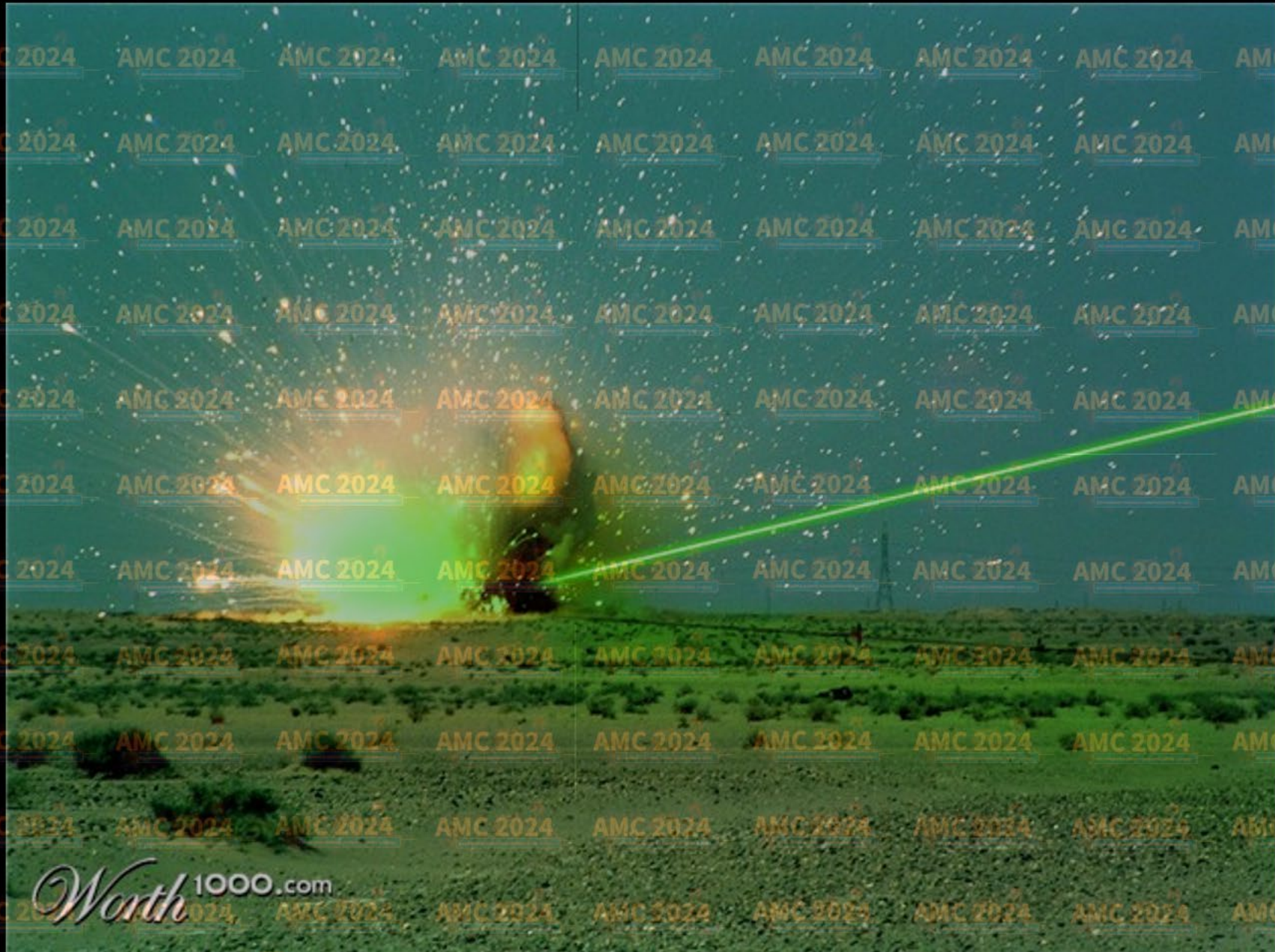
- Expensive apparatus (for high spectral/spatial resolution and sensitivity).
- Weak signal, compared to fluorescence.
- Limited spatial resolution (diffraction limited).



The More Time Approach



The More Power Approach



Worth 1000.com



Surface Plasmons

Dielectric

Metal

www.juluribk.com

Plasmons can be driven by photons at resonance to build large standing wave electric fields.

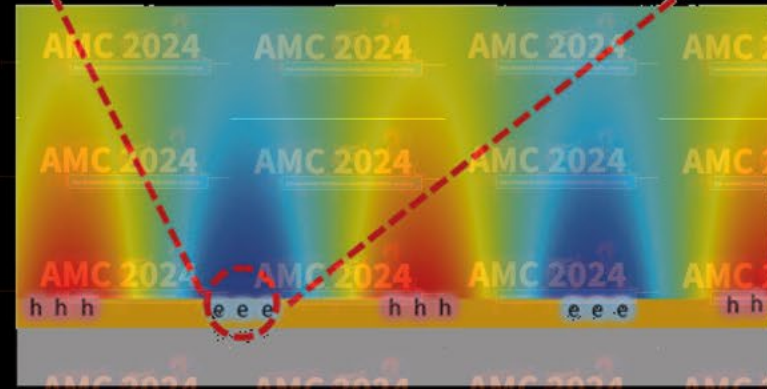
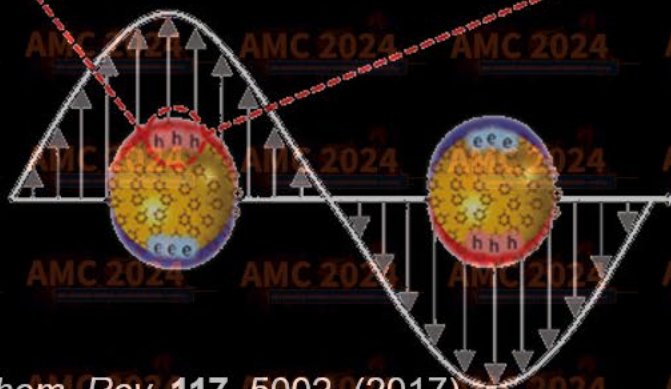
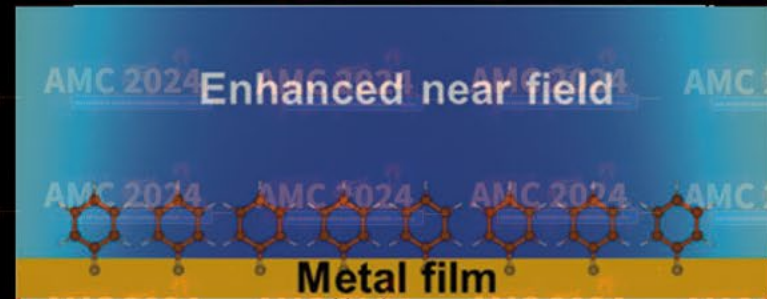
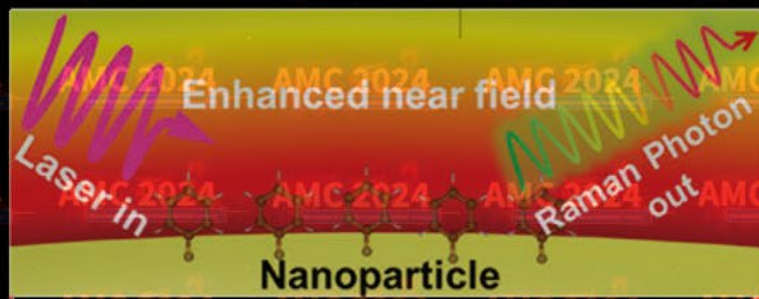
That leads to a strong enhancement of Raman scattering, proportional to the squared E field strength.

$$I = K \nu^4 p_0^2 \sin^2 \theta$$

Surface Enhanced Raman Spectroscopy (SERS)

Typically achieved with corrugated gold/silver surface or gold/silver nanoparticles with molecules of interest attached.

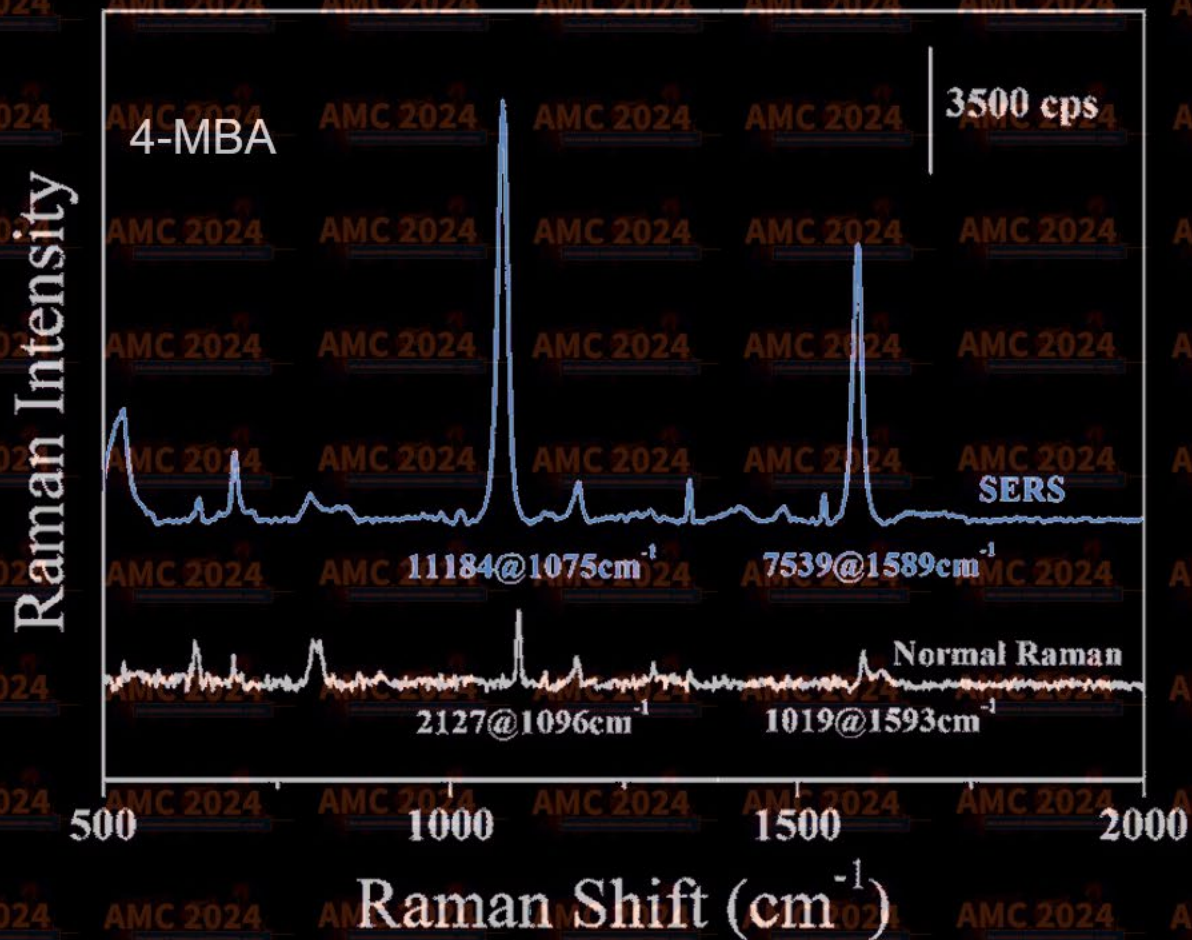
Capable of boosting Raman signal up to **14 Orders of Magnitude** or more! *Science* 275, 1102 (1997)



● Metal sphere ● Electric field ● Molecule ● h Holes ● e Electrons ● Prism

Chem. Rev. 117, 5002, (2017)

Surface Enhanced Raman Spectroscopy (SERS)



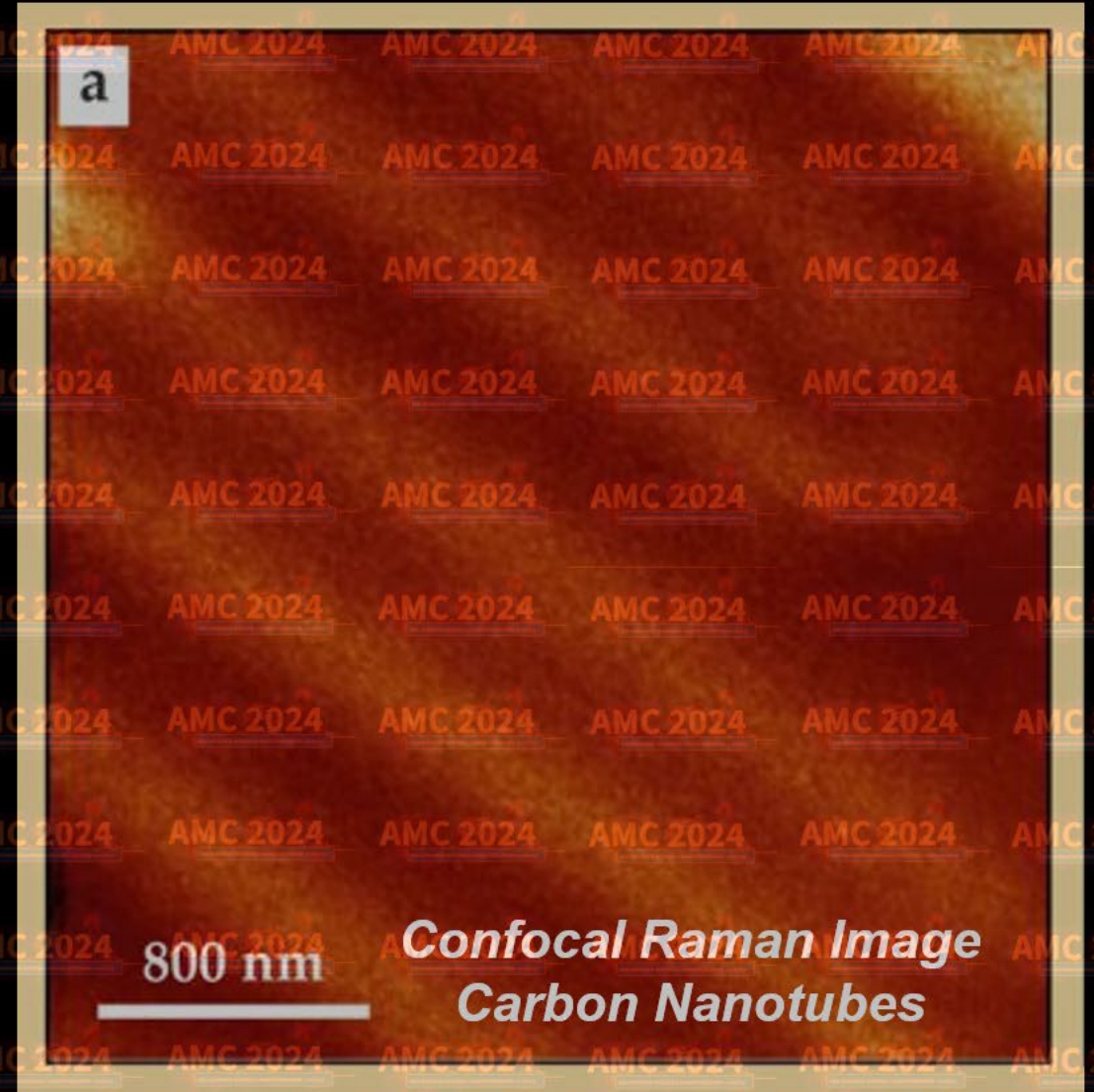
Anal. Methods, **6**, 9547 (2014)



Confocal Raman Microscopy

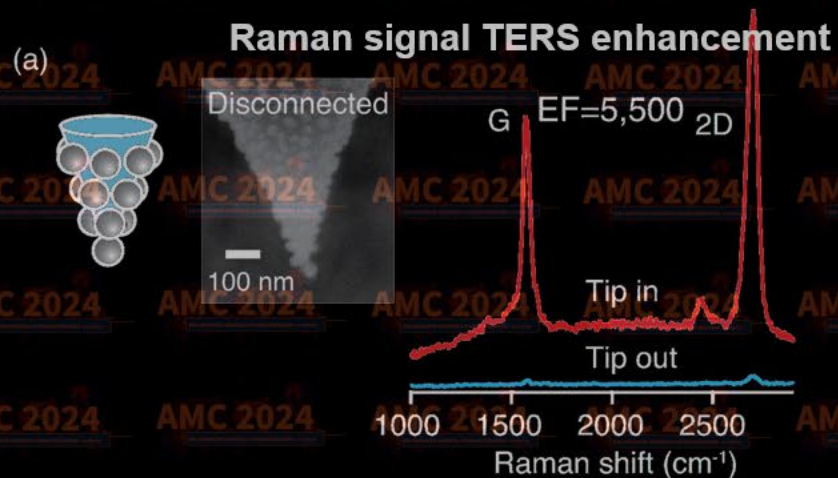
That's cool, but what about ...

- Limited spatial resolution (diffraction limited).

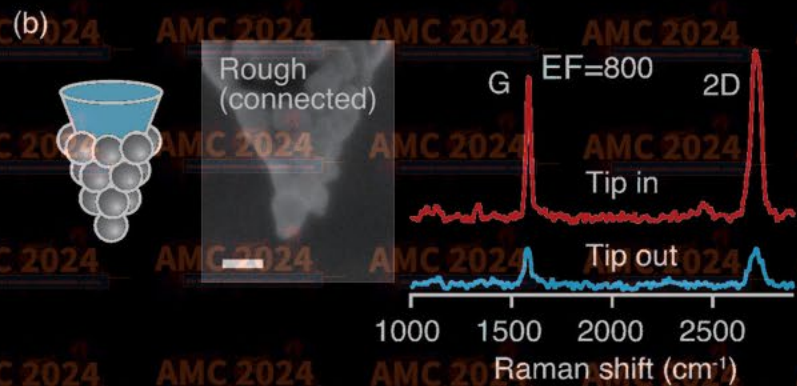


Phys. Rev. Lett. **103**, 186101 (2009)

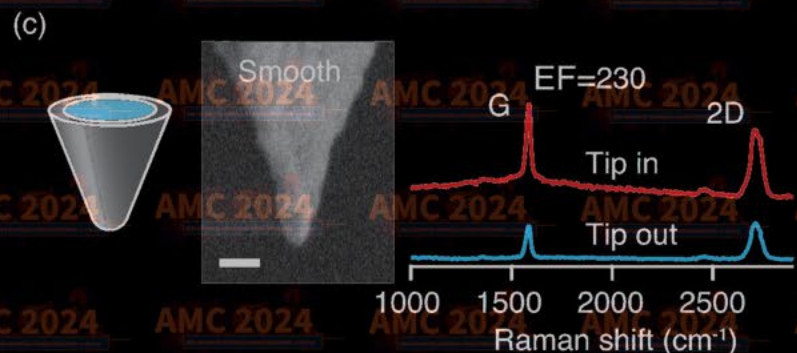
Tip Enhanced Raman Spectroscopy (TERS)



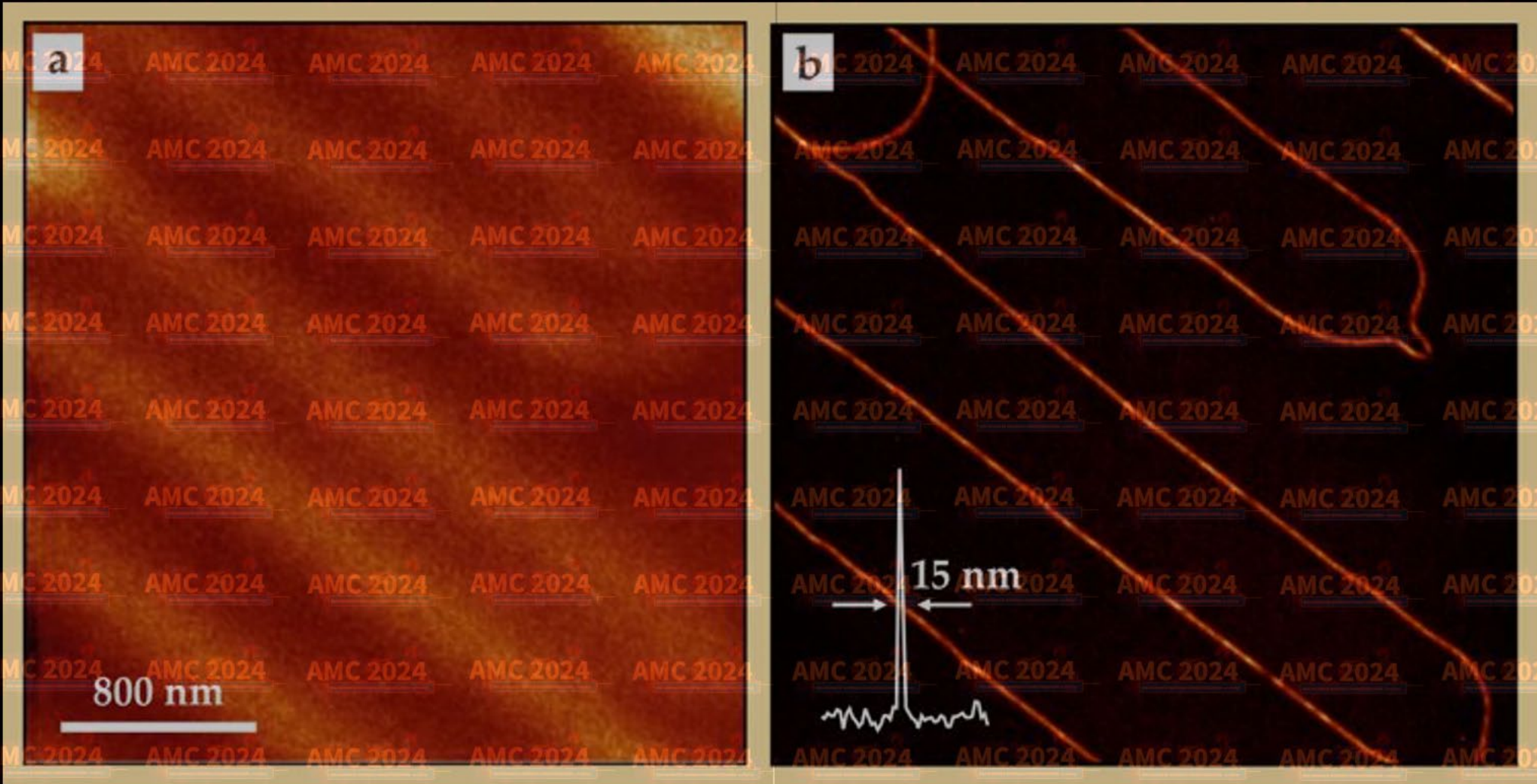
What is really cool is that this also works with a single metalized sharp tip, such as an STM or AFM tip!



Not only do you get the electric field enhancement, but now the source of the Raman signal is extremely localized.



Tip Enhanced Raman Spectroscopy (TERS)



Confocal Raman Image

Tip Enhanced Raman Image

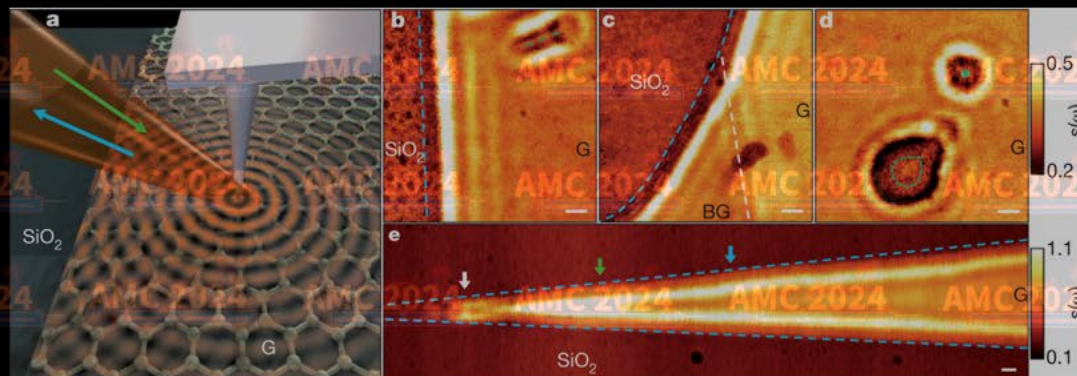
Carbon Nanotubes

Phys. Rev. Lett. **103**, 186101 (2009)¹⁰⁹

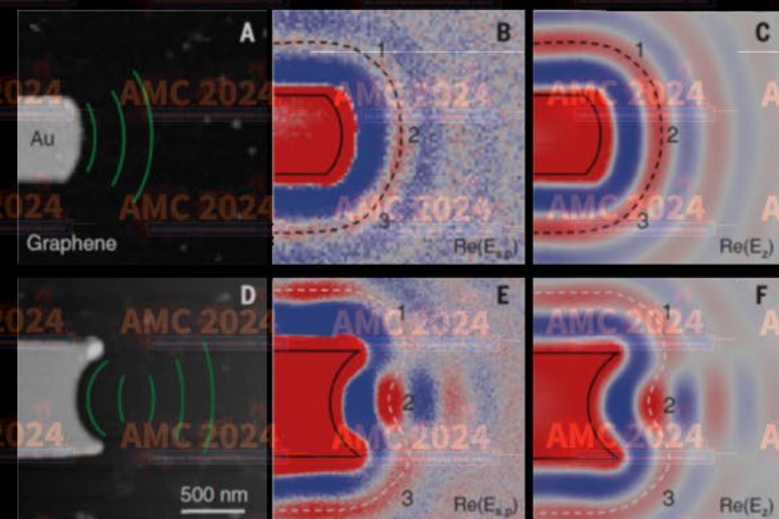
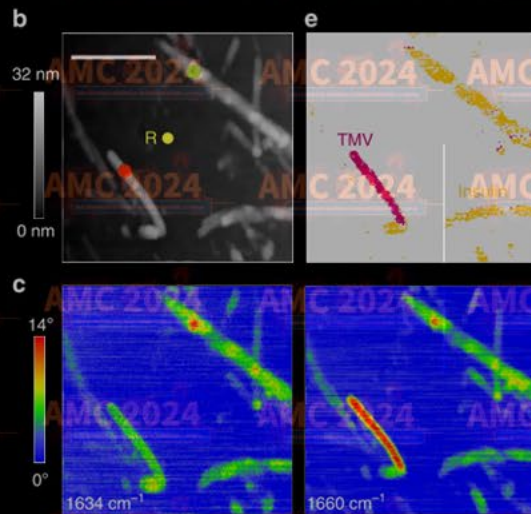
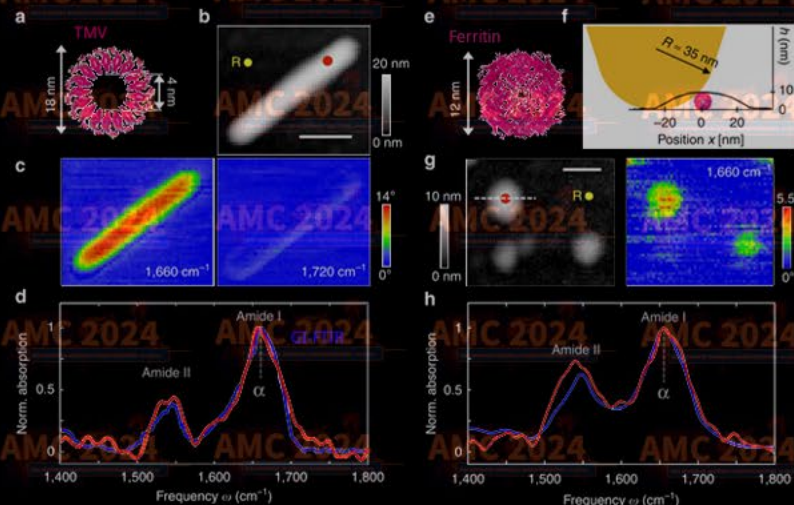
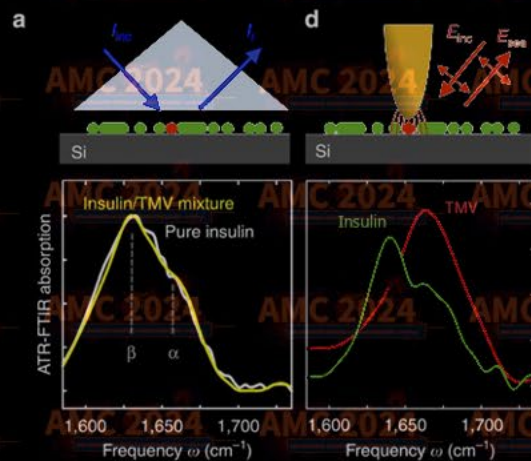


Near-field scanning optical nanospectroscopy

Nano-FTIR



Nature 000, 1-4 (2012) doi:10.1038/nature11253



Science 344, 1369

Nature Communications 4, 2890



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